

TL03x, TL03xA ENHANCED-JFET LOW-POWER LOW-OFFSET OPERATIONAL AMPLIFIERS

SLOS180C – FEBRUARY 1997 – REVISED DECEMBER 2001

- Direct Upgrades for the TL06x Low-Power BiFETs
- Low Power Consumption . . . 6.5 mW/Channel Typ
- On-Chip Offset-Voltage Trimming for Improved DC Performance (1.5 mV, TL031A)
- Higher Slew Rate and Bandwidth Without Increased Power Consumption
- Available in TSSOP for Small Form-Factor Designs

description

The TL03x series of JFET-input operational amplifiers offer improved dc and ac characteristics over the TL06x family of low-power BiFET operational amplifiers. On-chip zener trimming of offset voltage yields precision grades as low as 1.5 mV (TL031A) for greater accuracy in dc-coupled applications. The Texas Instruments improved BiFET process and optimized designs also yield improved bandwidths and slew rates without increased power consumption. The TL03x devices are pin-compatible with the TL06x and can be used to upgrade existing circuits or for optimal performance in new designs.

BiFET operational amplifiers offer the inherently higher input impedance of the JFET-input transistors without sacrificing the output drive associated with bipolar amplifiers. This higher input impedance makes the TL3x amplifiers better suited for interfacing with high-impedance sensors or very low-level ac signals. These devices also feature inherently better ac response than bipolar or CMOS devices having comparable power consumption.

The TL03x family has been optimized for micropower operation, while improving on the performance of the TL06x series. Designers requiring significantly faster ac response should consider the Excalibur™ TLE206x family of low-power BiFET operational amplifiers.

Because BiFET operational amplifiers are designed for use with dual power supplies, care must be taken to observe common-mode input-voltage limits and output swing when operating from a single supply. DC biasing of the input signal is required, and loads should be terminated to a virtual-ground node at midsupply. The TI TLE2426 integrated virtual-ground generator is useful when operating BiFET amplifiers from single supplies.

The TL03x devices are fully specified at ± 15 V and ± 5 V. For operation in low-voltage and/or single-supply systems, the TI LinCMOS families of operational amplifiers (TLC prefix) are recommended. When moving from BiFET to CMOS amplifiers, particular attention should be paid to slew rate, bandwidth requirements, and output loading.

The C-suffix devices are characterized for operation from 0°C to 70°C. The I-suffix devices are characterized for operation from –40°C to 85°C. The M-suffix devices are characterized for operation over the full military temperature range of –55°C to 125°C.



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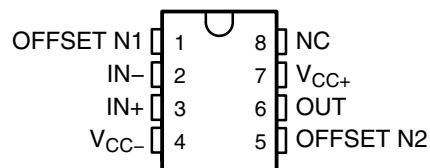
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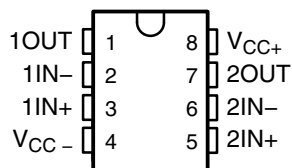
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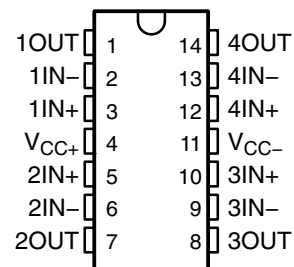
TL031x, TL031Ax
D, JG, OR P PACKAGE
(TOP VIEW)



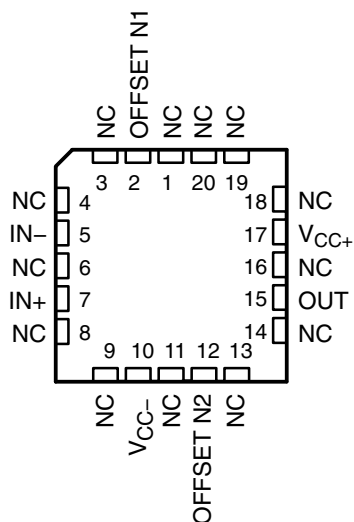
TL032x, TL032Ax
D, JG, OR P PACKAGE
(TOP VIEW)



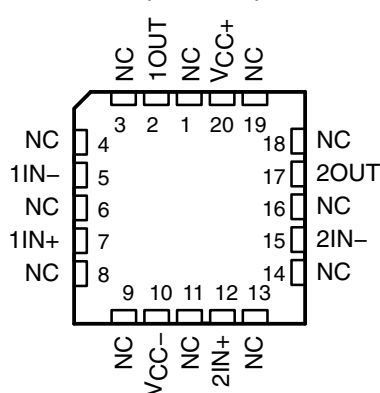
TL034x, TL034Ax
D, J, N, OR PW PACKAGE
(TOP VIEW)



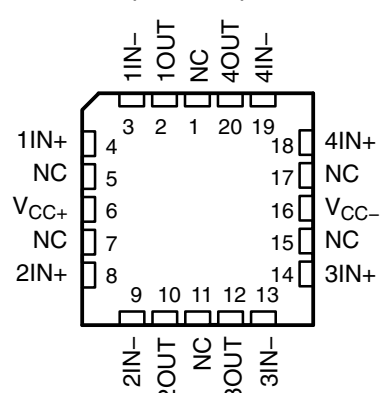
TL031M, TL031AM
FK PACKAGE
(TOP VIEW)



TL032M, TL032AM
FK PACKAGE
(TOP VIEW)



TL034M, TL034AM
FK PACKAGE
(TOP VIEW)



NC – No internal connection

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AVAILABLE OPTIONS

T_A	$V_{IO\text{MAX}}$ AT 25°C	PACKAGED DEVICES						
		SMALL OUTLINE (D)	CHIP CARRIER (FK)	CERAMIC DIP (J)	CERAMIC DIP (JG)	PLASTIC DIP (N)	PLASTIC DIP (P)	TSSOP (PW)
0°C to 70°C	0.8 mV	TL031ACD TL032ACD	—	—	—	—	TL031ACP TL032ACP	—
	1.5 mV	TL031CD TL032CD TL034ACD	—	—	—	TL034ACN	TL031CP TL032CP	—
	4 mV	TL034CD	—	—	—	TL034CN	—	TL034CPW
–40°C to 85°C	0.8 mV	TL031AID TL032AID	—	—	—	—	TL031AIP TL032AIP	—
	1.5 mV	TL031ID TL032ID TL034AID	—	—	—	TL034AIN	TL031IP TL032IP	—
	4 mV	TL034ID	—	—	—	TL034IN	—	—
–55°C to 125°C	0.8 mV	TL031AMD TL032AMD	TL031AMFK TL032AMFK	—	TL031AMJG TL032AMJG	—	TL031AMP TL032AMP	—
	1.5 mV	TL031MD TL032MD TL034AMD	TL031MFK TL032MFK TL034AMFK	TL034AMJ	TL031MJG TL032MJG	TL034AMN	TL031MP TL032MP	—
	4 mV	TL034MD	TL034MFK	TL034MJ	—	TL034MN	—	—

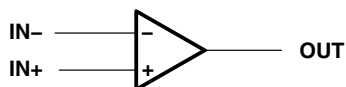
The D and PW packages are available taped and reeled and are indicated by adding an R suffix to device type (e.g., TL034CDR or TL034CPWR).



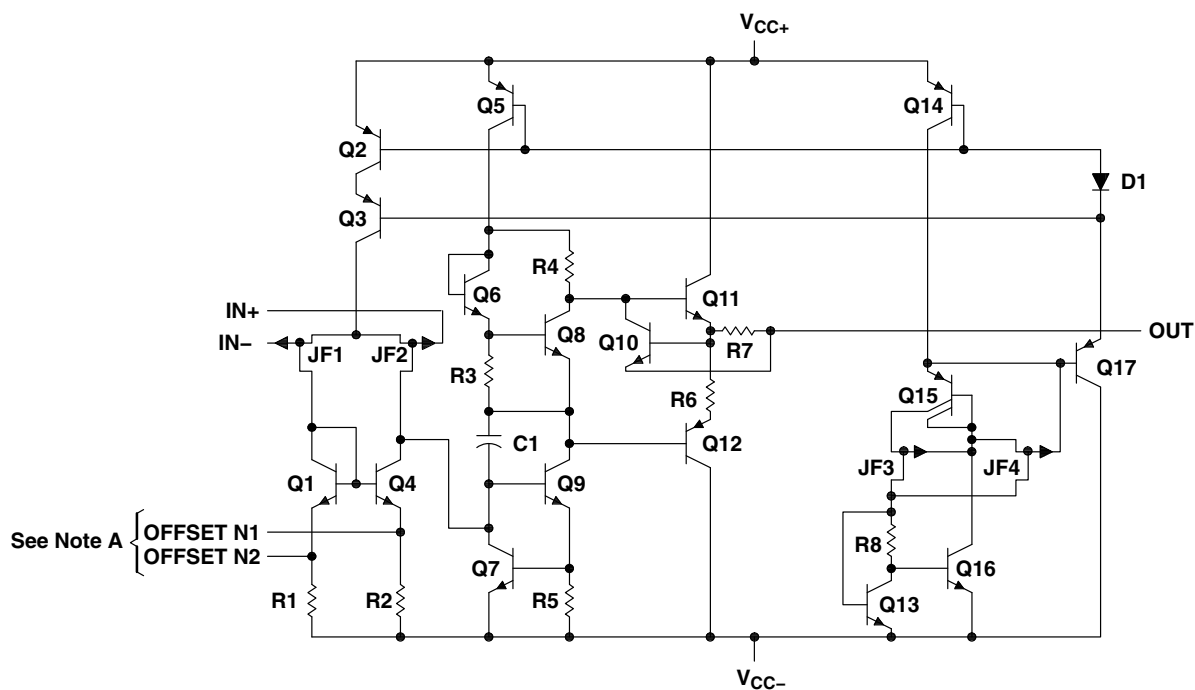
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symbol (each amplifier)



equivalent schematic (each amplifier)



NOTE A: OFFSET N1 and OFFSET N2 are available only on the TL031, TL031A.

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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)[†]

Supply voltage (see Note 1): V_{CC+}	18 V
V_{CC-}	–18 V
Differential input voltage, V_{ID} (see Note 2)	±30 V
Input voltage, V_I (any input) (see Notes 1 and 3)	±15 V
Input current, I_I (each input)	±1 mA
Output current, I_O (each output)	±40 mA
Total current into V_{CC+}	160 mA
Total current out of V_{CC-}	160 mA
Duration of short-circuit current at (or below) 25°C (see Note 4)	Unlimited
Continuous total power dissipation	See Dissipation Rating Table
Package thermal impedance, θ_{JA} (see Note 5): D package (8 pin)	97°C/W
D package (14 pin)	86°C/W
N package	80°C/W
P package	85°C/W
PW package	113°C/W
Lead temperature 1,6 mm (1 /16 inch) from case for 10 seconds: D, N, P, or PW package	260°C
Lead temperature 1,6 mm (1 /16 inch) from case for 60 seconds: J or JG package	300°C
Case temperature for 60 seconds: FK package	260°C
Storage temperature range, T_{stg}	–65°C to 150°C

[†] Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltage values, except differential voltages, are with respect to the midpoint between V_{CC+} and V_{CC-} .
2. Differential voltages are at $IN+$ with respect to $IN-$.
3. The magnitude of the input voltage must never exceed the magnitude of the supply voltage or 15 V, whichever is less.
4. The output may be shorted to either supply. Temperature and/or supply voltages must be limited to ensure that the maximum dissipation rating is not exceeded.
5. The package thermal impedance is calculated in accordance with JESD 51-7.

DISSIPATION RATING TABLE

PACKAGE	$T_A \leq 25^\circ\text{C}$ POWER RATING	DERATING FACTOR ABOVE $T_A = 25^\circ\text{C}$	$T_A = 70^\circ\text{C}$ POWER RATING	$T_A = 85^\circ\text{C}$ POWER RATING	$T_A = 125^\circ\text{C}$ POWER RATING
FK	1375 mW	11.0 mW/°C	880 mW	715 mW	275 mW
J	1375 mW	11.0 mW/°C	880 mW	715 mW	275 mW
JG	1050 mW	8.4 mW/°C	672 mW	546 mW	210 mW

recommended operating conditions

		C SUFFIX		I SUFFIX		M SUFFIX		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
$V_{CC\pm}$	Supply voltage	±5	±15	±5	±15	±5	±15	V
V_{IC}	Common-mode input voltage	$V_{CC\pm} = \pm 5\text{ V}$		–1.5	4	–1.5	4	V
		$V_{CC\pm} = \pm 15\text{ V}$		–11.5	14	–11.5	14	
T_A	Operating free-air temperature	0	70	–40	85	–55	125	°C



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TL031C and TL031AC electrical characteristics at specified free-air temperature

PARAMETER		TEST CONDITIONS		T _A	TL031C, TL031AC						UNIT
					V _{CC±} = ±5 V			V _{CC±} = ±15 V			
					MIN	TYP	MAX	MIN	TYP	MAX	
V _{IO}	Input offset voltage	V _O = 0, V _{IC} = 0, R _S = 50 Ω	TL031C	25°C	0.54	3.5	0.5		1.5	mV	
				Full range†	4.5		2.5				
			TL031AC	25°C	0.41	2.8	0.34		0.8		
				Full range†	3.8		1.8				
α _{V_{IO}}	Temperature coefficient of input offset voltage	V _O = 0, V _{IC} = 0, R _S = 50 Ω	TL031C	25°C to 70°C	7.1		5.9		μV/°C		
			TL031AC	25°C to 70°C	7.1		5.9	25			
Input offset voltage long-term drift†		V _O = 0, V _{IC} = 0, R _S = 50 Ω		25°C	0.04		0.04		μV/mo		
I _{IO}	Input offset current	V _O = 0, V _{IC} = 0 See Figure 5		25°C	1	100	1	100	pA		
				70°C	9	200	12	200			
I _{IB}	Input bias current	V _O = 0, V _{IC} = 0 See Figure 5		25°C	2	200	2	200	pA		
				70°C	50	400	80	400			
V _{ICR}	Common-mode input voltage range			25°C	-1.5 to 4	-3.4 to 5.4	-11.5 to 14	-13.4 to 15.4	V		
				Full range†	-1.5 to 4	-11.5 to 14					
V _{OM+}	Maximum positive peak output voltage swing	R _L = 10 kΩ		25°C	3	4.3	13	14	V		
				0°C	3	4.2	13	14			
				70°C	3	4.3	13	14			
V _{OM-}	Maximum negative peak output voltage swing	R _L = 10 kΩ		25°C	-3	-4.2	-12.5	-13.9	V		
				0°C	-3	-4.1	-12.5	-13.9			
				70°C	-3	-4.2	-12.5	-14			
A _{VD}	Large-signal differential voltage amplification§	R _L = 10 kΩ		25°C	4	12	5	14.3	V/mV		
				0°C	3	11.1	4	13.5			
				70°C	4	13.3	5	15.2			
r _i	Input resistance			25°C	10 ¹²		10 ¹²		Ω		
c _i	Input capacitance			25°C	5		4		pF		
CMRR	Common-mode rejection ratio	V _{IC} = V _{ICRmin} , V _O = 0, R _S = 50 Ω		25°C	70	87	75	94	dB		
				0°C	70	87	75	94			
				70°C	70	87	75	94			
k _{SVR}	Supply-voltage rejection ratio (ΔV _{CC±} /ΔV _{IO})	V _O = 0, R _S = 50 Ω		25°C	75	96	75	96	dB		
				0°C	75	96	75	96			
				70°C	75	96	75	96			

† Full range is 0°C to 70°C.

‡ Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at T_A = 150°C extrapolated to T_A = 25°C using the Arrhenius equation and assuming an activation energy of 0.96 eV.

§ At V_{CC±} = ±5 V, V_O = ±2.3 V; at V_{CC±} = ±15 V, V_O = ±10 V

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TL031C and TL031AC electrical characteristics at specified free-air temperature (continued)

PARAMETER		TEST CONDITIONS		T _A	TL031C, TL031AC						UNIT
					V _{CC±} = ±5 V			V _{CC±} = ±15 V			
					MIN	TYP	MAX	MIN	TYP	MAX	
P _D	Total power dissipation	V _O = 0,	No load	25°C	1.9	2.5	6.5		8.4		mW
				0°C	1.8	2.5	6.3		8.4		
				70°C	1.9	2.5	6.3		8.4		
I _{CC}	Supply current	V _O = 0,	No load	25°C	192	250	217		280		μA
				0°C	184	250	211		280		
				70°C	189	250	210		280		

TL031C and TL031AC operating characteristics at specified free-air temperature

PARAMETER		TEST CONDITIONS		T _A	TL031C, TL031AC						UNIT	
					V _{CC±} = ±5 V			V _{CC±} = ±15 V				
					MIN	TYP	MAX	MIN	TYP	MAX		
SR+	Positive slew rate at unity gain†	R _L = 10 kΩ, C _L = 100 pF See Figure 1		25°C	2			1.5 2.9			V/μs	
				0°C	1.8			1 2.6				
				70°C	2.2			1.5 3.2				
SR–	Negative slew rate at unity gain†	R _L = 10 kΩ, C _L = 100 pF See Figure 1		25°C	3.9			1.5 5.1			V/μs	
				0°C	3.7			1.5 5				
				70°C	4			1.5 5				
t _r	Rise time	V _{I(PP)} = ±10 mV, R _L = 10 kΩ, C _L = 100 pF See Figures 1 and 2		25°C	138			132			ns	
				0°C	134			127				
				70°C	150			142				
t _f	Fall time	V _{I(PP)} = ±10 mV, R _L = 10 kΩ, C _L = 100 pF See Figure 1		25°C	138			132			ns	
				0°C	134			127				
				70°C	150			142				
Overshoot factor		V _{I(PP)} = ±10 mV, R _L = 10 kΩ, C _L = 100 pF See Figures 1 and 2		25°C	11%			5%				
				0°C	10%			4%				
				70°C	12%			6%				
V _n	Equivalent input noise voltage	TL031C	R _S = 20 Ω See Figure 3	f = 10 Hz	25°C	61			61			nV/√Hz
				f = 1 kHz		41			41			
		TL031AC		f = 10 Hz	25°C	61			61			
				f = 1 kHz		41			41 60			
I _n	Equivalent input noise current	f = 1 kHz		25°C	0.003			0.003			pA/√Hz	
B ₁	Unity-gain bandwidth	V _I = 10 mV R _L = 10 kΩ, C _L = 25 pF See Figure 4		25°C	1			1.1			MHz	
				0°C	1			1.1				
				70°C	1			1				
φ _m	Phase margin at unity gain	V _I = 10 mV R _L = 10 kΩ, C _L = 25 pF See Figure 4		25°C	61°			65°				
				0°C	61°			65°				
				70°C	60°			64°				

[†] For V_{CC±} = ±5 V, V_{I(PP)} = ±1 V; for V_{CC±} = ±15 V, V_{I(PP)} = ±5 V



**TEXAS
INSTRUMENTS**

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TL031I and TL031AI electrical characteristics at specified free-air temperature

PARAMETER	TEST CONDITIONS		T _A	TL031I, TL031AI						UNIT
				V _{CC±} = ±5 V			V _{CC±} = ±15 V			
				MIN	TYP	MAX	MIN	TYP	MAX	
V _{IO} Input offset voltage	V _O = 0, V _{IC} = 0, R _S = 50 Ω	TL031I	25°C	0.54	3.5	0.5	1.5	mV		
			Full range†	5.3	3.3					
		TL031AI	25°C	0.41	2.8	0.34	0.8			
			Full range†	4.6	2.6					
α _{V_{IO}} Temperature coefficient of input offset voltage	V _O = 0, V _{IC} = 0, R _S = 50 Ω	TL031I	25°C to 85°C	6.5	6.2	μV/°C				
		TL031AI	25°C to 85°C	6.5	6.2		25			
Input offset voltage long-term drift‡	V _O = 0, V _{IC} = 0, R _S = 50 Ω		25°C	0.04	0.04	μV/mo				
I _{IO} Input offset current	V _O = 0, V _{IC} = 0 See Figure 5		25°C	1	100	1	100	pA		
			85°C	0.02	0.45	0.02	0.45	nA		
I _{IB} Input bias current	V _O = 0, V _{IC} = 0 See Figure 5		25°C	2	200	2	200	pA		
			85°C	0.2	0.9	0.2	0.9	nA		
V _{ICR} Common-mode input voltage range			25°C	-1.5 to 4	-3.4 to 5.4	-11.5 to 14	-13.4 to 15.4	V		
			Full range†	-1.5 to 4	-11.5 to 14					
V _{OM+} Maximum positive peak output voltage swing	R _L = 10 kΩ		25°C	3	4.3	13	14	V		
			-40°C	3	4.1	13	14			
			85°C	3	4.4	13	14			
V _{OM-} Maximum negative peak output voltage swing	R _L = 10 kΩ		25°C	-3	-4.2	-12.5	-13.9	V		
			-40°C	-3	-4.1	-12.5	-13.8			
			85°C	-3	-4.2	-12.5	-14			
A _{VD} Large-signal differential voltage amplification§	R _L = 10 kΩ		25°C	4	12	5	14.3	V/mV		
			-40°C	3	8.4	4	11.6			
			85°C	4	13.5	5	15.3			
r _i Input resistance			25°C	10 ¹²	10 ¹²	Ω				
c _i Input capacitance			25°C	5	4	pF				
CMRR Common-mode rejection ratio	V _{IC} = V _{ICRmin} , V _O = 0, R _S = 50 Ω		25°C	70	87	75	94	dB		
			-40°C	70	87	75	94			
			85°C	70	87	75	94			
k _{SVR} Supply-voltage rejection ratio (ΔV _{CC±} /ΔV _{IO})	V _O = 0, R _S = 50 Ω		25°C	75	96	75	96	dB		
			-40°C	75	96	75	96			
			85°C	75	96	75	96			

† Full range is -40°C to 85°C.

‡ Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at T_A = 150°C extrapolated to T_A = 25°C using the Arrhenius equation and assuming an activation energy of 0.96 eV.

§ At V_{CC±} = ±5 V, V_O = ±2.3 V; at V_{CC±} = ±15 V, V_O = ±10 V



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TL031I and TL031AI electrical characteristics at specified free-air temperature (continued)

PARAMETER		TEST CONDITIONS		T _A	TL031I, TL031AI						UNIT
					V _{CC±} = ±5 V			V _{CC±} = ±15 V			
					MIN	TYP	MAX	MIN	TYP	MAX	
P _D	Total power dissipation	V _O = 0,	No load	25°C		1.9	2.5		6.5	8.4	mW
				−40°C		1.4	2.5		5.4	8.4	
				85°C		1.9	2.5		6.2	8.4	
I _{CC}	Supply current	V _O = 0,	No load	25°C		192	250		217	280	μA
				−40°C		144	250		181	280	
				85°C		189	250		207	280	

TL031I and TL031AI operating characteristics at specified free-air temperature

PARAMETER		TEST CONDITIONS		T _A	TL031I, TL031AI						UNIT	
					V _{CC±} = ±5 V			V _{CC±} = ±15 V				
					MIN	TYP	MAX	MIN	TYP	MAX		
SR+	Positive slew rate at unity gain†	R _L = 10 kΩ, C _L = 100 pF See Figure 1		25°C	2			1.5 2.9			V/μs	
				−40°C	1.6			1 2.1				
				85°C	2.3			1.5 3.3				
SR−	Negative slew rate at unity gain†	R _L = 10 kΩ, C _L = 100 pF See Figure 1		25°C	3.9			1.5 5.1			V/μs	
				−40°C	3.3			1.5 4.8				
				85°C	4.1			1.5 4.9				
t _r	Rise time	V _{I(PP)} = ±10 mV, R _L = 10 kΩ, C _L = 100 pF See Figures 1 and 2		25°C	138			132			ns	
				−40°C	132			123				
				85°C	154			146				
t _f	Fall time	V _{I(PP)} = ±10 mV, R _L = 10 kΩ, C _L = 100 pF See Figure 1		25°C	138			132			ns	
				−40°C	132			123				
				85°C	154			146				
Overshoot factor		V _{I(PP)} = ±10 mV, R _L = 10 kΩ, C _L = 100 pF See Figures 1 and 2		25°C	11%			5%				
				−40°C	12%			5%				
				85°C	13%			7%				
V _n	Equivalent input noise voltage	TL031I	R _S = 20 Ω See Figure 3	f = 10 Hz	25°C	61			61			nV/√Hz
				f = 1 kHz		41			41			
		TL031AI	f = 10 Hz	25°C	61			61				
			f = 1 kHz		41			41 60				
I _n	Equivalent input noise current	f = 1 kHz		25°C	0.003			0.003			pA/√Hz	
B ₁	Unity-gain bandwidth	V _I = 10 mV R _L = 10 kΩ, C _L = 25 pF See Figure 4		25°C	1			1.1			MHz	
				−40°C	1			1.1				
				85°C	0.9			1				
φ _m	Phase margin at unity gain	V _I = 10 mV, R _L = 10 kΩ, C _L = 25 pF See Figure 4		25°C	61°			65°				
				−40°C	60°			65°				
				85°C	60°			64°				

[†] For V_{CC±} = ±5 V, V_{I(PP)} = ±1 V; for V_{CC±} = ±15 V, V_{I(PP)} = ±5 V

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TL031M and TL031AM electrical characteristics at specified free-air temperature

PARAMETER		TEST CONDITIONS		T _A	TL031M, TL031AM						UNIT
					V _{CC±} = ±5 V			V _{CC±} = ±15 V			
					MIN	TYP	MAX	MIN	TYP	MAX	
V _{IO}	Input offset voltage	V _O = 0, V _{IC} = 0, R _S = 50 Ω	TL031M	25°C	0.54	3.5	0.5	1.5	mV		
				Full range†	6.5	4.5					
		TL031AM	25°C	0.41	2.8	0.34	0.8				
			Full range†	5.8	3.8						
α _{V_{IO}}	Temperature coefficient of input offset voltage	V _O = 0, V _{IC} = 0, R _S = 50 Ω	TL031M	25°C to 125°C	5.1	4.3	μV/°C				
			TL031AM	25°C to 125°C	5.1	4.3					
Input offset voltage long-term drift‡		V _O = 0, V _{IC} = 0, R _S = 50 Ω		25°C	0.04	0.04	μV/mo				
I _{IO}	Input offset current	V _O = 0, V _{IC} = 0 See Figure 5		25°C	1	100	1	100	pA		
				125°C	0.2	10	0.2	10	nA		
I _{IB}	Input bias current	V _O = 0, V _{IC} = 0 See Figure 5		25°C	2	200	2	200	pA		
				125°C	7	20	8	20	nA		
V _{ICR}	Common-mode input voltage range			25°C	-1.5 to 4	-3.4 to 5.4	-11.5 to 14	-13.4 to 15.4	V		
				Full range†	-1.5 to 4	-11.5 to 14					
V _{OM+}	Maximum positive peak output voltage swing	R _L = 10 kΩ		25°C	3	4.3	13	14	V		
				-55°C	3	4.1	13	14			
				125°C	3	4.4	13	14			
V _{OM-}	Maximum negative peak output voltage swing	R _L = 10 kΩ		25°C	-3	-4.2	-12.5	-13.9	V		
				-55°C	-3	-4	-12.5	-13.8			
				125°C	-3	-4.3	-12.5	-14			
A _{VD}	Large-signal differential voltage amplification§	R _L = 10 kΩ		25°C	4	12	5	14.3	V/mV		
				-55°C	3	7.1	4	10.4			
				125°C	3	12.9	4	15			
r _i	Input resistance			25°C	10 ¹²		10 ¹²		Ω		
c _i	Input capacitance			25°C	5		4		pF		
CMRR	Common-mode rejection ratio	V _{IC} = V _{ICRmin} , V _O = 0, R _S = 50 Ω		25°C	70	87	75	94	dB		
				-55°C	70	87	70	94			
				125°C	70	87	70	94			
k _{SVR}	Supply-voltage rejection ratio (ΔV _{CC±} /ΔV _{IO})	V _O = 0, R _S = 50 Ω		25°C	75	96	75	96	dB		
				-55°C	75	96	75	95			
				125°C	75	96	75	96			
P _D	Total power dissipation	V _O = 0, No load		25°C	1.9	2.5	6.5	8.4	mW		
				-55°C	1.1	2.5	4.7	8.4			
				125°C	1.8	2.5	5.8	8.4			

† Full range is -55°C to 125°C.

‡ Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at T_A = 150°C extrapolated to T_A = 25°C using the Arrhenius equation and assuming an activation energy of 0.96 eV.

§ At V_{CC±} = ±5 V, V_O = ±2.3 V; at V_{CC±} = ±15 V, V_O = ±10 V



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TL031M and TL031AM electrical characteristics at specified free-air temperature (continued)

PARAMETER	TEST CONDITIONS	T _A	TL031M, TL031AM						UNIT
			V _{CC±} = ±5 V			V _{CC±} = ±15 V			
			MIN	TYP	MAX	MIN	TYP	MAX	
I _{CC} Supply current	V _O = 0, No load	25°C		192	250		217	280	μA
		–55°C		114	250		156	280	
		125°C		178	250		197	280	

TL031M and TL031AM operating characteristics at specified free-air temperature

PARAMETER		TEST CONDITIONS		T _A	TL031M, TL031AM						UNIT	
					V _{CC±} = ±5 V			V _{CC±} = ±15 V				
					MIN	TYP	MAX	MIN	TYP	MAX		
SR+	Positive slew rate at unity gain†	R _L = 10 kΩ, C _L = 100 pF See Figure 1		25°C	2			1.5 2.9			V/μs	
				–55°C	1.4			1 1.9				
				125°C	2.4			1 3.5				
SR–	Negative slew rate at unity gain†	R _L = 10 kΩ, C _L = 100 pF See Figure 1		25°C	3.9			1.5 5.1			V/μs	
				–55°C	3.2			1 4.6				
				125°C	4.1			1 4.7				
t _r	Rise time	V _{I(PP)} = ±10 mV, R _L = 10 kΩ, C _L = 100 pF See Figures 1 and 2		25°C	138			132			ns	
				–55°C	142			123				
				125°C	166			158				
t _f	Fall time	V _{I(PP)} = ±10 mV, R _L = 10 kΩ, C _L = 100 pF See Figure 1		25°C	138			132			ns	
				–55°C	142			123				
				125°C	166			158				
Overshoot factor		V _{I(PP)} = ±10 mV, R _L = 10 kΩ, C _L = 100 pF See Figures 1 and 2		25°C	11%			5%				
				–55°C	16%			6%				
				125°C	14%			8%				
V _n	Equivalent input noise voltage	TL031M	R _S = 20 Ω See Figure 3	f = 10 Hz	25°C	61			61			nV/√Hz
				f = 1 kHz		41			41			
		TL031AM		f = 10 Hz	25°C	61			61			
				f = 1 kHz		41			41			
I _n	Equivalent input noise current	f = 1 kHz		25°C	0.003			0.003			pA/√Hz	
B ₁	Unity-gain bandwidth	V _I = 10 mV, R _L = 10 kΩ, C _L = 25 pF See Figure 4		25°C	1			1.1			MHz	
				–55°C	1			1.1				
				125°C	0.9			0.9				
φ _m	Phase margin at unity gain	V _I = 10 mV, R _L = 10 kΩ, C _L = 25 pF See Figure 4		25°C	61°			65°				
				–55°C	57°			64°				
				125°C	59°			62°				

[†] For V_{CC±} = ±5 V, V_{I(PP)} = ±1 V; for V_{CC±} = ±15 V, V_{I(PP)} = ±5 V



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TL032C and TL032AC electrical characteristics at specified free-air temperature

PARAMETER		TEST CONDITIONS		T _A	TL032C, TL032AC						UNIT
					V _{CC±} = ±5 V			V _{CC±} = ±15 V			
					MIN	TYP	MAX	MIN	TYP	MAX	
V _{IO}	Input offset voltage	V _O = 0, V _{IC} = 0, R _S = 50 Ω	TL032C	25°C	0.69	3.5	0.57	1.5	mV		
				Full range†	4.5	2.5					
			TL032AC	25°C	0.53	2.8	0.39	0.8			
				Full range†	3.8	1.8					
α _{V_{IO}}	Temperature coefficient of input offset voltage	V _O = 0, V _{IC} = 0, R _S = 50 Ω	TL032C	25°C to 70°C	11.5	10.8	μV/°C				
			TL032AC	25°C to 70°C	11.5	10.8		25			
	Input offset voltage long-term drift‡	V _O = 0, V _{IC} = 0, R _S = 50 Ω		25°C	0.04	0.04	μV/mo				
I _{IO}	Input offset current	V _O = 0, See Figure 5	V _{IC} = 0	25°C	1	100	1	100	pA		
				70°C	9	200	12	200			
I _{IB}	Input bias current	V _O = 0, See Figure 5	V _{IC} = 0	25°C	2	200	2	200	pA		
				70°C	50	400	80	400			
V _{ICR}	Common-mode input voltage range			25°C	-1.5 to 4	-3.4 to 5.4	-11.5 to 14	-13.4 to 15.4	V		
				Full range†	-1.5 to 4	-11.5 to 14					
V _{OM+}	Maximum positive peak output voltage swing	R _L = 10 kΩ		25°C	3	4.3	13	14	V		
				0°C	3	4.2	13	14			
				70°C	3	4.3	13	14			
V _{OM-}	Maximum negative peak output voltage swing	R _L = 10 kΩ		25°C	-3	-4.2	-12.5	-13.9	V		
				0°C	-3	-4.1	-12.5	-13.9			
				70°C	-3	-4.2	-12.5	-14			
A _{VD}	Large-signal differential voltage amplification§	R _L = 10 kΩ		25°C	4	12	5	14.3	V/mV		
				0°C	3	11.1	4	13.5			
				70°C	4	13.3	5	15.2			
r _i	Input resistance			25°C	10 ¹²	10 ¹²	Ω				
c _i	Input capacitance			25°C	5	14	pF				
CMRR	Common-mode rejection ratio	V _{IC} = V _{ICRmin} , V _O = 0, R _S = 50 Ω		25°C	70	87	75	94	dB		
				0°C	70	87	75	94			
				70°C	70	87	75	94			
k _{SVR}	Supply-voltage rejection ratio (ΔV _{CC±} /ΔV _{IO})	V _{CC±} = ±5 V to ±15 V, V _O = 0, R _S = 50 Ω		25°C	75	96	75	96	dB		
				0°C	75	96	75	96			
				70°C	75	96	75	96			

† Full range is 0°C to 70°C.

‡ Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at T_A = 150°C extrapolated to T_A = 25°C using the Arrhenius equation and assuming an activation energy of 0.96 eV.

§ At V_{CC±} = ±5 V, V_O = 2.3 V; at V_{CC±} = ±15 V, V_O = ±10 V



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TL032C and TL032AC electrical characteristics at specified free-air temperature (continued)

PARAMETER	TEST CONDITIONS	T _A	TL032C, TL032AC						UNIT
			V _{CC±} = ±5 V			V _{CC±} = ±15 V			
			MIN	TYP	MAX	MIN	TYP	MAX	
P _D Total power dissipation (two amplifiers)	V _O = 0, No load	25°C		3.8	5		13	17	mW
		0°C		3.7	5		12.7	17	
		70°C		3.8	5		12.6	17	
I _{CC} Supply current (two amplifiers)	V _O = 0, No load	0°C		368	500		422	560	μA
		70°C		378	500		420	560	
V _{O1} /V _{O2} Crosstalk attenuation	A _{VD} = 100 dB	25°C		120			120		dB

TL032C and TL032AC operating characteristics at specified free-air temperature

PARAMETER		TEST CONDITIONS		T _A	TL032C, TL032AC						UNIT	
					V _{CC±} = ±5 V			V _{CC±} = ±15 V				
					MIN	TYP	MAX	MIN	TYP	MAX		
SR+	Positive slew rate at unity gain†	R _L = 10 kΩ, C _L = 100 pF See Figure 1	25°C	1.2			1.5 2.9			V/μs		
			0°C	1.8			1 2.6					
			70°C	2.2			1.5 3.2					
SR–	Negative slew rate at unity gain†	R _L = 10 kΩ, C _L = 100 pF See Figure 1	25°C	3.9			1.5 5.1			V/μs		
			0°C	3.7			1.5 5					
			70°C	4			1.5 5					
t _r	Rise time	V _{I(PP)} = ±10 V, R _L = 10 kΩ, C _L = 100 pF See Figures 1 and 2	25°C	138			132			ns		
			0°C	134			127					
			70°C	150			142					
t _f	Fall time	V _{I(PP)} = ±10 V, R _L = 10 kΩ, C _L = 100 pF See Figures 1 and 2	25°C	138			132			ns		
			0°C	134			127					
			70°C	150			142					
Overshoot factor			V _{I(PP)} = ±10 V, R _L = 10 kΩ, C _L = 100 pF See Figures 1 and 2	25°C	11%			5%				
				0°C	10%			4%				
				70°C	12%			6%				
V _n	Equivalent input noise voltage	TL032C	R _S = 20 Ω See Figure 3	f = 10 Hz	25°C	49			49			nV/√Hz
				f = 1 kHz		41			41			
		TL032AC		f = 10 Hz	25°C	49			49			
				f = 1 kHz		41			41 60			
I _n	Equivalent input noise current	f = 1 kHz		25°C	0.003			0.003			pA/√Hz	
B ₁	Unity-gain bandwidth	V _I = 10 mV, R _L = 10 kΩ, C _L = 25 pF See Figure 4	25°C	1			1.1			MHz		
			0°C	1			1.1					
			70°C	1			1					
φ _m	Phase margin at unity gain	V _I = 10 mV, R _L = 10 kΩ, C _L = 25 pF See Figure 4	25°C	61°			65°					
			0°C	61°			65°					
			70°C	60°			64°					

† For V_{CC±} = ±5 V, V_{I(PP)} = ±1 V; for V_{CC±} = ±15 V, V_{I(PP)} = ±5 V



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TL032I and TL032AI electrical characteristics at specified free-air temperature

PARAMETER	TEST CONDITIONS		T _A	TL032I, TL032AI						UNIT
				V _{CC±} = ±5 V			V _{CC±} = ±15 V			
				MIN	TYP	MAX	MIN	TYP	MAX	
V _{IO} Input offset voltage	V _O = 0, V _{IC} = 0, R _S = 50 Ω	TL032I	25°C	0.69	3.5	0.57		1.5	mV	
			Full range†	5.3		3.3				
		TL032AI	25°C	0.53	2.8	0.39		0.8		
			Full range†	4.6		2.6				
α _{V_{IO}} Temperature coefficient of input offset voltage	V _O = 0, V _{IC} = 0, R _S = 50 Ω	TL032I	25°C to 85°C	11.4		10.8		μV/°C		
		TL032AI	25°C to 85°C	11.4		10.8 25				
Input offset voltage long-term drift‡	V _O = 0, V _{IC} = 0, R _S = 50 Ω		25°C	0.04		0.04		μV/mo		
I _{IO} Input offset current	V _O = 0, See Figure 5	V _{IC} = 0	25°C	1	100	1	100	pA		
			85°C	0.02	0.45	0.02	0.45	nA		
I _{IB} Input bias current	V _O = 0, See Figure 5	V _{IC} = 0	25°C	2	200	2	200	pA		
			85°C	0.2	0.9	0.3	0.9	nA		
V _{ICR} Common-mode input voltage range			25°C	-1.5 to 4	-3.4 to 5.4	-11.5 to 14	-13.4 to 15.4	V		
			Full range†	-1.5 to 4		-11.5 to 14				
V _{OM+} Maximum positive peak output voltage swing	R _L = 10 kΩ		25°C	3	4.3	13	14	V		
			-40°C	3	4.2	13	14			
			85°C	3	4.4	13	14			
V _{OM-} Maximum negative peak output voltage swing	R _L = 10 kΩ		25°C	-3	-4.2	-12.5	-13.9	V		
			-40°C	-3	-4.1	-12.5	-13.8			
			85°C	-3	-4.2	-12.5	-14			
A _{VD} Large-signal differential voltage amplification§	R _L = 10 kΩ		-40°C	3	8.4	4	11.6	V/mV		
			85°C	4	13.5	5	15.3			
r _i Input resistance			25°C	10 ¹²		10 ¹²		Ω		
c _i Input capacitance			25°C	5		4		pF		
CMRR Common-mode rejection ratio	V _{IC} = V _{ICRmin} , V _O = 0, R _S = 50 Ω		25°C	70	87	75	94	dB		
			-40°C	70	87	75	94			
			85°C	70	87	75	94			
k _{SVR} Supply-voltage rejection ratio (ΔV _{CC±} /ΔV _{IO})	V _{CC±} = ±5 V to ±15 V, V _O = 0, R _S = 50 Ω		25°C	75	96	75	96	dB		
			-40°C	75	96	75	96			
			85°C	75	96	75	96			

† Full range is -40°C to 85°C.

‡ Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at T_A = 150°C extrapolated to T_A = 25°C using the Arrhenius equation and assuming an activation energy of 0.96 eV.

§ At V_{CC±} = ±5 V, V_O = 2.3 V; at V_{CC±} = ±15 V, V_O = ±10 V

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TL032I and TL032AI electrical characteristics at specified free-air temperature (continued)

PARAMETER	TEST CONDITIONS	T _A	TL032I, TL032AI						UNIT
			V _{CC±} = ±5 V			V _{CC±} = ±15 V			
			MIN	TYP	MAX	MIN	TYP	MAX	
P _D Total power dissipation (two amplifiers)	V _O = 0, No load	25°C		3.8	5		13	17	mW
		–40°C		2.9	5		10.9	17	
		85°C		3.7	5		12.4	17	
I _{CC} Supply current (two amplifiers)	V _O = 0, No load	25°C		384	500		434	560	μA
		–40°C		288	500		362	560	
		85°C		372	500		414	560	
V _{O1} /V _{O2} Crosstalk attenuation	A _{VD} = 100 dB	25°C		120			120		dB

TL032I and TL032AI operating characteristics at specified free-air temperature

PARAMETER		TEST CONDITIONS		T _A	TL032I, TL032AI						UNIT
					V _{CC±} = ±5 V			V _{CC±} = ±15 V			
					MIN	TYP	MAX	MIN	TYP	MAX	
SR+	Positive slew rate at unity gain†	R _L = 10 kΩ, C _L = 100 pF		25°C	2			1.5 2.9			V/μs
				−40°C	1.6			1 2.1			
				85°C	2.3			1.5 3.3			
SR−	Negative slew rate at unity gain†	R _L = 10 kΩ, C _L = 100 pF		25°C	3.9			1.5 5.1			V/μs
				−40°C	3.3			1.5 4.8			
				85°C	4.1			1.5 4.9			
t _r	Rise time	V _{I(PP)} = ±10 V, R _L = 10 kΩ, C _L = 100 pF See Figures 1 and 2		25°C	138			132			ns
				−40°C	132			123			
				85°C	154			146			
t _f	Fall time	V _{I(PP)} = ±10 V, R _L = 10 kΩ, C _L = 100 pF See Figure 1		25°C	138			132			ns
				−40°C	132			123			
				85°C	154			146			
Overshoot factor		V _{I(PP)} = ±10 V, R _L = 10 kΩ, C _L = 100 pF See Figures 1 and 2		25°C	11%			5%			
				−40°C	12%			5%			
				85°C	13%			7%			
V _n	Equivalent input noise voltage	TL032I	f = 10 Hz	25°C	49			49			nV/√Hz
			f = 1 kHz		41			41			
		TL032AI	f = 10 Hz	25°C	49			49			
			f = 1 kHz		41			41 60			
I _n	Equivalent input noise current	f = 1 kHz		25°C	0.003			0.003			pA/√Hz
B ₁	Unity-gain bandwidth	V _I = 10 mV, R _L = 10 kΩ, C _L = 25 pF See Figure 4		25°C	1			1.1			MHz
				−40°C	1			1.1			
				85°C	0.9			1			
φ _m	Phase margin at unity gain	V _I = 10 mV, R _L = 10 kΩ, C _L = 25 pF See Figure 4		25°C	61°			65°			
				−40°C	61°			65°			
				85°C	60°			64°			

† For $V_{CC\pm} = \pm 5 \text{ V}$, $V_{I(PP)} = \pm 1 \text{ V}$; for $V_{CC\pm} = \pm 15 \text{ V}$, $V_{I(PP)} = \pm 5 \text{ V}$



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TL032M and TL032AM electrical characteristics at specified free-air temperature

PARAMETER		TEST CONDITIONS		T _A	TL032M, TL032AM						UNIT
					V _{CC±} = ±5 V			V _{CC±} = ±15 V			
					MIN	TYP	MAX	MIN	TYP	MAX	
V _{IO}	Input offset voltage	V _O = 0, V _{IC} = 0, R _S = 50 Ω	TL032M	25°C	0.69	3.5		0.57	1.5	mV	
				Full range†		6.5		4.5			
			TL032AM	25°C	0.53	2.8		0.39	0.8		
				Full range†		5.8		3.8			
α _{V_{IO}}	Temperature coefficient of input offset voltage	V _O = 0, V _{IC} = 0, R _S = 50 Ω	TL032M	25°C to 125°C		9.7		9.7	μV/°C		
			TL032AM	25°C to 125°C		9.7		9.7			
	Input offset voltage long-term drift‡	V _O = 0, V _{IC} = 0, R _S = 50 Ω		25°C		0.04		0.04	μV/mo		
I _{IO}	Input offset current	V _O = 0, See Figure 5	V _{IC} = 0	25°C		1	100		1	100	pA
				125°C		0.2	10		0.2	10	nA
I _{IB}	Input bias current	V _O = 0, See Figure 5	V _{IC} = 0	25°C		2	200		2	200	pA
				125°C		7	20		8	20	nA
V _{ICR}	Common-mode input voltage range			25°C	-1.5 to 4	-3.4 to 5.4		-11.5 to 14	-13.4 to 15.4	V	
				Full range†	-1.5 to 4			-11.5 to 14			
V _{OM+}	Maximum positive peak output voltage swing	R _L = 10 kΩ		25°C	3	4.3		13	14	V	
				-55°C	3	4.1		13	14		
				125°C	3	4.4		13	14		
V _{OM-}	Maximum negative peak output voltage swing	R _L = 10 kΩ		25°C	-3	-4.2		-12.5	-13.9	V	
				-55°C	-3	-4		-12.5	-13.8		
				125°C	-3	-4.3		-12.5	-14		
A _{VD}	Large-signal differential voltage amplification§	R _L = 10 kΩ		25°C	4	12		5	14.3	V/mV	
				-55°C	3	7.1		4	10.4		
				125°C	3	12.9		4	15		
r _i	Input resistance			25°C		10 ¹²		10 ¹²	Ω		
c _i	Input capacitance			25°C		5		4	pF		
CMRR	Common-mode rejection ratio	V _{IC} = V _{ICR} min, V _O = 0, R _S = 50 Ω		25°C	70	87		75	94	dB	
				-55°C	70	87		70	94		
				125°C	70	87		70	94		
k _{SVR}	Supply-voltage rejection ratio (ΔV _{CC±} /ΔV _{IO})	V _{CC±} = ±5 V to ±15 V, V _O = 0, R _S = 50 Ω		25°C	75	96		75	96	dB	
				-55°C	75	95		75	95		
				125°C	75	96		75	96		

† Full range is -55°C to 125°C.

‡ Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at T_A = 150°C extrapolated to T_A = 25°C using the Arrhenius equation and assuming an activation energy of 0.96 eV.

§ At V_{CC±} = ±5 V, V_O = 2.3 V; at V_{CC±} = ±15 V, V_O = ±10 V

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TL032M and TL032AM electrical characteristics at specified free-air temperature (continued)

PARAMETER	TEST CONDITIONS	T _A	TL032M, TL032AM						UNIT
			V _{CC±} = ±5 V			V _{CC±} = ±15 V			
			MIN	TYP	MAX	MIN	TYP	MAX	
P _D Total power dissipation (two amplifiers) V _O = 0,	V _O = 0, No load	25°C		3.8	5		13	17	mW
		−55°C		2.3	5		9.4	17	
		125°C		3.6	5		11.8	17	
I _{CC} Supply current (two amplifiers)	V _O = 0, No load	25°C		384	500		434	560	μA
		−55°C		228	500		312	560	
		125°C		356	500		394	560	
V _{O1} /V _{O2} Crosstalk attenuation	A _{VD} = 100 dB	25°C		120			120		dB

TL032M and TL032AM operating characteristics at specified free-air temperature

PARAMETER		TEST CONDITIONS		T _A	TL032M, TL032AM						UNIT	
					V _{CC±} = ±5 V			V _{CC±} = ±15 V				
					MIN	TYP	MAX	MIN	TYP	MAX		
SR+	Positive slew rate at unity gain†	R _L = 10 kΩ, C _L = 100 pF See and Figure 1		25°C	2			1.5 2.9			V/μs	
				−55°C	1.4			1 1.9				
				125°C	2.4			1 3.5				
SR−	Negative slew rate at unity gain†	R _L = 10 kΩ, C _L = 100 pF See and Figure 1		25°C	3.9			1.5 5.1			V/μs	
				−55°C	3.2			1 4.6				
				125°C	4.1			1 4.7				
t _r	Rise time	V _{I(PP)} = ±10 V, R _L = 10 kΩ, C _L = 100 pF See Figures 1 and 2		25°C	138			132			ns	
				−55°C	142			123				
				125°C	166			58				
t _f	Fall time	V _{I(PP)} = ±10 V, R _L = 10 kΩ, C _L = 100 pF See Figure 1		25°C	138			132			ns	
				−55°C	142			123				
				125°C	166			158				
Overshoot factor		V _{I(PP)} = ±10 V, R _L = 10 kΩ, C _L = 100 pF See Figures 1 and 2		25°C	11%			5%				
				−55°C	16%			6%				
				125°C	14%			8%				
V _n	Equivalent input noise voltage	TL032M	R _S = 20 Ω See Figure 3	f = 10 Hz	25°C	49			49			nV/√Hz
				f = 1 kHz		41			41			
		TL032AM		f = 10 Hz	25°C	49			49			
				f = 1 kHz		41			41			
I _n	Equivalent input noise current	f = 1 kHz		25°C	0.003			0.003			pA/√Hz	
B1	Unity-gain bandwidth	V _I = 10 mV, R _L = 10 kΩ, C _L = 25 pF See Figure 4		25°C	1			1.1			MHz	
				−55°C	1			1.1				
				125°C	0.9			0.9				
φ _m	Phase margin at unity gain	V _I = 10 mV, R _L = 10 kΩ, C _L = 25 pF See Figure 4		25°C	61°			65°				
				−55°C	57°			64°				
				125°C	59°			62°				

† For $V_{CC\pm} = \pm 5\text{ V}$, $V_{I(PP)} = \pm 1\text{ V}$; for $V_{CC\pm} = \pm 15\text{ V}$, $V_{I(PP)} = \pm 5\text{ V}$



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TL034C and TL034AC electrical characteristics at specified free-air temperature

PARAMETER		TEST CONDITIONS		T _A	TL034C, TL034AC						UNIT
					V _{CC±} = ±5 V			V _{CC±} = ±15 V			
					MIN	TYP	MAX	MIN	TYP	MAX	
V _{IO}	Input offset voltage	V _O = 0, V _{IC} = 0, R _S = 50 Ω	TL034C	25°C	0.91		6	0.79		4	mV
				Full range†	8.2		6.2				
			TL034AC	25°C	0.7		3.5	0.58		1.5	
				Full range†	5.7		3.7				
α _{V_{IO}}	Temperature coefficient of input offset voltage	V _O = 0, V _{IC} = 0, R _S = 50 Ω	TL034C	25°C to 70°C	11.6		12			μV/°C	
			TL034AC	25°C to 70°C	11.6		12		25		
	Input offset voltage long-term drift‡	V _O = 0, V _{IC} = 0, R _S = 50 Ω		25°C	0.04		0.04			μV/mo	
I _{IO}	Input offset current	V _O = 0, V _{IC} = 0 See Figure 5		25°C	1	100	1		100	pA	
				70°C	9	200	12		200		
I _{IB}	Input bias current	V _O = 0, V _{IC} = 0 See Figure 5		25°C	2	200	2		200	pA	
				70°C	50	400	80		400		
V _{ICR}	Common-mode input voltage range			25°C	-1.5 to 4	-3.4 to 5.4	-11.5 to 14		-13.4 to 15.4	V	
				Full range†	-1.5 to 4	-11.5 to 14					
V _{OM+}	Maximum positive peak output voltage swing	R _L = 10 kΩ		25°C	3	4.3	13		14	V	
				0°C	3	4.2	13		14		
				70°C	3	4.3	13		14		
V _{OM-}	Maximum negative peak output voltage swing	R _L = 10 kΩ		25°C	-3	-4.2	-12.5		-13.9	V	
				0°C	-3	-4.1	-12.5		-13.9		
				70°C	-3	-4.2	-12.5		-14		
A _{VD}	Large-signal differential voltage amplification§	R _L = 10 kΩ		25°C	4	12	5		14.3	V/mV	
				0°C	3	11.1	4		13.5		
				70°C	4	13.3	5		15.2		
r _i	Input resistance			25°C	10 ¹²			10 ¹²		Ω	
c _i	Input capacitance			25°C	5			14		pF	
CMRR	Common-mode rejection ratio	V _{IC} = V _{ICRmin} , V _O = 0, R _S = 50 Ω		25°C	70	87	75		94	dB	
				0°C	70	87	75		94		
				70°C	70	87	75		94		
k _{SVR}	Supply-voltage rejection ratio (ΔV _{CC±} /ΔV _{IO})	V _O = 0, R _S = 50 Ω		25°C	75	96	75		96	dB	
				0°C	75	96	75		96		
				70°C	75	96	75		96		

† Full range is 0°C to 70°C.

‡ Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at T_A = 150°C extrapolated to T_A = 25°C using the Arrhenius equation and assuming an activation energy of 0.96 eV.

§ At V_{CC±} = ±5 V, V_O = ±2.3 V; at V_{CC±} = ±15 V, V_O = ±10 V

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TL034C and TL034AC electrical characteristics at specified free-air temperature (continued)

PARAMETER	TEST CONDITIONS	T _A	TL034C, TL034AC						UNIT
			V _{CC±} = ±5 V			V _{CC±} = ±15 V			
			MIN	TYP	MAX	MIN	TYP	MAX	
P _D Total power dissipation (two amplifiers)	V _O = 0, No load	25°C		7.7	10		26	34	mW
		0°C		7.4	10		25.3	34	
		70°C		7.6	10		25.2	34	
I _{CC} Supply current (four amplifiers)	V _O = 0, No load	25°C		0.77	1		0.87	1.12	mA
		0°C		0.74	1		0.85	1.12	
		70°C		0.76	1		0.84	1.12	
V _{O1} /V _{O2} Crosstalk attenuation	A _{VD} = 100	25°C		120			120		dB

TL034C and TL034AC operating characteristics at specified free-air temperature

PARAMETER		TEST CONDITIONS		T _A	TL034C, TL034AC						UNIT
					V _{CC±} = ±5 V			V _{CC±} = ±15 V			
					MIN	TYP	MAX	MIN	TYP	MAX	
SR+	Positive slew rate at unity gain†	R _L = 10 kΩ, C _L = 100 pF See Figure 1	25°C	2			1.5 2.9			V/μs	
			0°C	1.8			1 2.6				
			70°C	2.2			1.5 3.2				
SR–	Negative slew rate at unity gain†	R _L = 10 kΩ, C _L = 100 pF See Figure 1	25°C	3.9			1.5 5.1			V/μs	
			0°C	3.7			1.5 5				
			70°C	4			1.5 5				
t _r	Rise time	V _{I(PP)} = ±10 V, R _L = 10 kΩ, C _L = 100 pF See Figures 1 and 2	25°C	138			132			ns	
			0°C	134			127				
			70°C	150			142				
t _f	Fall time	V _{I(PP)} = ±10 V, R _L = 10 kΩ, C _L = 100 pF See Figure 1	25°C	138			132			ns	
			0°C	134			127				
			70°C	150			142				
Overshoot factor		V _{I(PP)} = ±10 V, R _L = 10 kΩ, C _L = 100 pF See Figures 1 and 2	25°C	11%			5%				
			0°C	10%			4%				
			70°C	12%			6%				
V _n	Equivalent input noise voltage	TL034C	f = 10 Hz	25°C	83			83			nV/√Hz
			f = 1 kHz		43			43			
		TL034AC	f = 10 Hz	25°C	83			83			
			f = 1 kHz		43			43 60			
I _n	Equivalent input noise current	f = 1 kHz		25°C	0.003			0.003			pA/√Hz
B ₁	Unity-gain bandwidth	V _I = 10 mV R _L = 10 kΩ, C _L = 25 pF See Figure 4	25°C	1			1.1			MHz	
			0°C	1			1.1				
			70°C	1			1				
φ _m	Phase margin at unity gain	V _I = 10 mV, R _L = 10 kΩ, C _L = 25 pF See Figure 4	25°C	61°			65°				
			0°C	61°			65°				
			70°C	60°			64°				

† For V_{CC±} = ±5 V, V_{I(PP)} = ±1 V; for V_{CC±} = ±15 V, V_{I(PP)} = ±5 V



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TL034I and TL034AI electrical characteristics at specified free-air temperature

PARAMETER		TEST CONDITIONS		T _A	TL034I, TL034AI						UNIT
					V _{CC±} = ±5 V			V _{CC±} = ±15 V			
					MIN	TYP	MAX	MIN	TYP	MAX	
V _{IO}	Input offset voltage	V _O = 0, V _{IC} = 0, R _S = 50 Ω	TL034I	25°C	0.91		3.6	0.79		4	mV
				Full range†			9.3	7.3			
			TL034AI	25°C	0.7		3.5	0.58		1.5	
				Full range†			6.8	4.8			
α _{V_{IO}}	Temperature coefficient of input offset voltage	V _O = 0, V _{IC} = 0, R _S = 50 Ω	TL034I	25°C to 85°C	11.5		11.6			μV/°C	
			TL034AI	25°C to 85°C	11.5		11.6		25		
	Input offset voltage long-term drift‡	V _O = 0, V _{IC} = 0, R _S = 50 Ω		25°C	0.04		0.04			μV/mo	
I _{IO}	Input offset current	V _O = 0, V _{IC} = 0 See Figure 5		25°C	1	100	1	100	pA		
				85°C	0.02	0.45	0.02	0.45	nA		
I _{IB}	Input bias current	V _O = 0, V _{IC} = 0 See Figure 5		25°C	2	200	2	200	pA		
				85°C	0.2	0.9	0.3	0.9	nA		
V _{ICR}	Common-mode input voltage range			25°C	-1.5 to 4	-3.4 to 5.4	-11.5 to 14	-13.4 to 15.4	V		
				Full range†	-1.5 to 4	-11.5 to 14					
V _{OM+}	Maximum positive peak output voltage swing	R _L = 10 kΩ		25°C	3	4.3	13	14	V		
				-40°C	3	4.1	13	14			
				85°C	3	4.4	13	14			
V _{OM-}	Maximum negative peak output voltage swing	R _L = 10 kΩ		25°C	-3	-4.2	-12.5	-13.9	V		
				-40°C	-3	-4.1	-12.5	-13.8			
				85°C	-3	-4.2	-12.5	-14			
A _{VD}	Large-signal differential voltage amplification§	R _L = 10 kΩ		-40°C	4	12	5	14.3	V/mV		
				85°C	3	8.4	4	11.6			
r _i	Input resistance			25°C	10 ¹²		10 ¹²		Ω		
c _i	Input capacitance			25°C	5		4		pF		
CMRR	Common-mode rejection ratio	V _{IC} = V _{ICRmin} , V _O = 0, R _S = 50 Ω		25°C	70	87	75	94	dB		
				-40°C	70	87	75	94			
				85°C	70	87	75	94			
k _{SVR}	Supply-voltage rejection ratio (ΔV _{CC±} / ΔV _{IO})	V _O = 0, R _S = 50 Ω		25°C	75	96	75	96	dB		
				-40°C	75	96	75	96			
				85°C	75	96	75	96			

† Full range is -40°C to 85°C.

‡ Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at T_A = 150°C extrapolated to T_A = 25°C using the Arrhenius equation and assuming an activation energy of 0.96 eV.

§ At V_{CC±} = ±5 V, V_O = ±2.3 V; at V_{CC±} = ±15 V, V_O = ±10 V

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TL034I and TL034AI electrical characteristics at specified free-air temperature (continued)

PARAMETER	TEST CONDITIONS	T _A	TL034I, TL034AI						UNIT
			V _{CC±} = ±5 V			V _{CC±} = ±15 V			
			MIN	TYP	MAX	MIN	TYP	MAX	
P _D Total power dissipation (four amplifiers)	V _O = 0, No load	25°C		7.7	10		26	34	mW
		−40°C		5.8	10		21.7	34	
		85°C		7.4	10		24.8	34	
I _{CC} Supply current (four amplifiers)	V _O = 0, No load	25°C		0.77	1		0.87	1.12	mA
		−40°C		0.58	1		0.72	1.12	
		85°C		0.74	1		0.83	1.12	
V _{O1} /V _{O2} Crosstalk attenuation	A _{VD} = 100	25°C		120			120		dB

TL034I and TL034AI operating characteristics

PARAMETER		TEST CONDITIONS		T _A	TL034I, TL034AI						UNIT
					V _{CC±} = ±5 V			V _{CC±} = ±15 V			
					MIN	TYP	MAX	MIN	TYP	MAX	
SR+	Positive slew rate at unity gain†	R _L = 10 kΩ, C _L = 100 pF See Figure 1	25°C	2			1.5 2.9			V/μs	
			−40°C	1.6			1 2.1				
			85°C	2.3			1.5 3.3				
SR−	Negative slew rate at unity gain†	R _L = 10 kΩ, C _L = 100 pF See Figure 1	25°C	3.9			1.5 5.1			V/μs	
			−40°C	3.3			1.5 4.8				
			85°C	4.1			1.5 4.9				
t _r	Rise time	V _{I(PP)} = ±10 V, R _L = 10 kΩ, C _L = 100 pF See Figures 1 and 2	25°C	138			132			ns	
			−40°C	132			123				
			85°C	154			146				
t _f	Fall time	V _{I(PP)} = ±10 V, R _L = 10 kΩ, C _L = 100 pF See Figures 1 and 2	25°C	138			132			ns	
			−40°C	132			123				
			85°C	154			146				
Overshoot factor			V _{I(PP)} = ±10 V, R _L = 10 kΩ, C _L = 100 pF See Figures 1 and 2	25°C	11%			5%			
				−40°C	12%			5%			
				85°C	13%			7%			
V _n	Equivalent input noise voltage	TL034I	f = 10 Hz	25°C	83			83			nV/√Hz
			f = 1 kHz		43			43			
		TL034AI	f = 10 Hz	25°C	83			83			
			f = 1 kHz		43			43 60			
I _n	Equivalent input noise current	f = 1 kHz		25°C	0.003			0.003			pA/√Hz
B ₁	Unity-gain bandwidth	V _I = 10 mV, R _L = 10 kΩ, C _L = 25 pF See Figure 4	25°C	1			1.1			MHz	
			−40°C	1			1.1				
			85°C	0.9			1				
φ _m	Phase margin at unity gain	V _I = 10 mV, R _L = 10 kΩ, C _L = 25 pF See Figure 4	25°C	61°			65°				
			−40°C	61°			65°				
			85°C	60°			64°				

† For V_{CC±} = ±5 V, V_{I(PP)} = ±1 V; for V_{CC±} = ±15 V, V_{I(PP)} = ±5 V



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TL034M and TL034AM electrical characteristics at specified free-air temperature

PARAMETER		TEST CONDITIONS		T _A	TL034M, TL034AM						UNIT
					V _{CC±} = ±5 V			V _{CC±} = ±15 V			
					MIN	TYP	MAX	MIN	TYP	MAX	
V _{IO}	Input offset voltage	V _O = 0, V _{IC} = 0, R _S = 50 Ω	TL034M	25°C	0.91	3.6	0.78	4	mV		
				Full range†	11		9				
			TL034AM	25°C	0.7	3.5	0.58	1.5			
				Full range†	8.5		6.5				
α _{V_{IO}}	Temperature coefficient of input offset voltage	V _O = 0, V _{IC} = 0, R _S = 50 Ω	TL034M	25°C to 125°C	10.6		10.9		μV/°C		
			TL034AM	25°C to 125°C	10.6		10.9				
Input offset voltage long-term drift‡		V _O = 0, V _{IC} = 0, R _S = 50 Ω		25°C	0.04		0.04		μV/mo		
I _{IO}	Input offset current	V _O = 0, V _{IC} = 0 See Figure 5		25°C	1	100	1	100	pA		
				125°C	0.2	10	0.2	10	nA		
I _{IB}	Input bias current	V _O = 0, V _{IC} = 0 See Figure 5		25°C	2	200	2	200	pA		
				125°C	7	20	8	20	nA		
V _{ICR}	Common-mode input voltage range			25°C	-1.5 to 4	-3.4 to 5.4	-11.5 to 14	-13.4 to 15.4	V		
				Full range†	-1.5 to 4		-11.5 to 14				
V _{OM+}	Maximum positive peak output voltage swing	R _L = 10 kΩ		25°C	3	4.3	13	14	V		
				-55°C	3	4.1	13	14			
				125°C	3	4.4	13	14			
V _{OM-}	Maximum negative peak output voltage swing	R _L = 10 kΩ		25°C	-3	-4.2	-12.5	-13.9	V		
				-55°C	-3	-4	-12.5	-13.8			
				125°C	-3	-4.3	-12.5	-14			
A _{VD}	Large-signal differential voltage amplification§	R _L = 10 kΩ		25°C	4	12	5	14.3	V/mV		
				-55°C	3	7.1	4	10.4			
				125°C	3	12.9	4	15			
r _i	Input resistance			25°C	10 ¹²			Ω			
c _i	Input capacitance			25°C	5			pF			
CMRR	Common-mode rejection ratio	V _{IC} = V _{ICRmin} , V _O = 0, R _S = 50 Ω		25°C	70	87	75	94	dB		
				-55°C	70	87	70	94			
				125°C	70	87	70	94			
k _{SVR}	Supply-voltage rejection ratio (ΔV _{CC±} /ΔV _{IO})	V _O = 0, R _S = 50 Ω		25°C	75	96	75	96	dB		
				-55°C	75	95	75	95			
				125°C	75	96	75	96			

† Full range is -55°C to 125°C.

‡ Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at T_A = 150°C extrapolated to T_A = 25°C using the Arrhenius equation and assuming an activation energy of 0.96 eV.

§ At V_{CC±} = ±5 V, V_O = ±2.3 V; at V_{CC±} = ±15 V, V_O = ±10 V

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TL034M and TL034AM electrical characteristics at specified free-air temperature (continued)

PARAMETER	TEST CONDITIONS	T _A	TL034M, TL034AM						UNIT
			V _{CC±} = ±5 V			V _{CC±} = ±15 V			
			MIN	TYP	MAX	MIN	TYP	MAX	
P _D Total power dissipation (two amplifiers)	V _O = 0, No load	25°C		7.7	10		26	34	mW
		–55°C		4.6	12		18.7	45	
		125°C		7.1	12		23.6	45	
I _{CC} Supply current (two amplifiers)	V _O = 0, No load	25°C		0.77	1		0.87	1.12	mA
		–55°C		0.46	1.2		0.62	1.5	
		125°C		0.71	1.2		0.79	1.5	
V _{O1} /V _{O2} Crosstalk attenuation	A _{VD} = 100	25°C		120			120		dB

TL034M and TL034AM operating characteristics at specified free-air temperature

PARAMETER		TEST CONDITIONS		T _A	TL034M, TL034AM						UNIT	
					V _{CC±} = ±5 V			V _{CC±} = ±15 V				
					MIN	TYP	MAX	MIN	TYP	MAX		
SR+	Positive slew rate at unity gain†	R _L = 10 kΩ, C _L = 100 pF See Figure 1	25°C	2			1.5 2.9			V/μs		
			–55°C	1.4			1 1.9					
			125°C	2.4			1 3.5					
SR–	Negative slew rate at unity gain†	R _L = 10 kΩ, C _L = 100 pF See Figure 1	25°C	3.9			1.5 5.1			V/μs		
			–55°C	3.2			1 4.6					
			125°C	4.1			1 4.7					
t _r	Rise time	V _{I(PP)} = ±10 V, R _L = 10 kΩ, C _L = 100 pF See Figures 1 and 2	25°C	138			132			ns		
			–55°C	142			123					
			125°C	166			58					
t _f	Fall time	V _{I(PP)} = ±10 V, R _L = 10 kΩ, C _L = 100 pF See Figure 1	25°C	138			132			ns		
			–55°C	142			123					
			125°C	166			158					
Overshoot factor		V _{I(PP)} = ±10 V, R _L = 10 kΩ, C _L = 100 pF See Figures 1 and 2	25°C	11%			5%					
			–55°C	16%			6%					
			125°C	14%			8%					
V _n	Equivalent input noise voltage	TL034M	R _S = 20 Ω	f = 10 Hz	25°C	83			83			nV/√Hz
			See Figure 3	f = 1 kHz		43			43			
		TL034AM		f = 10 Hz	25°C	83			83			
				f = 1 kHz		43			43			
I _n	Equivalent input noise current	f = 1 kHz		25°C	0.003			0.003			pA/√Hz	
B1	Unity-gain bandwidth	V _I = 10 mV, R _L = 10 kΩ, C _L = 25 pF See Figure 4	25°C	1			1.1			MHz		
			–55°C	1			1.1					
			125°C	0.9			0.9					
φ _m	Phase margin at unity gain	V _I = 10 mV, R _L = 10 kΩ, C _L = 25 pF See Figure 4	25°C	61°			65°					
			–55°C	57°			64°					
			125°C	59°			62°					

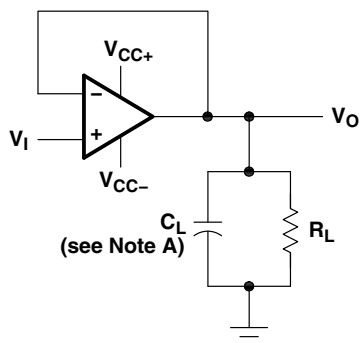
† For V_{CC±} = ±5 V, V_{I(PP)} = ±1 V; for V_{CC±} = ±15 V, V_{I(PP)} = ±5 V



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PARAMETER MEASUREMENT INFORMATION



NOTE A: C_L includes fixture capacitance.

Figure 1. Slew-Rate and Overshoot Test Circuit

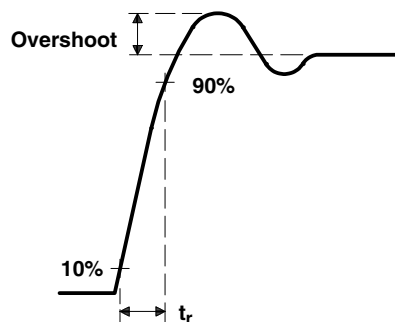


Figure 2. Rise Time and Overshoot Waveform

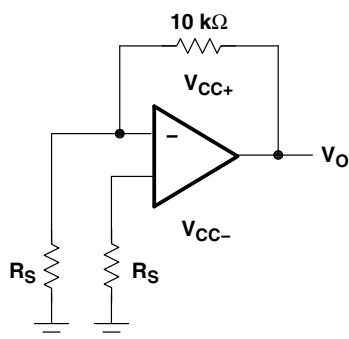
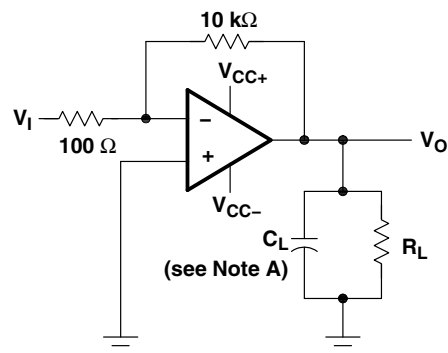


Figure 3. Noise-Voltage Test Circuit



NOTE A: C_L includes fixture capacitance.

Figure 4. Unity-Gain Bandwidth and Phase-Margin Test Circuit

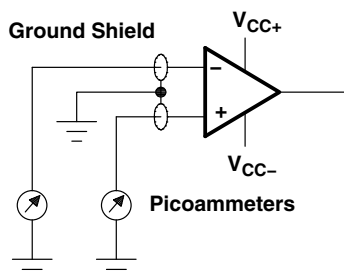


Figure 5. Input-Bias and Offset-Current Test Circuit

PARAMETER MEASUREMENT INFORMATION

typical values

Typical values presented in this data sheet represent the median (50% point) of device parametric performance.

input bias and offset current

At the picoampere bias current level typical of the TL03x and TL03xA, accurate measurement of the bias current becomes difficult. Not only does this measurement require a picoammeter, but test-socket leakages easily can exceed the actual device bias currents. To accurately measure these small currents, Texas Instruments uses a two-step process. The socket leakage is measured using picoammeters with bias voltages applied but with no device in the socket. The device is then inserted into the socket and a second test that measures both the socket leakage and the device input bias current is performed. The two measurements are then subtracted algebraically to determine the bias current of the device.

noise

With the increasing emphasis on low noise levels in many of today's applications, the input noise voltage density is performed at $f = 1$ kHz, unless otherwise noted.

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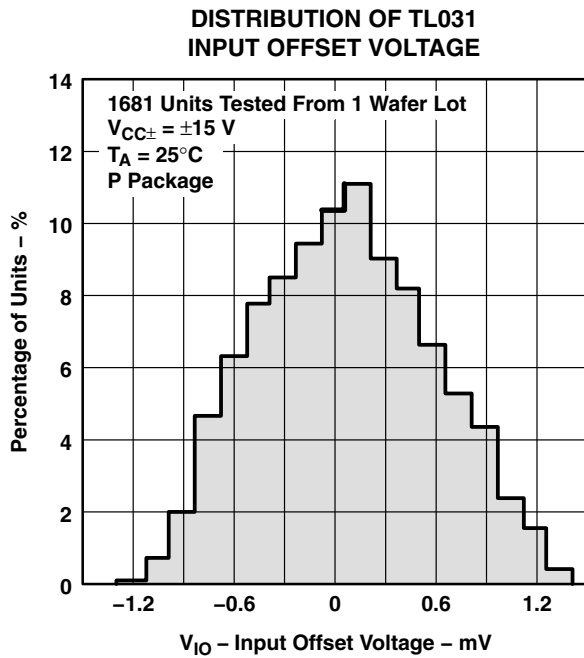


Figure 6

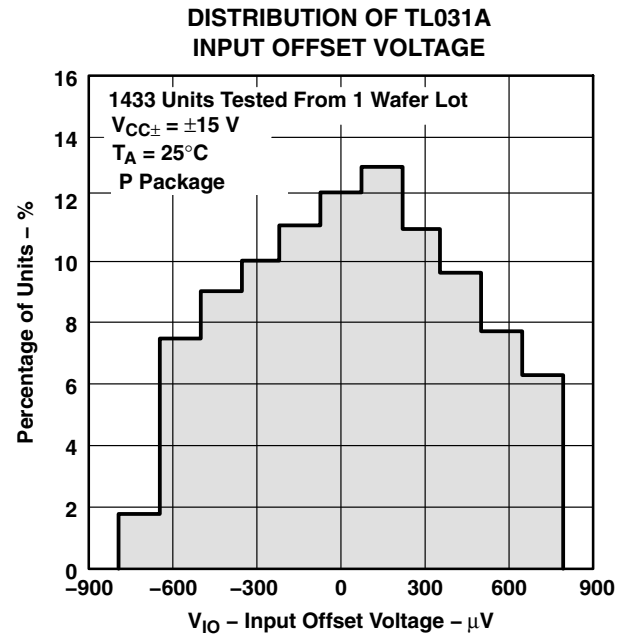


Figure 7

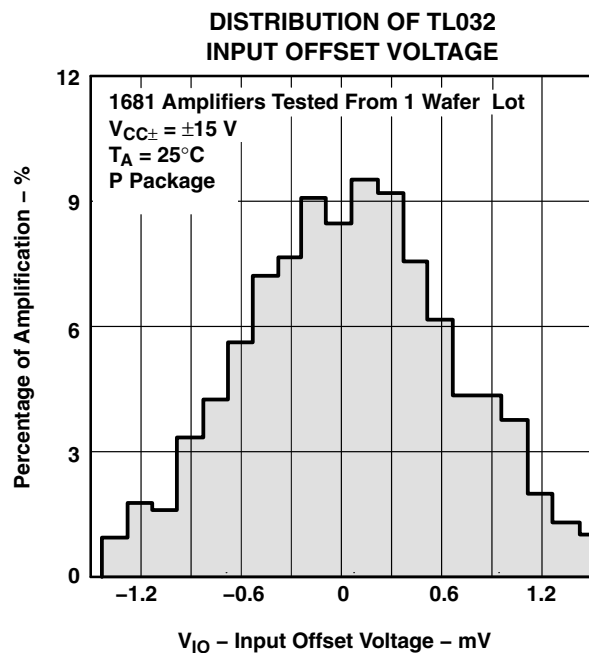


Figure 8

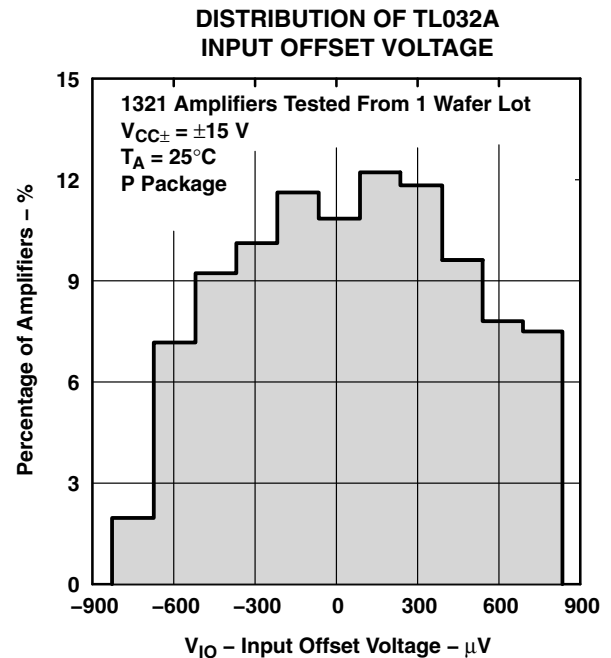


Figure 9

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**DISTRIBUTION OF TL034
INPUT OFFSET VOLTAGE**

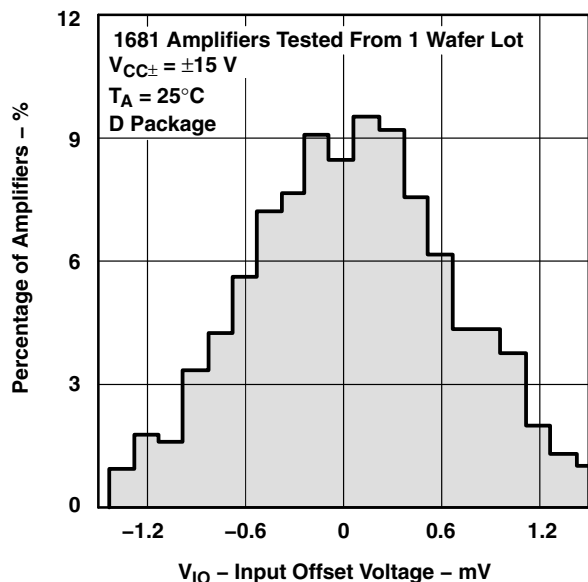


Figure 10

**DISTRIBUTION OF TL034A
INPUT OFFSET VOLTAGE**

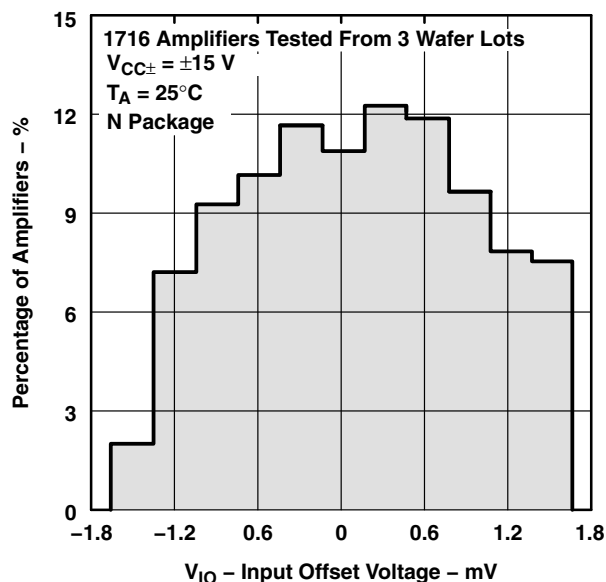


Figure 11

**DISTRIBUTION OF TL031
INPUT OFFSET-VOLTAGE
TEMPERATURE COEFFICIENT**

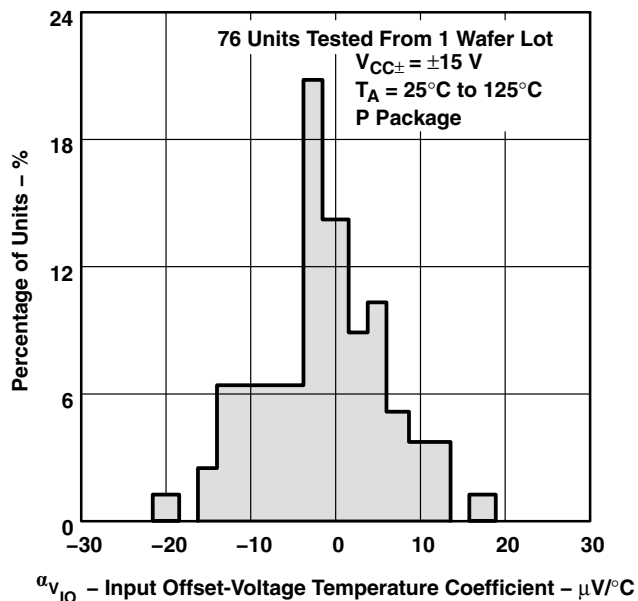


Figure 12

**DISTRIBUTION OF TL032
INPUT OFFSET-VOLTAGE
TEMPERATURE COEFFICIENT**

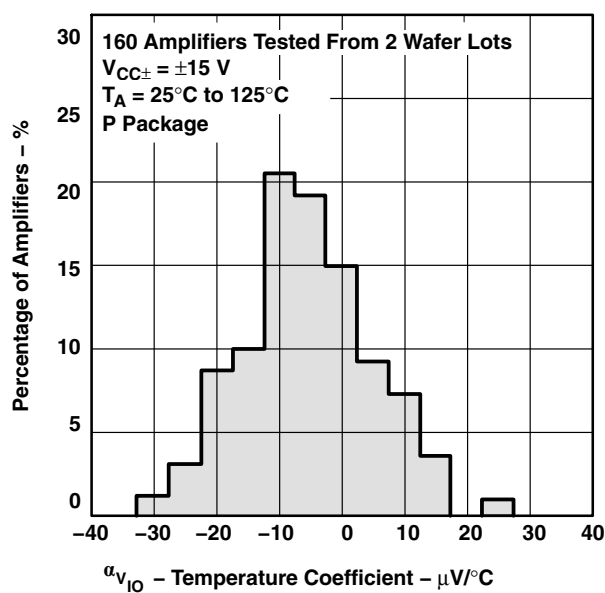


Figure 13

TYPICAL CHARACTERISTICS

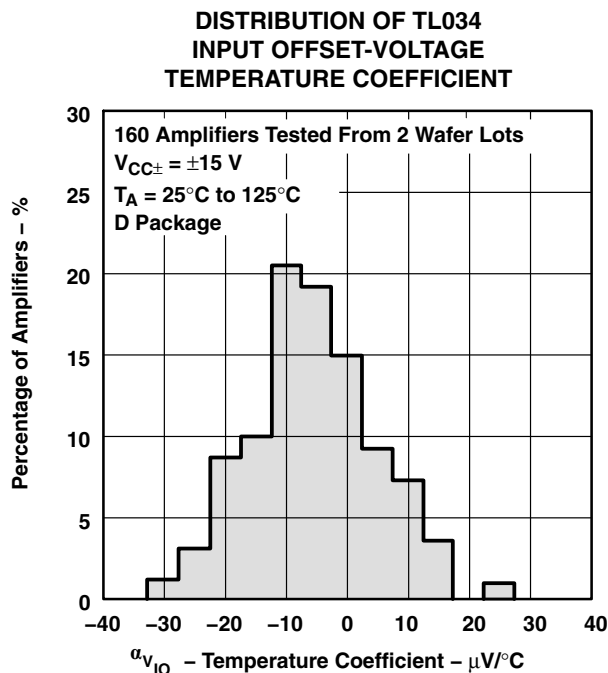


Figure 14

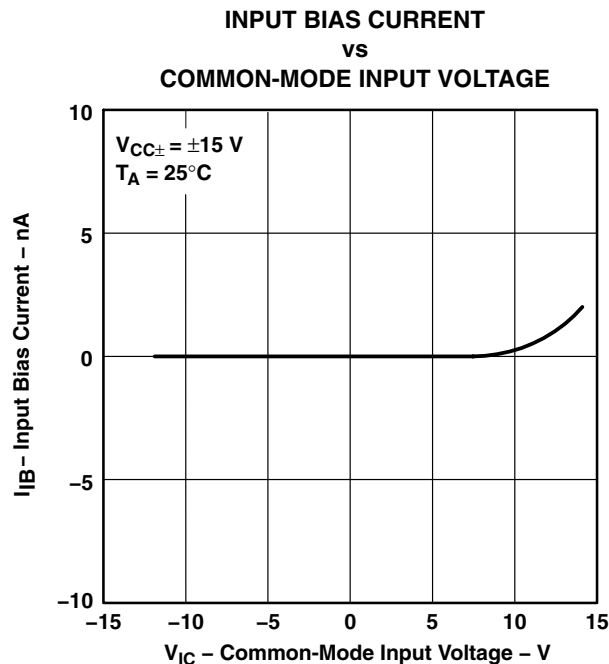


Figure 15

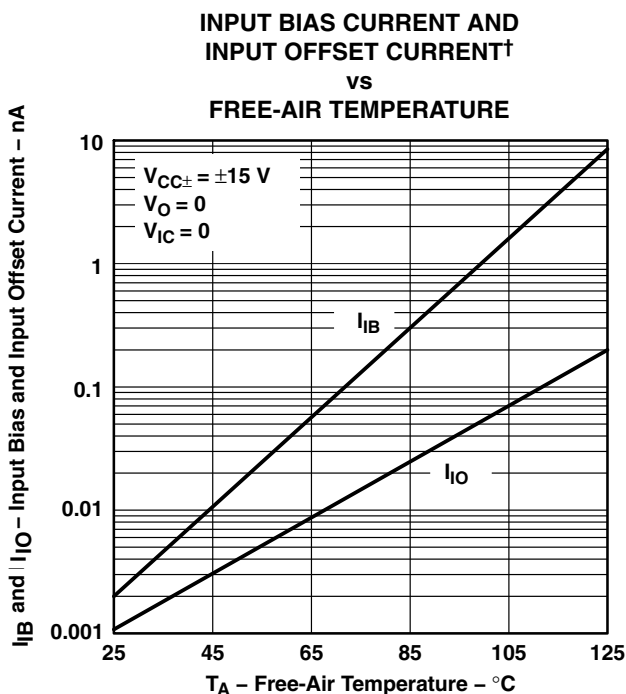


Figure 16

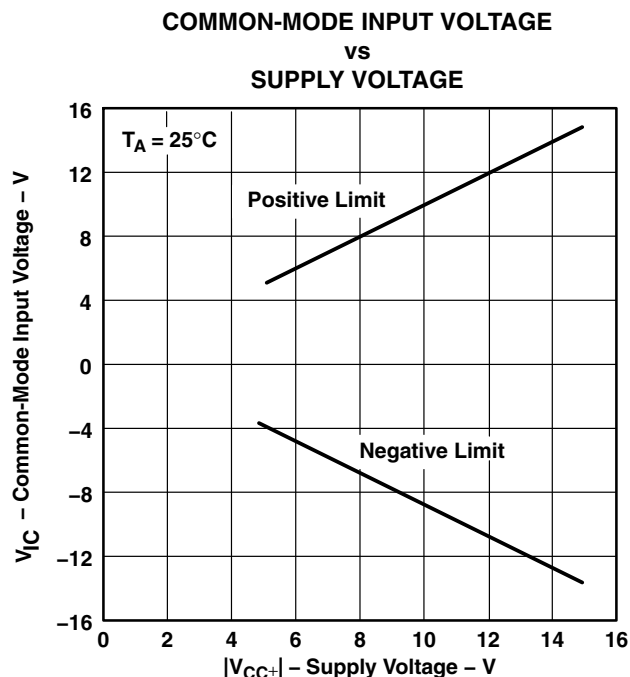


Figure 17

† Data at high and low temperatures are applicable only within the recommended operating free-air temperature ranges of the various devices.

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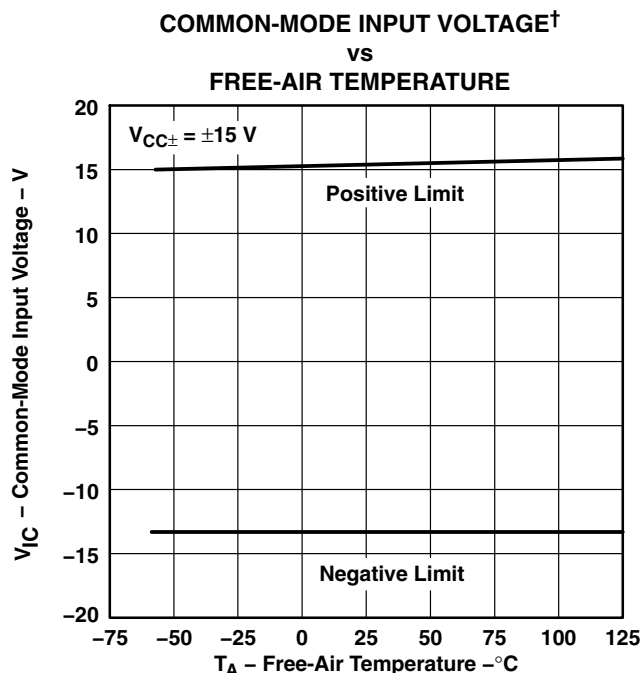


Figure 18

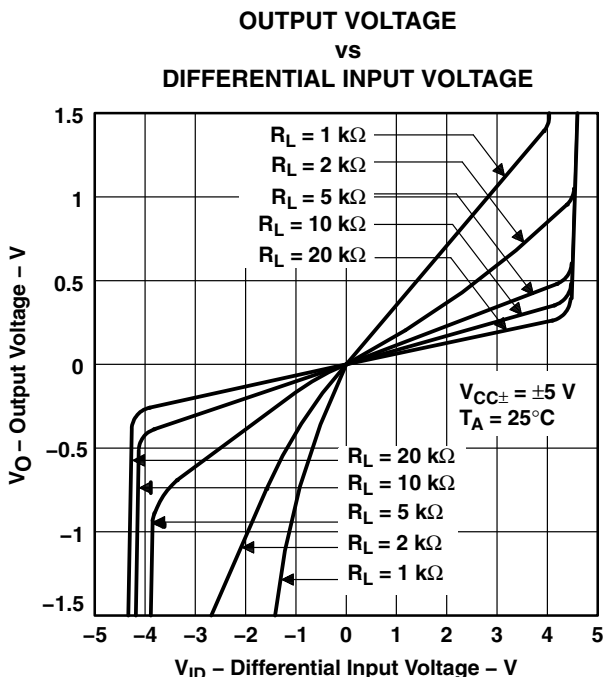


Figure 19

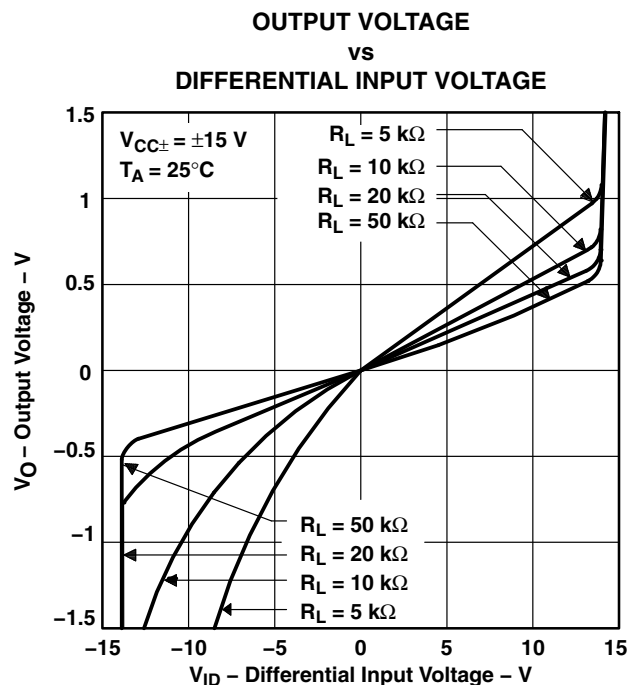


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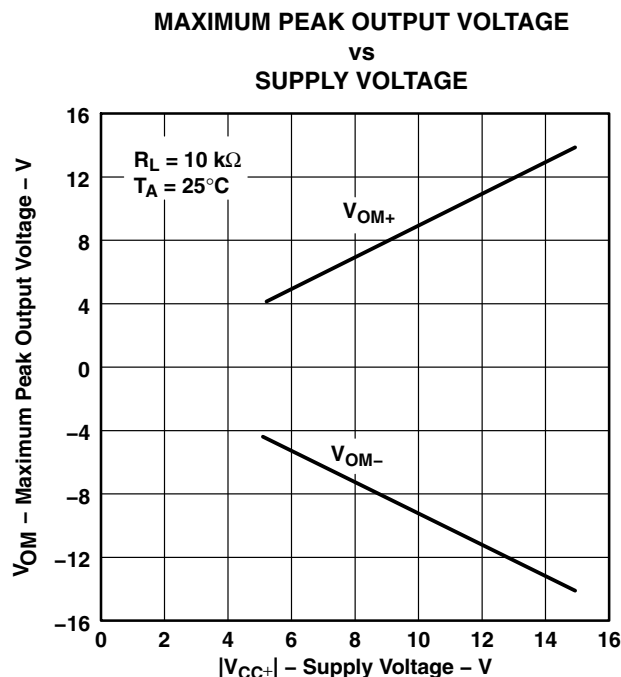


Figure 21

† Data at high and low temperatures are applicable only within the recommended operating free-air temperature ranges of the various devices.

TYPICAL CHARACTERISTICS

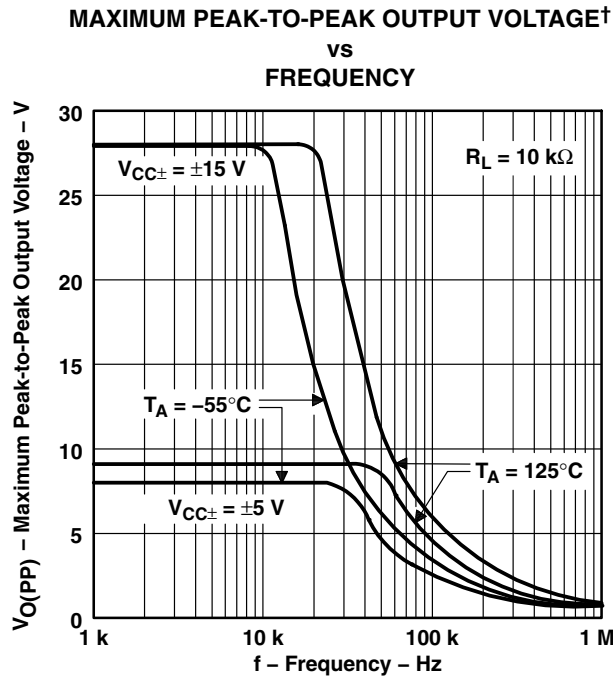


Figure 22

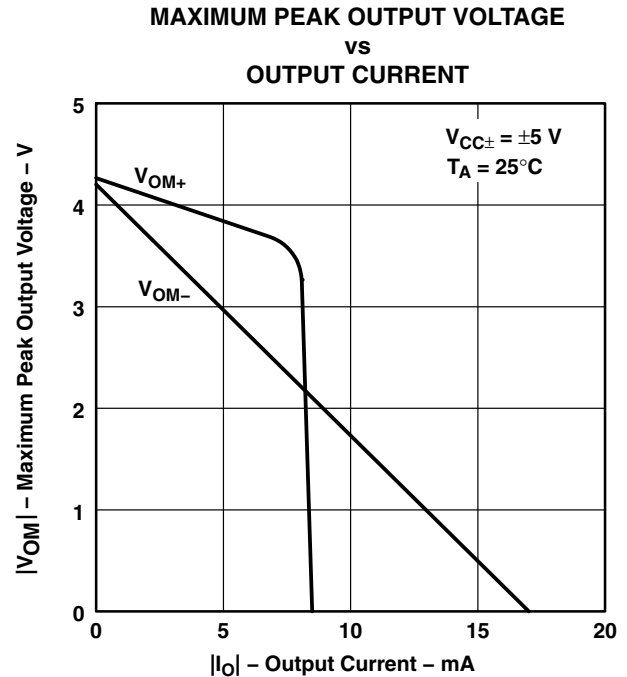


Figure 23

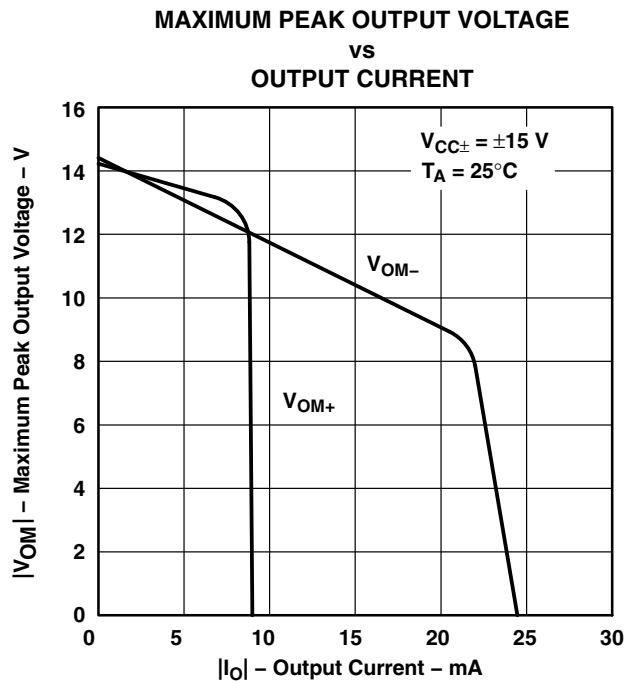


Figure 24

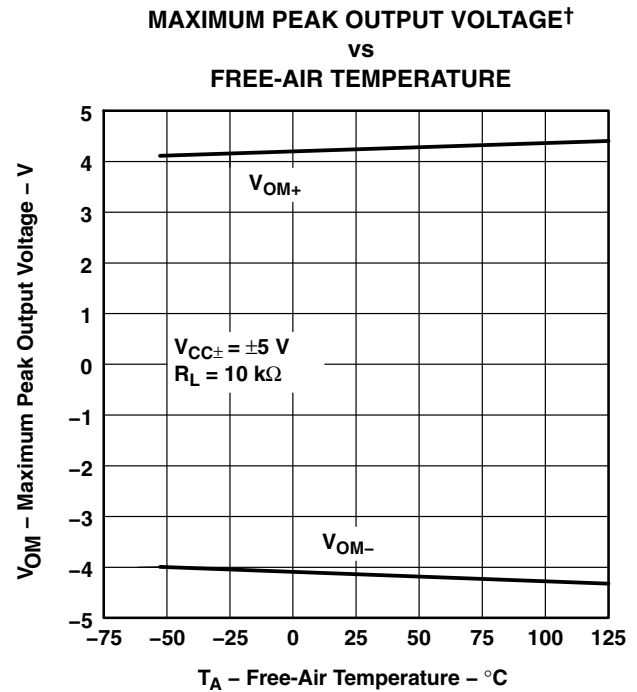


Figure 25

† Data at high and low temperatures are applicable only within the recommended operating free-air temperature ranges of the various devices.

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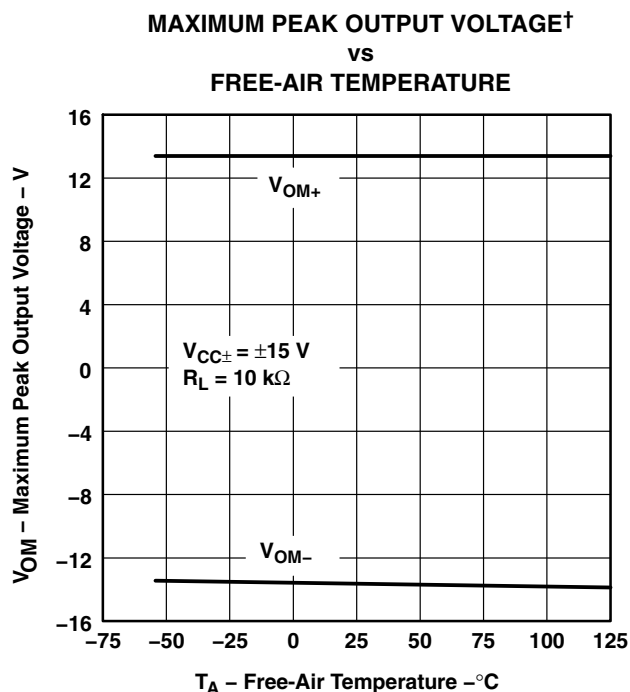


Figure 26

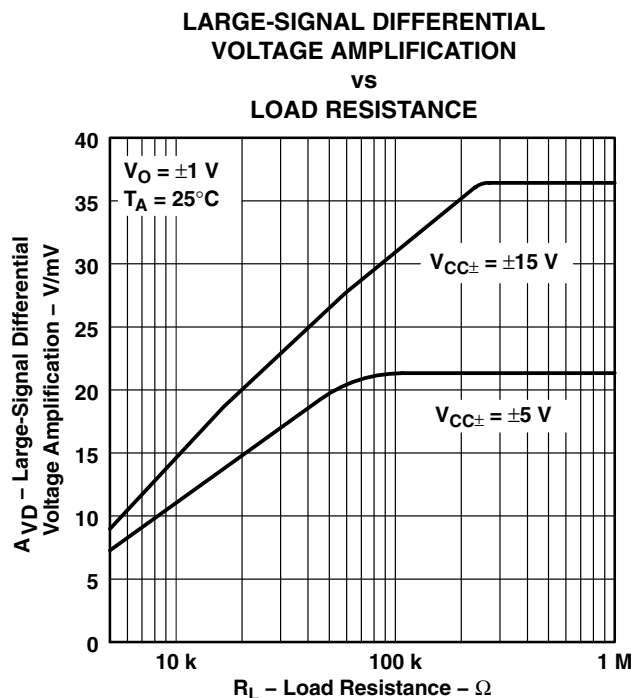


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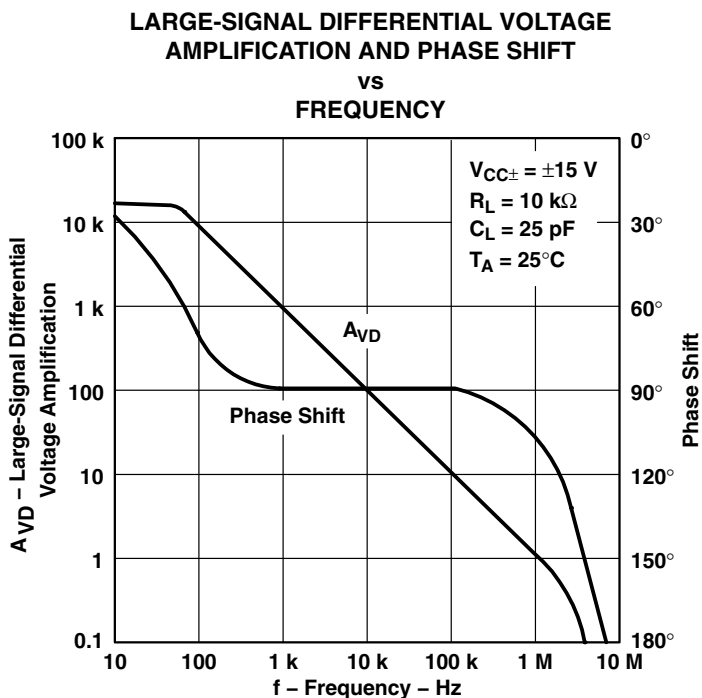


Figure 28

† Data at high and low temperatures are applicable only within the recommended operating free-air temperature ranges of the various devices.

TYPICAL CHARACTERISTICS

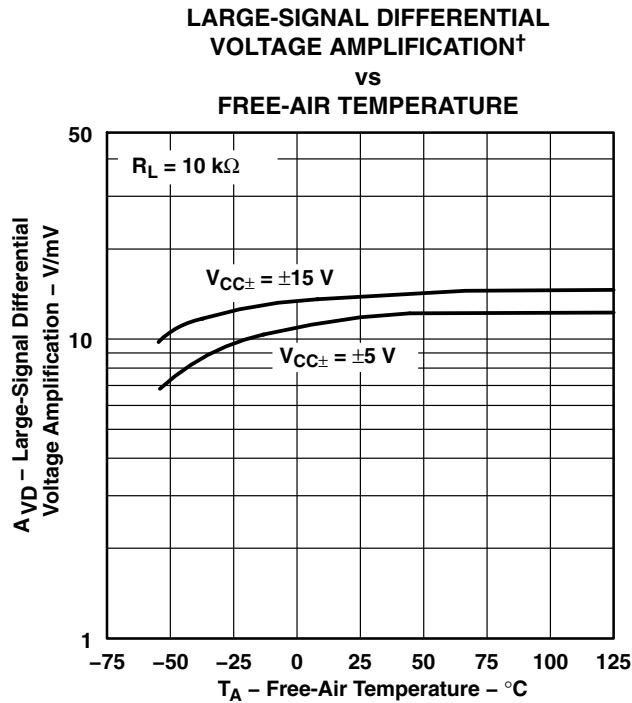


Figure 29

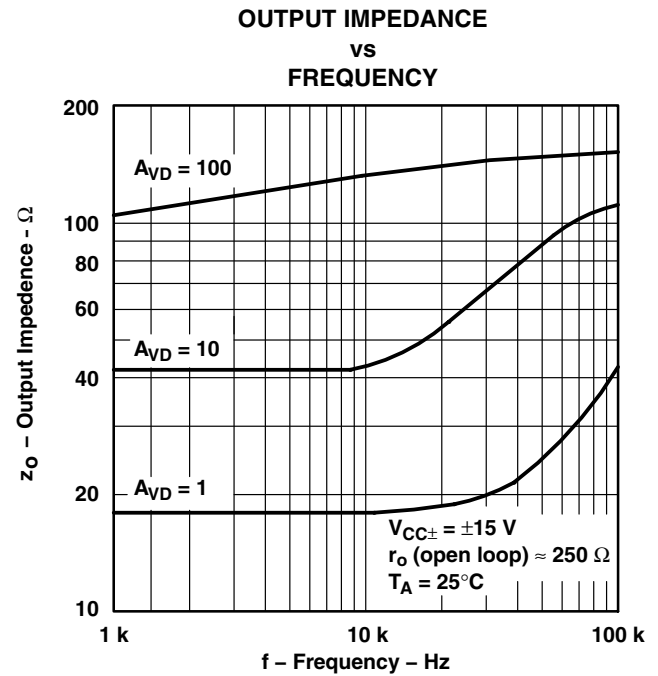


Figure 30

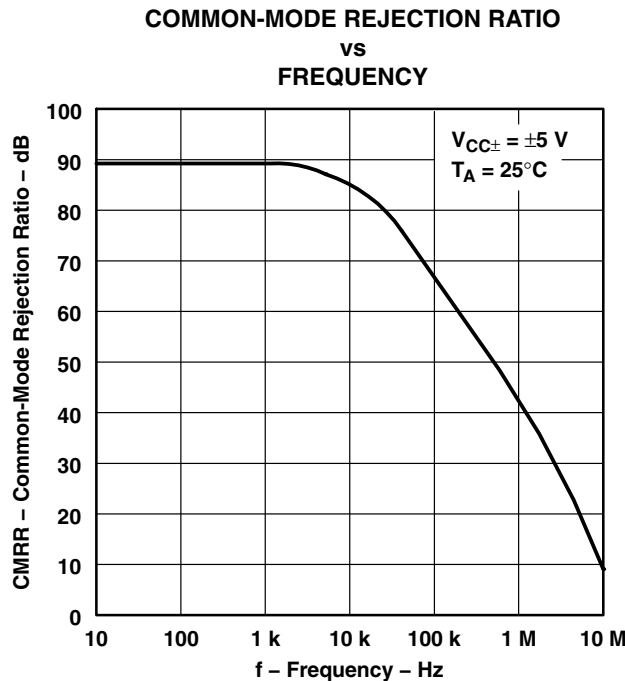


Figure 31

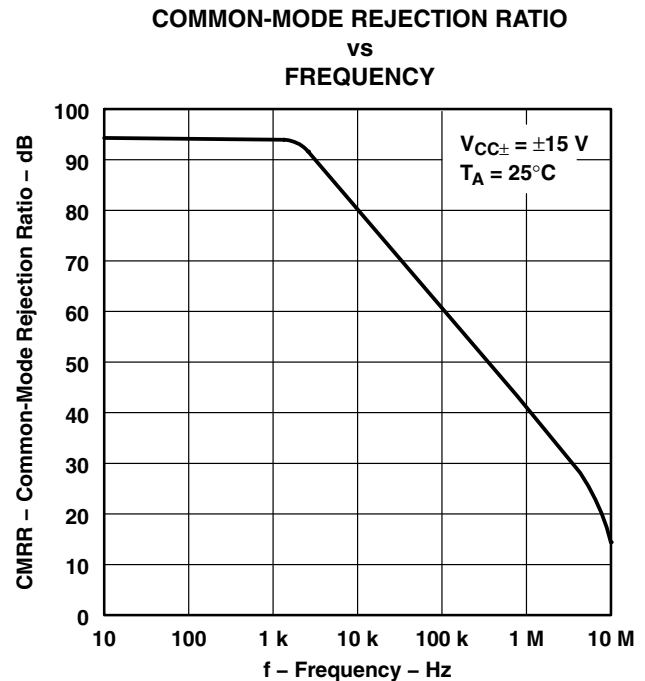


Figure 32

† Data at high and low temperatures are applicable only within the recommended operating free-air temperature ranges of the various devices.

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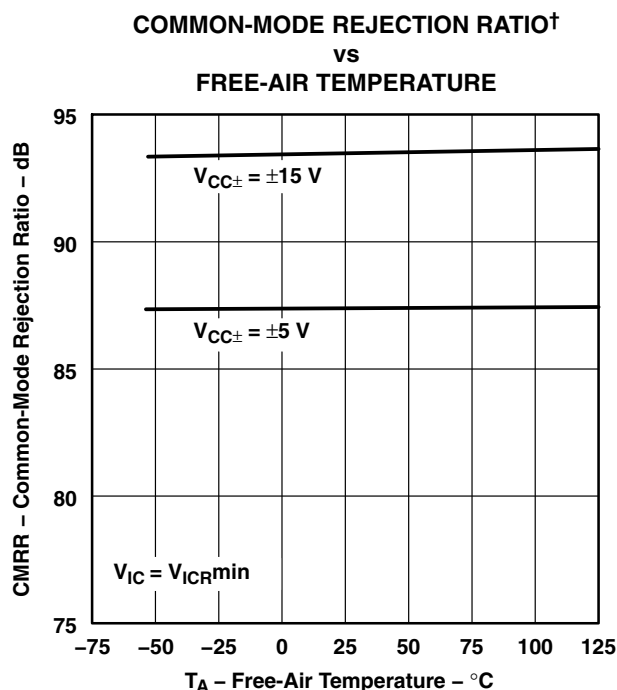


Figure 33

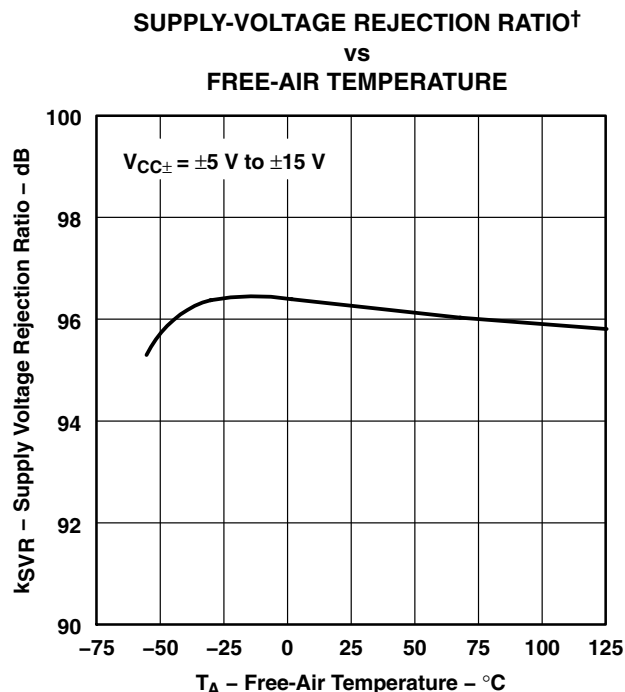


Figure 34

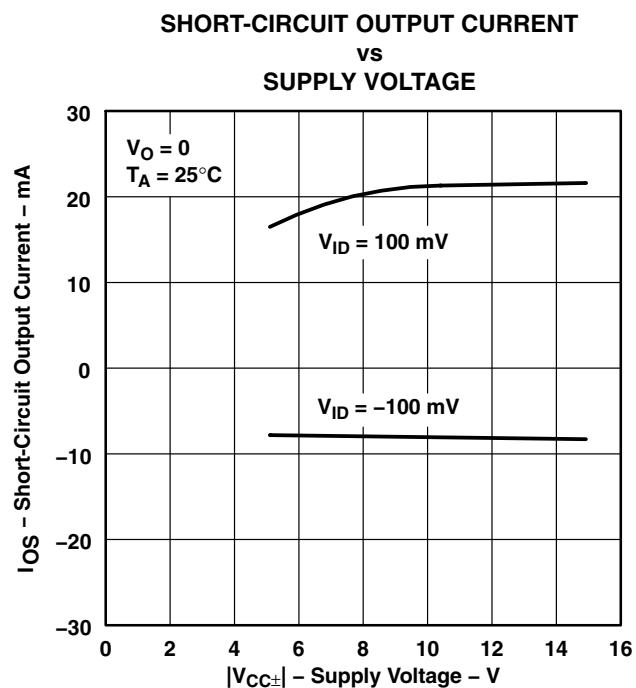


Figure 35

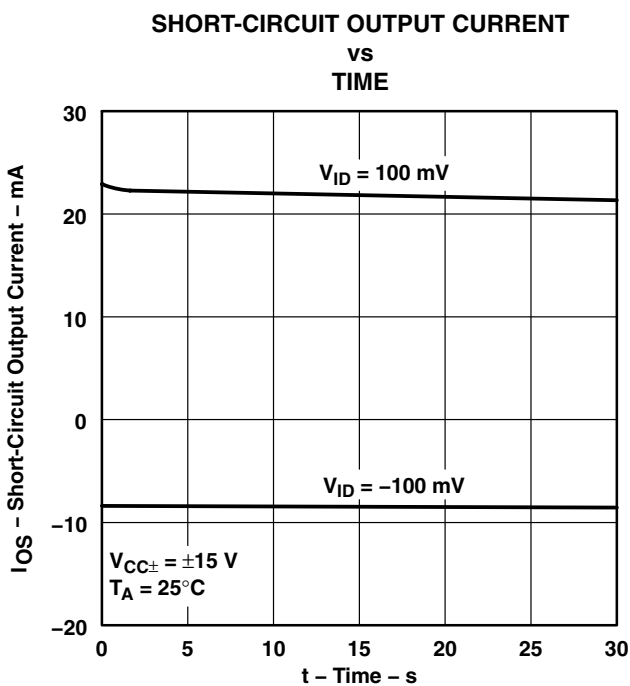


Figure 36

† Data at high and low temperatures are applicable only within the recommended operating free-air temperature ranges of the various devices.

TYPICAL CHARACTERISTICS

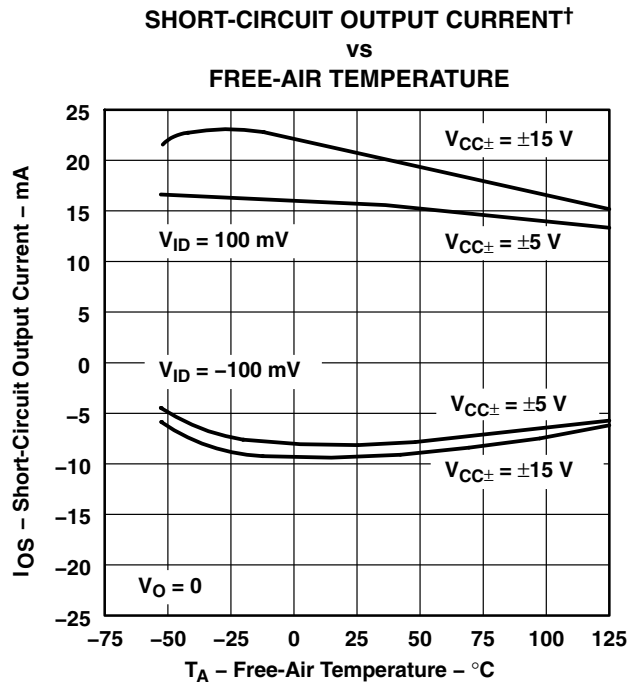


Figure 37

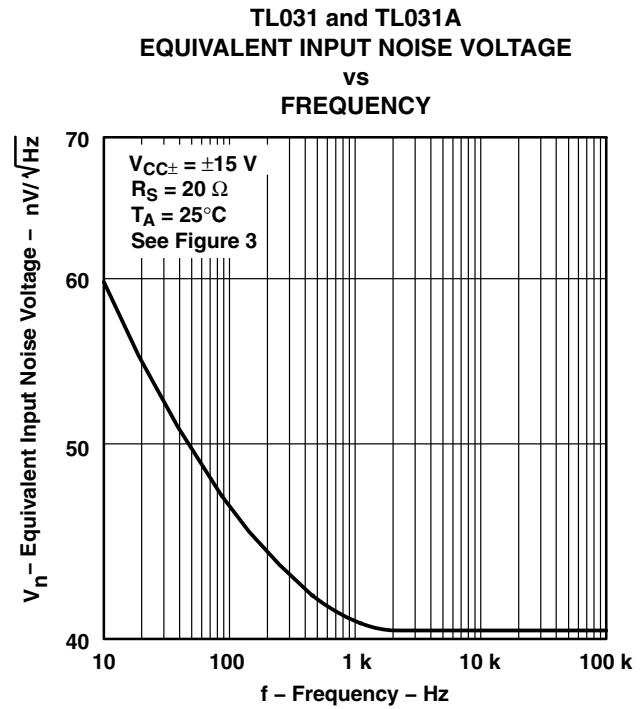


Figure 38

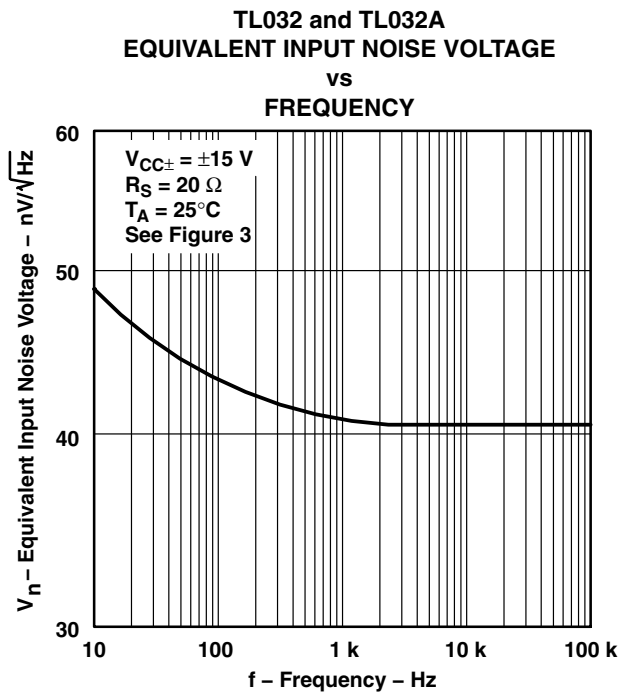


Figure 39

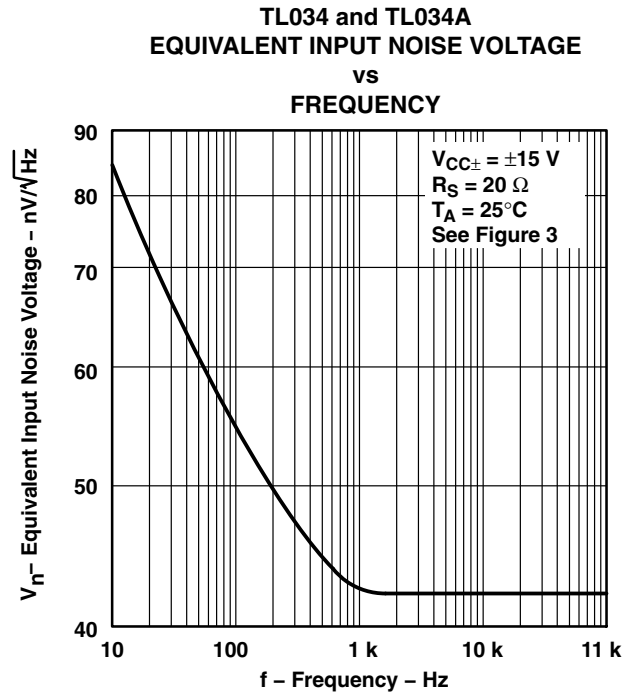


Figure 40

† Data at high and low temperatures are applicable only within the recommended operating free-air temperature ranges of the various devices.

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TL031 and TL031A
SUPPLY CURRENT†
vs
SUPPLY VOLTAGE

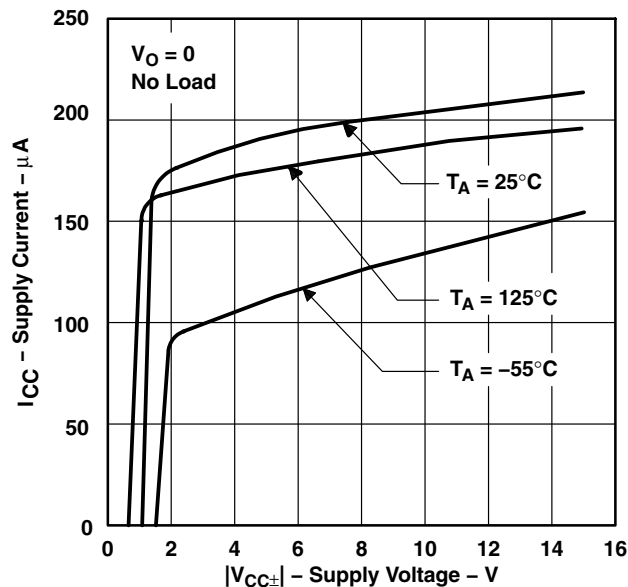


Figure 41

TL032 and TL032A
SUPPLY CURRENT†
vs
SUPPLY VOLTAGE

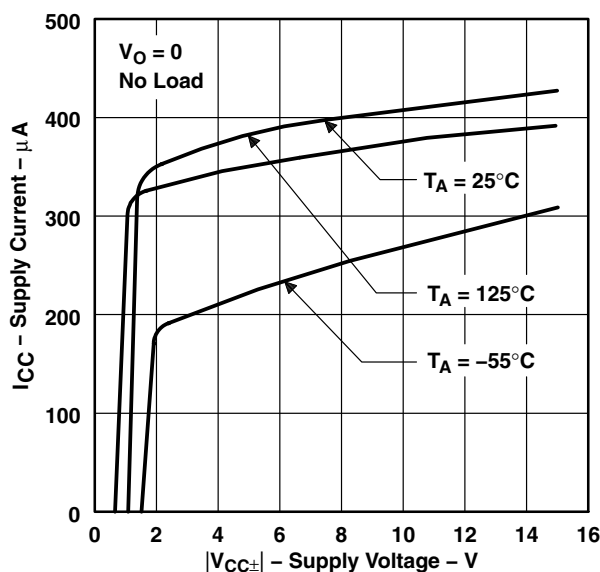


Figure 42

TL034 and TL034A
SUPPLY CURRENT†
vs
SUPPLY VOLTAGE

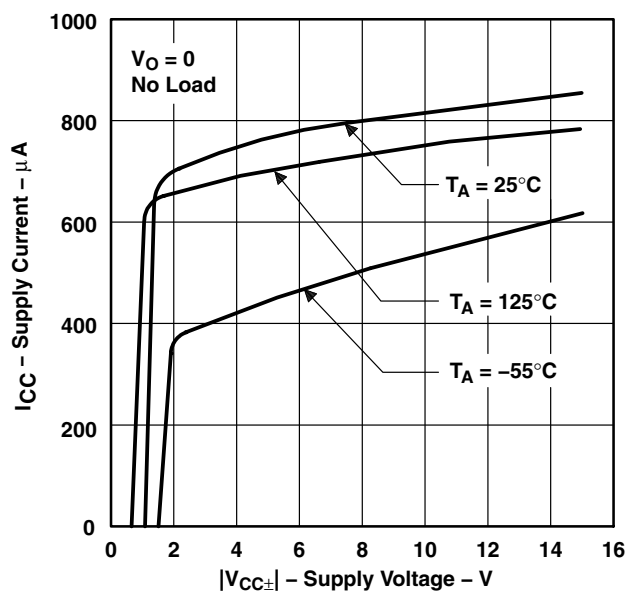


Figure 43

TL031 and TL031A
SUPPLY CURRENT†
vs
FREE-AIR TEMPERATURE

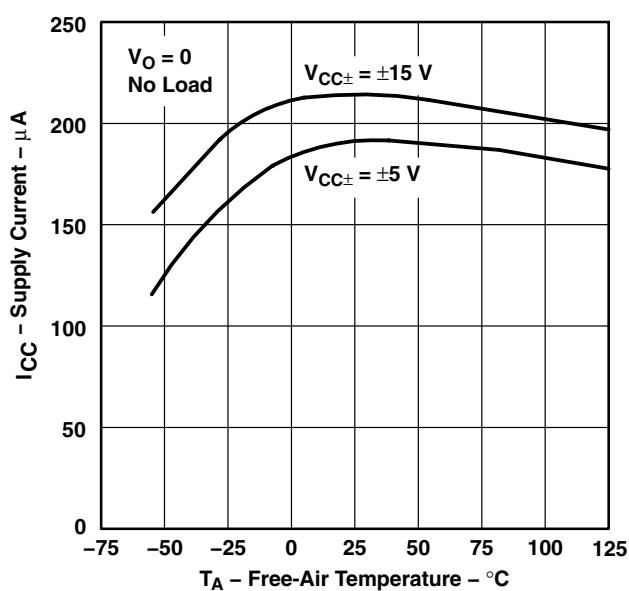
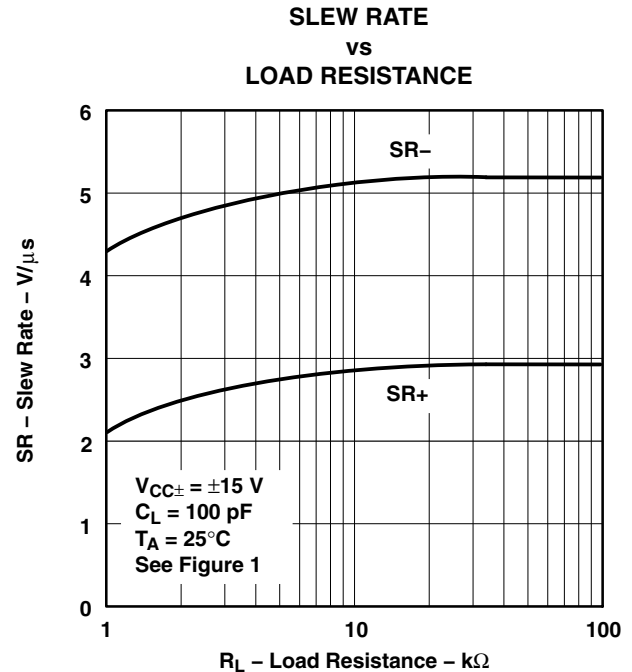
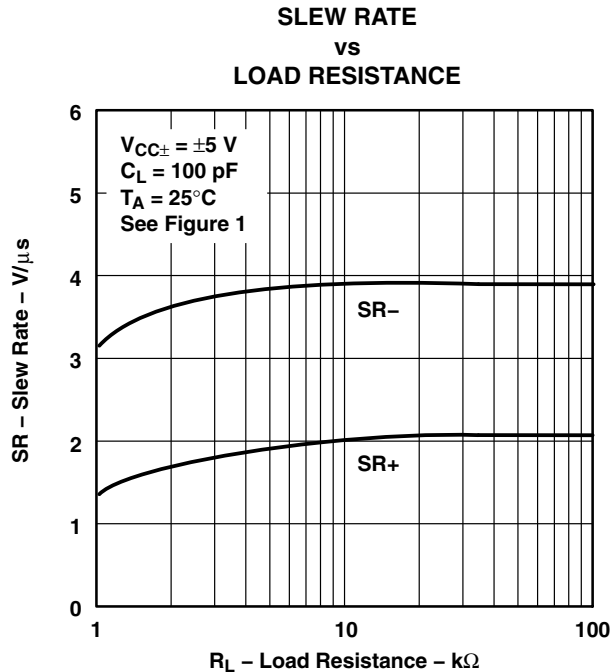
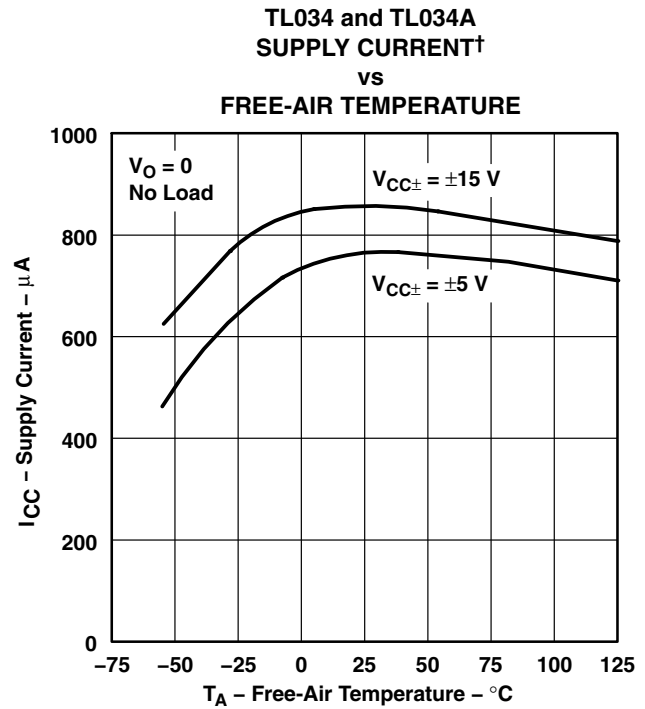
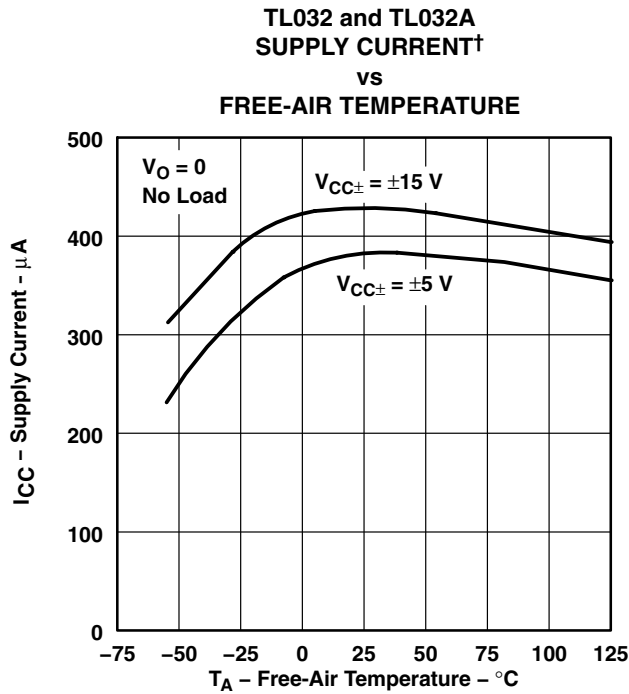


Figure 44

† Data at high and low temperatures are applicable only within the recommended operating free-air temperature ranges of the various devices.

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† Data at high and low temperatures are applicable only within the recommended operating free-air temperature ranges of the various devices.

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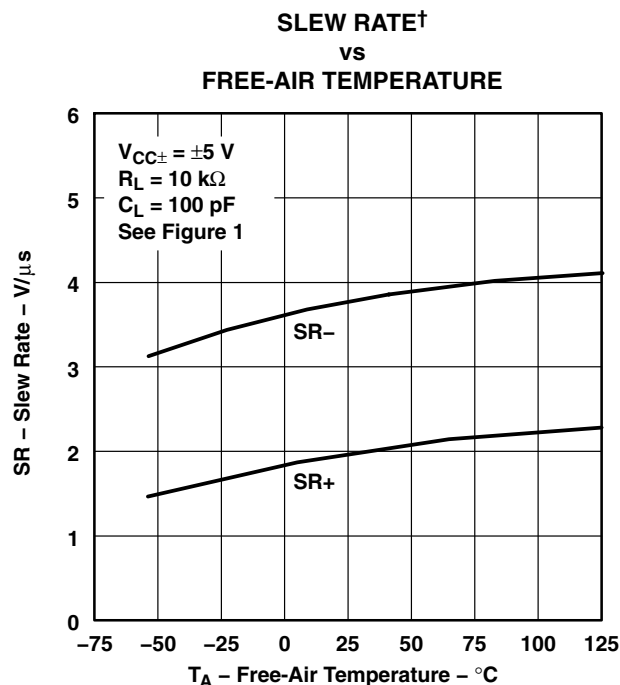


Figure 49

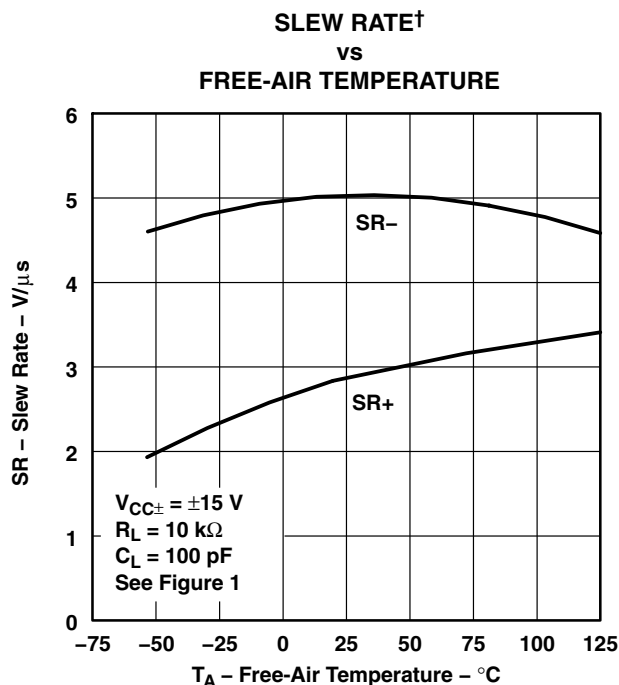


Figure 50

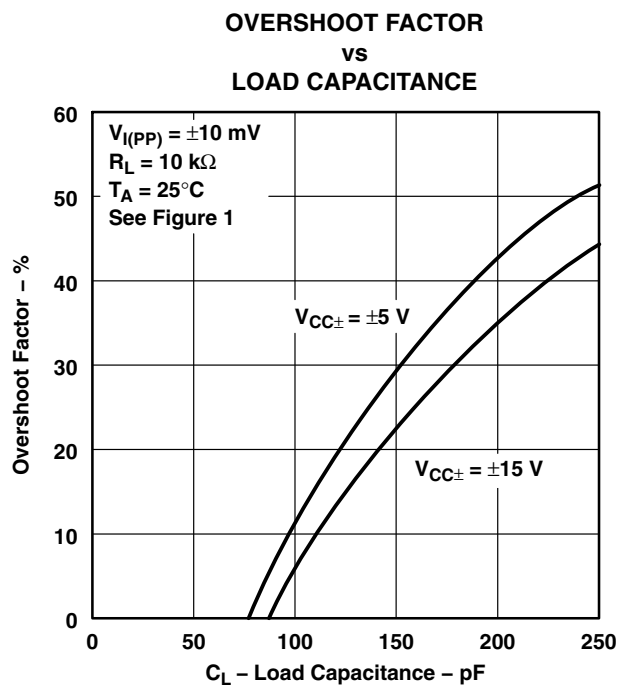


Figure 51

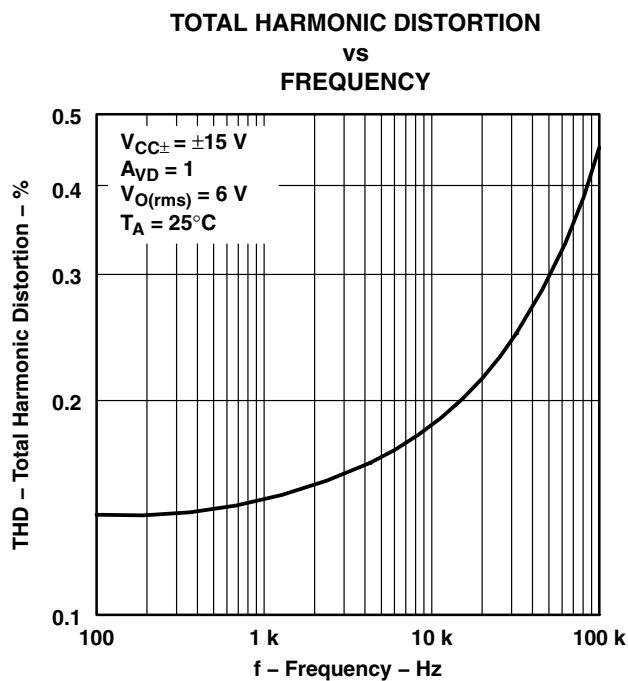


Figure 52

† Data at high and low temperatures are applicable only within the recommended operating free-air temperature ranges of the various devices.

TYPICAL CHARACTERISTICS

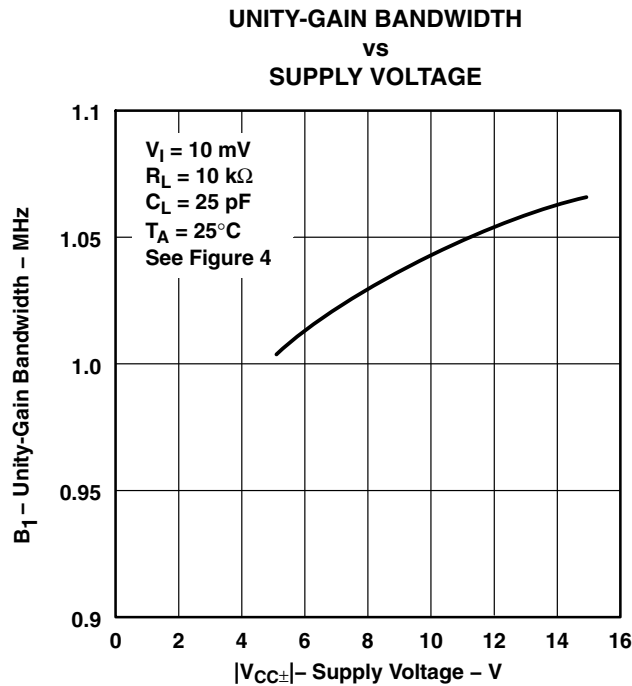


Figure 53

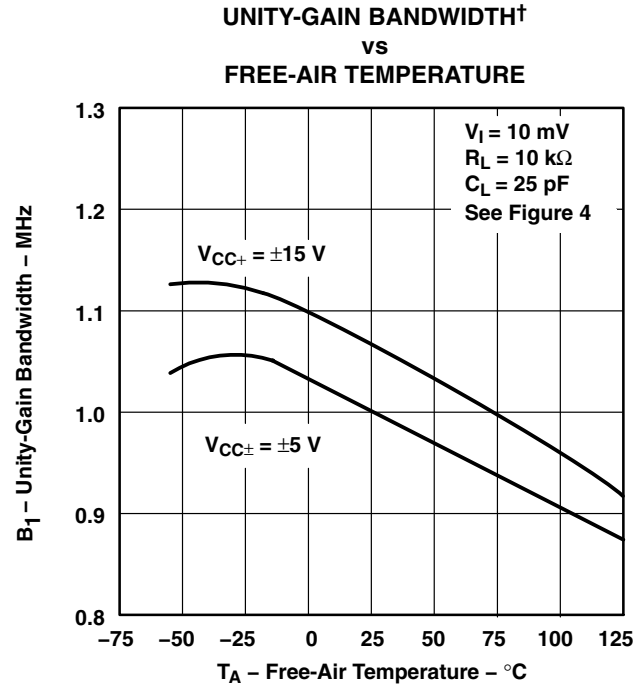


Figure 54

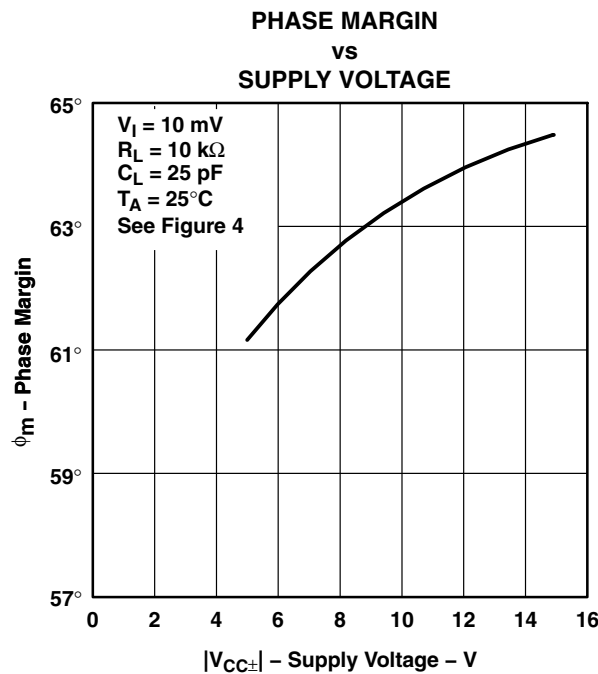
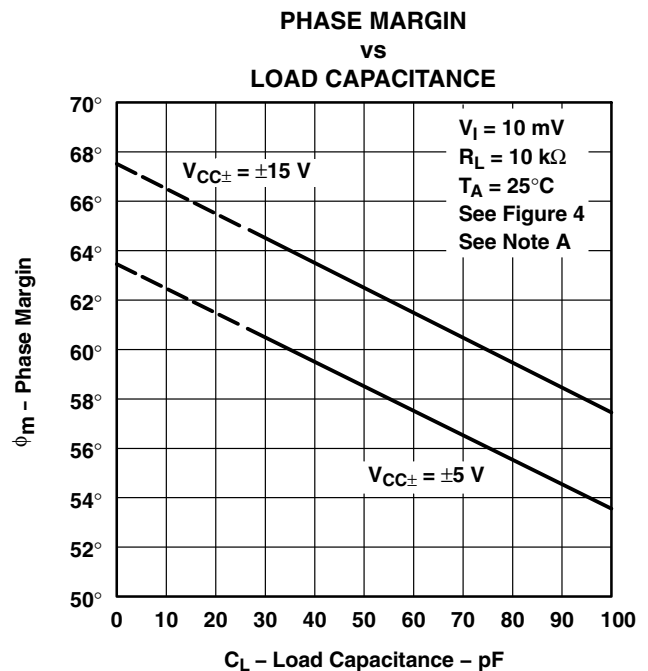


Figure 55



NOTE A: Values of phase margin below a load capacitance of 25 pF were estimated.

Figure 56

† Data at high and low temperatures are applicable only within the recommended operating free-air temperature ranges of the various devices.

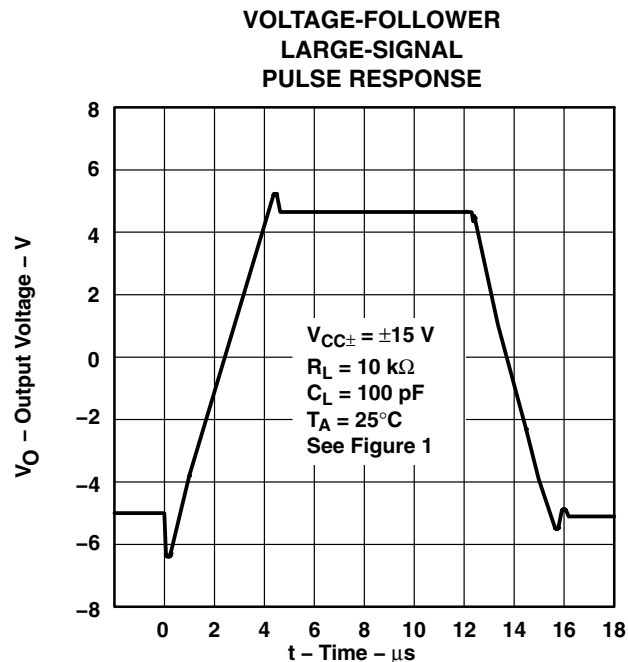
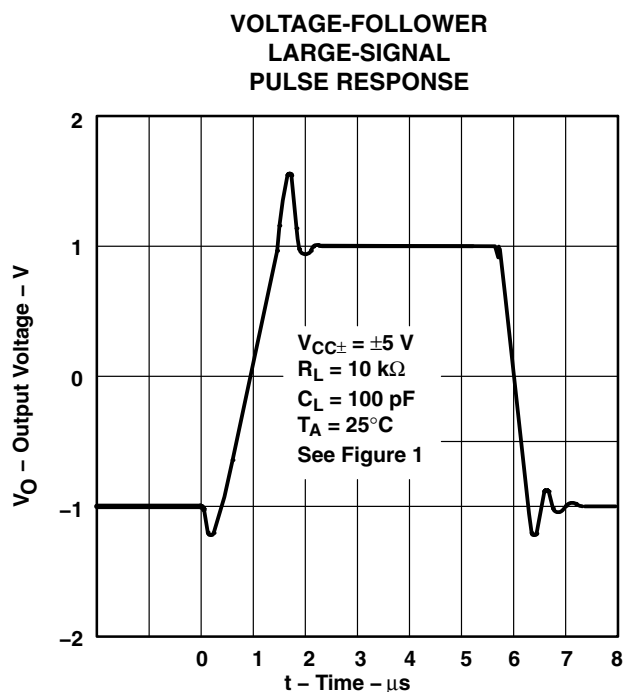
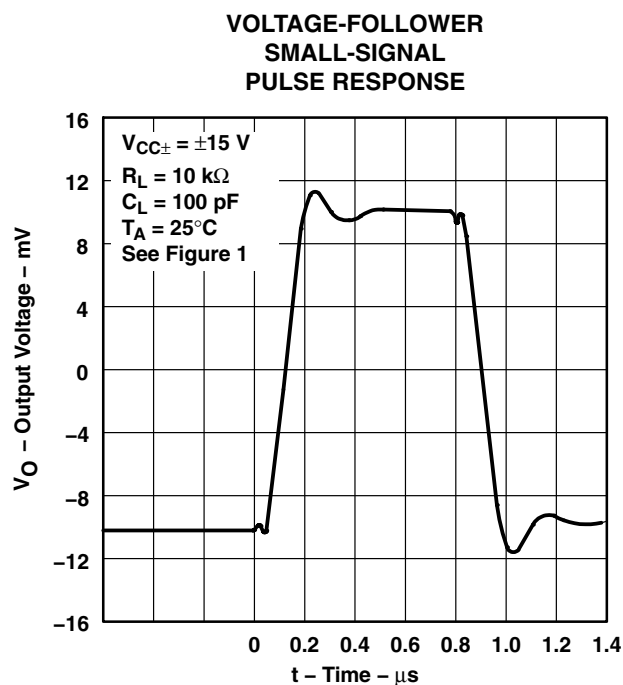
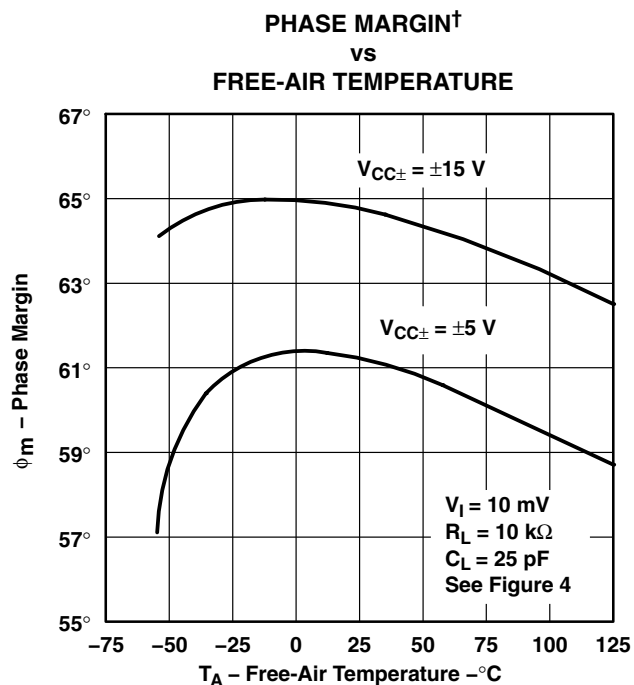
TL03x, TL03xA

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† Data at high and low temperatures are applicable only within the recommended operating free-air temperature ranges of the various devices.

APPLICATION INFORMATION

input characteristics

The TL03x and TL03xA are specified with a minimum and a maximum input voltage that, if exceeded at either input, could cause the device to malfunction.

Due to the extremely high input impedance and resulting low bias-current requirements, the TL03x and TL03xA are well suited for low-level signal processing; however, leakage currents on printed circuit boards and sockets easily can exceed bias-current requirements and cause degradation in system performance. It is a good practice to include guard rings around inputs (see Figure 61). These guard rings should be driven from a low-impedance source at the same voltage level as the common-mode input.

Unused amplifiers should be connected as grounded unity-gain followers to avoid oscillation.

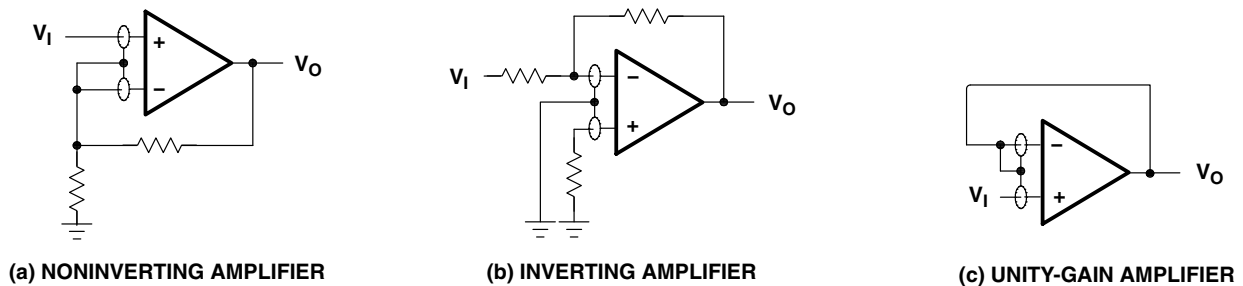


Figure 61. Use of Guard Rings

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APPLICATION INFORMATION

output characteristics

All operating characteristics (except bandwidth and phase margin) are specified with 100-pF load capacitance. The TL03x and TL03xA drive higher capacitive loads; however, as the load capacitance increases, the resulting response pole occurs at lower frequencies, thereby causing ringing, peaking, or even oscillation. The value of the load capacitance at which oscillation occurs varies with production lots. If an application appears to be sensitive to oscillation due to load capacitance, adding a small resistance in series with the load should alleviate the problem (see Figure 63). Capacitive loads of 1000 pF and larger can be driven if enough resistance is added in series with the output (see Figure 62).

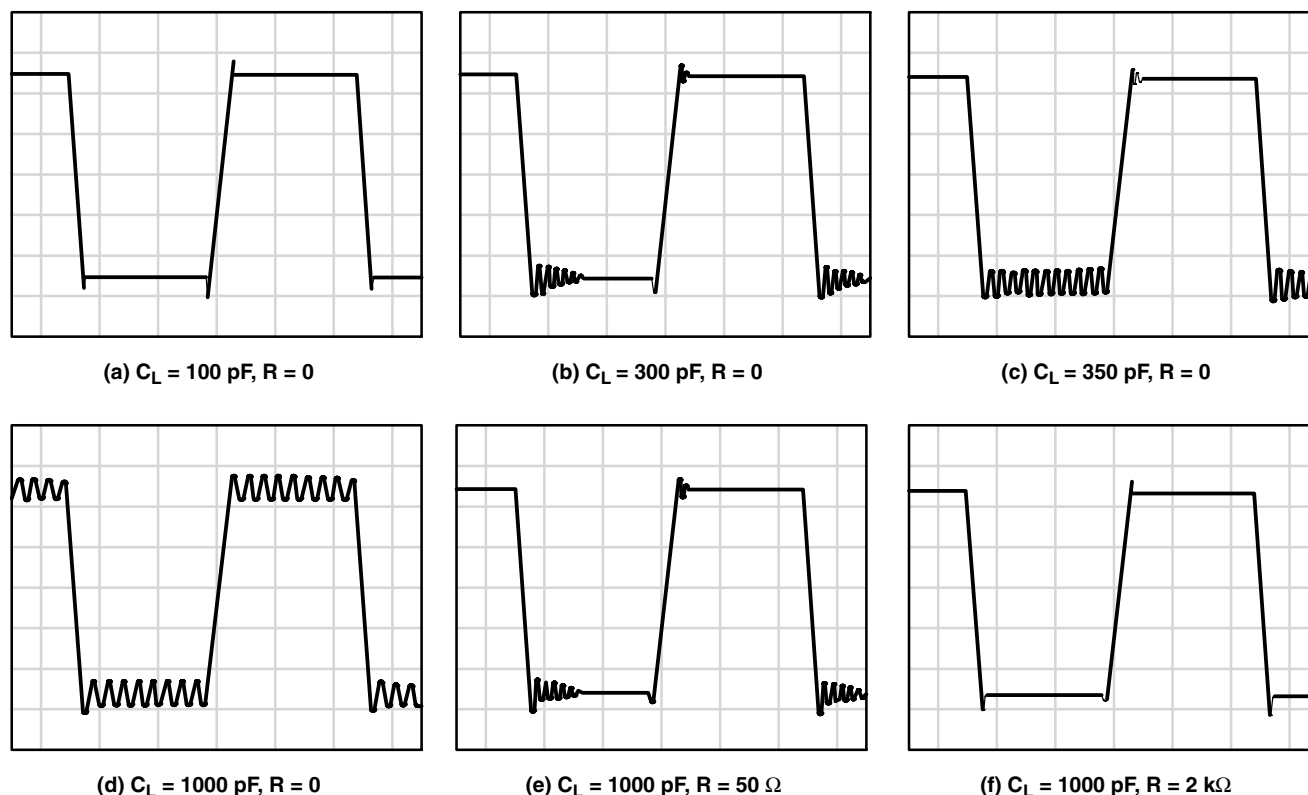


Figure 62. Effect of Capacitive Loads

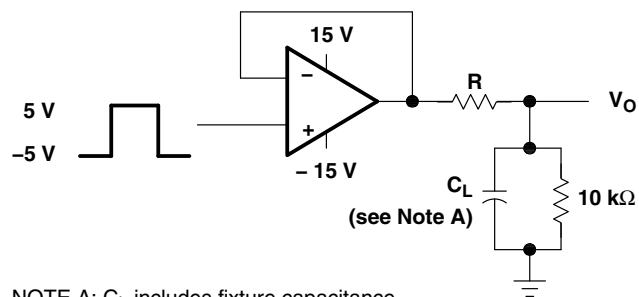


Figure 63. Test Circuit for Output Characteristics

APPLICATION INFORMATION

high-Q notch filter

In general, Texas Instruments enhanced-JFET operational amplifiers serve as excellent filters. The circuit in Figure 64 provides a narrow notch at a specific frequency. Notch filters are designed to eliminate frequencies that are interfering with the operation of an application. For this filter, the center frequency can be calculated as:

$$f_o = \frac{1}{2\pi \times R1 \times C1}$$

With the resistors and capacitors shown in Figure 64, the center frequency is 1 kHz. $C1 = C3 = C2 + 2$ and $R1 = R3 = 2 \times R2$. The center frequency can be modified by varying these values. When adjusting the center frequency, ensure that the operational amplifier has sufficient gain at the frequency required.

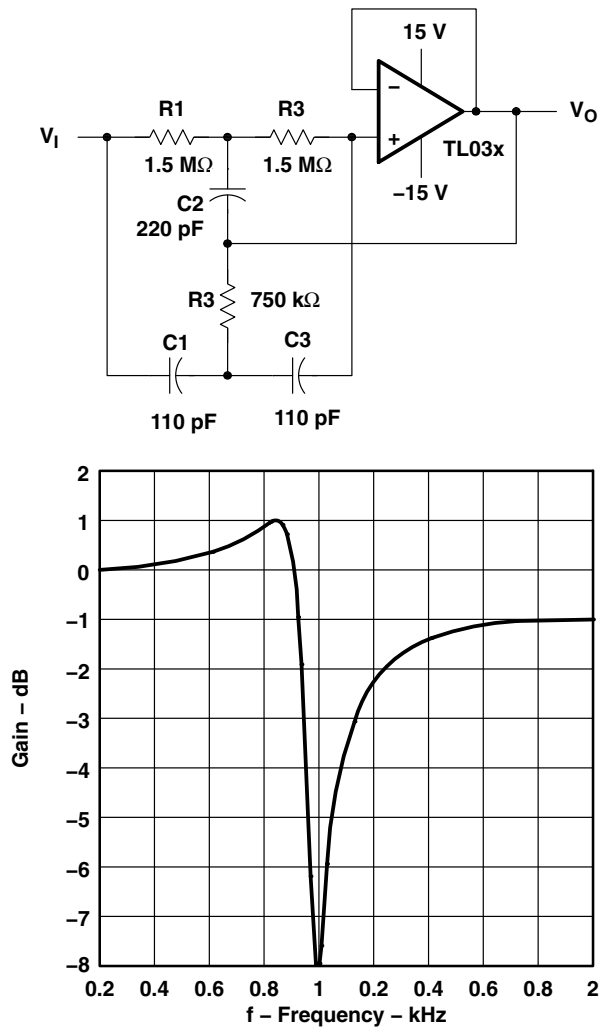


Figure 64. High-Q Notch Filter

TL03x, TL03xA

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APPLICATION INFORMATION

transimpedance amplifier

The low-power precision TL03x allows accurate measurement of low currents. The high input impedance and low offset voltage of the TL03xA greatly simplify the design of a transimpedance amplifier. At room temperature, this design achieves 10-bit accuracy with an error of less than 1/2 LSB.

Assuming that R_2 is much less than R_1 and ignoring error terms, the output voltage can be expressed as:

$$V_O = -I_{IN} \times R_F \left(\frac{R_1 + R_2}{R_2} \right)$$

Using the resistor values shown in the schematic for a 1-nA input current, the output voltage equals -0.1 V. If the V_O limit for the TL03xA is measured at ± 12 V, the maximum input current for these resistor values is ± 120 nA. Similarly, one LSB on a 10-bit scale corresponds to 12 mV of output voltage, or 120 pA of input current.

The following equation shows the effect of input offset voltage and input bias current on the output voltage:

$$V_O = - \left[V_{IO} + R_F (I_{IO} + I_{IB}) \right] \left(\frac{R_1 + R_2}{R_2} \right)$$

If the application requires input protection for the transimpedance amplifier, do not use standard PN diodes. Instead, use low-leakage Siliconix SN4117 JFETs (or equivalent) connected as diodes across the TL03xA inputs (see Figure 65).

As with all precision applications, special care must be taken to eliminate external sources of leakage and interference. Other precautions include using high-quality insulation, cleaning insulating surfaces to remove fluxes and other residue, and enclosing the application within a protective box.

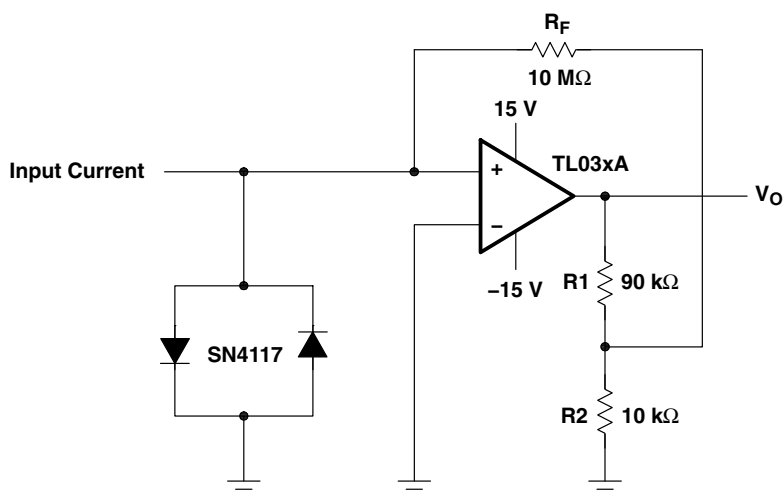


Figure 65. Transimpedance Amplifier

APPLICATION INFORMATION

4-mA to 20-mA current loops

Often, information from an analog sensor must be sent over a distance to the receiving circuitry. For many applications, the most feasible method involves converting voltage information to a current before transmission. The following circuits give two variations of low-power current loops. The circuit in Figure 66 requires three wires from the transmitting to receiving circuitry, while the second variation in Figure 67 requires only two wires, but includes an extra integrated circuit. Both circuits benefit from the high input impedance of the TL03xA because many inexpensive sensors do not have low output impedance.

Assuming that the voltage at the noninverting input of the TL03xA is zero, the following equation determines the output current:

$$I_O = V_I \left(\frac{R_3}{R_1 \times R_S} \right) + 5V \left(\frac{R_3}{R_2 \times R_S} \right) = 0.16 \times V_I + 4 \text{ mA}$$

The circuits presently provide 4-mA to 20-mA output current for an input voltage of 0 to 100 mV. By modifying R1, R2, and R3, the input voltage range or the output current range can be adjusted.

Including the offset voltage of the operational amplifier in the above equation clearly illustrates why the low offset TL03xA was chosen:

$$\begin{aligned} I_O &= V_I \left(\frac{R_3}{R_1 \times R_S} \right) + 5V \left(\frac{R_3}{R_2 \times R_S} \right) - V_I \left(\frac{R_3}{R_1 \times R_S} + \frac{R_3}{R_2 \times R_S} + \frac{R_1}{R_S} \right) \\ &= 0.16 \times V_I + 4 \text{ mA} - 0.17 \times V_I \end{aligned}$$

For example, an offset voltage of 1 mV decreases the output current by 0.17 mA.

Due to the low power consumption of the TL03xA, both circuits have at least 2 mA available to drive the actual sensor from the 5-V reference node.

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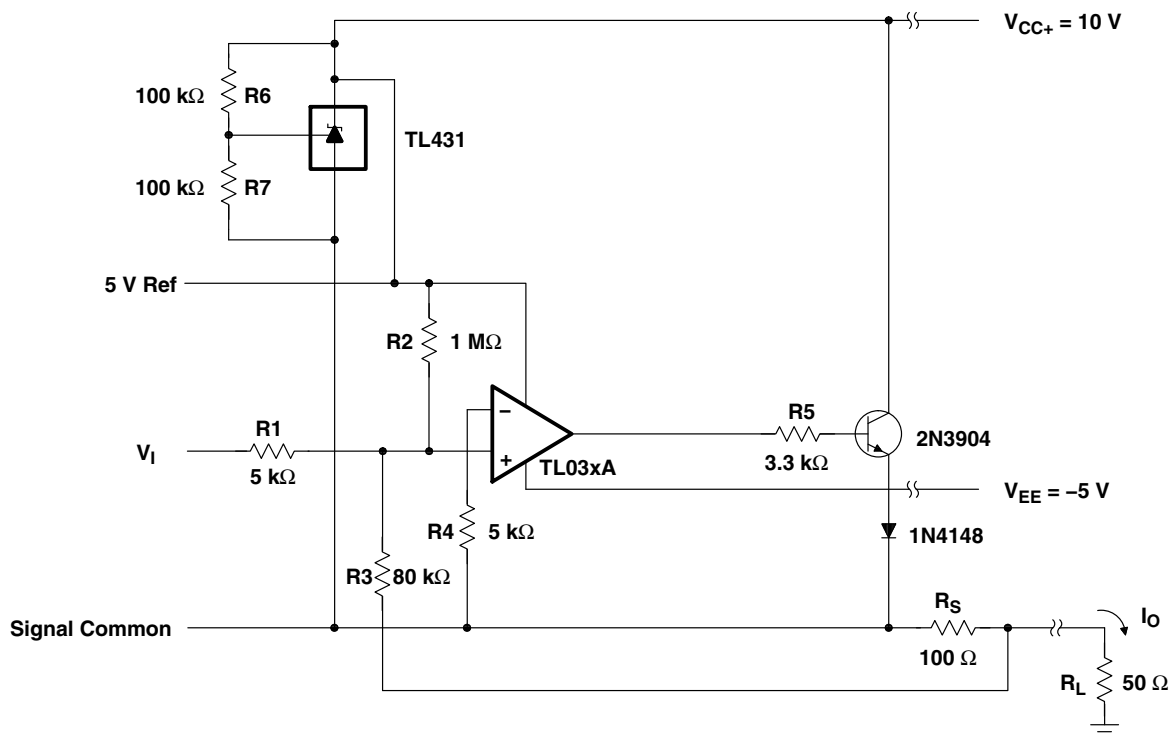


Figure 66. Three-Wire 4-mA to 20-mA Current Loop

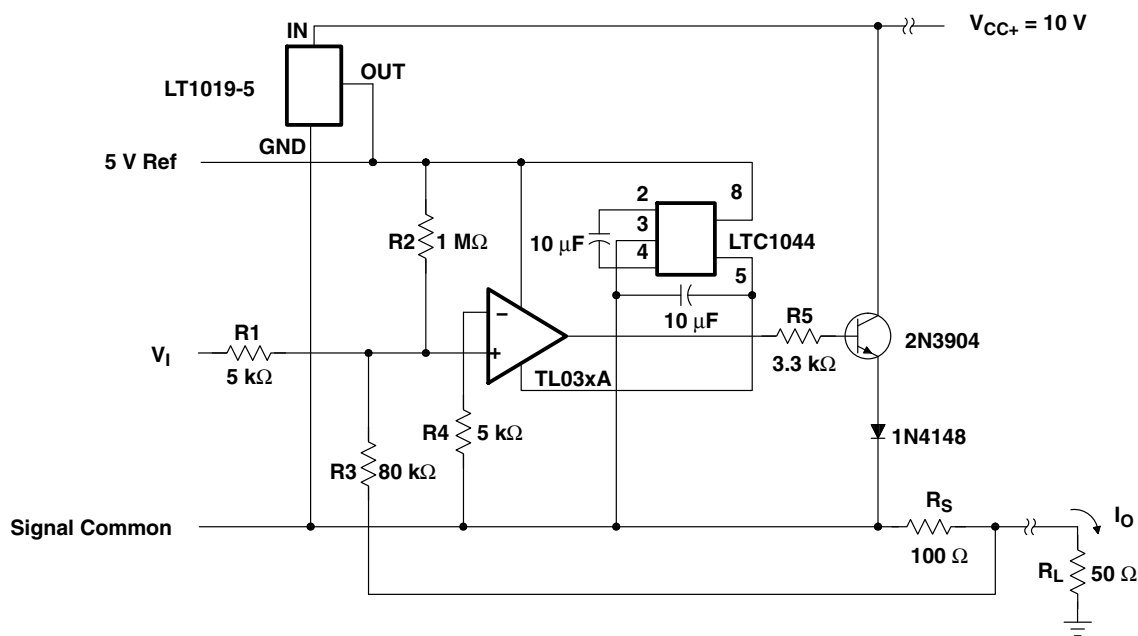


Figure 67. Two-Wire 4-mA to 20-mA Current Loop

APPLICATION INFORMATION

low-level light-detector preamplifier

Applications that need to detect small currents require high input-impedance operational amplifiers; otherwise, the bias currents of the operational amplifier camouflage the current being monitored. Phototransistors provide a current that is proportional to the light reaching the transistor. The TL03x allows even the small currents resulting from low-level light to be detected.

In Figure 68, if there is no light, the phototransistor is off and the output is high. As light is detected, the operational amplifier output begins pulling low. Adjusting R4 both compensates for offset voltage of the amplifier and adjusts the point of light detection by the amplifier.

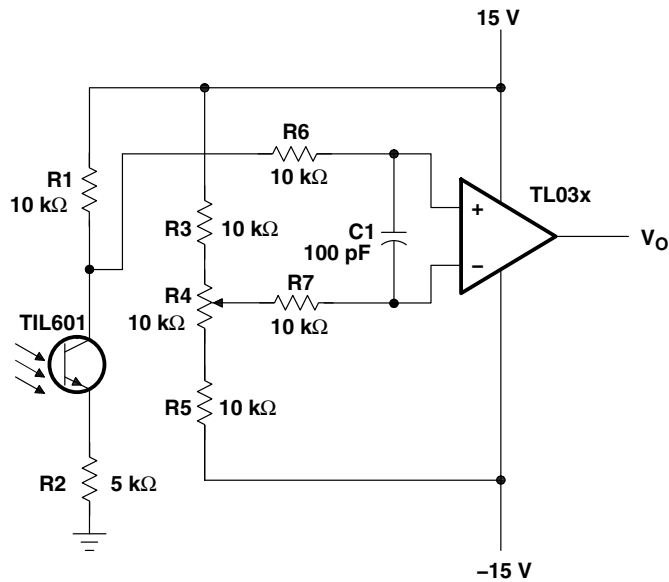


Figure 68. Low-Level Light-Detector Preamplifier

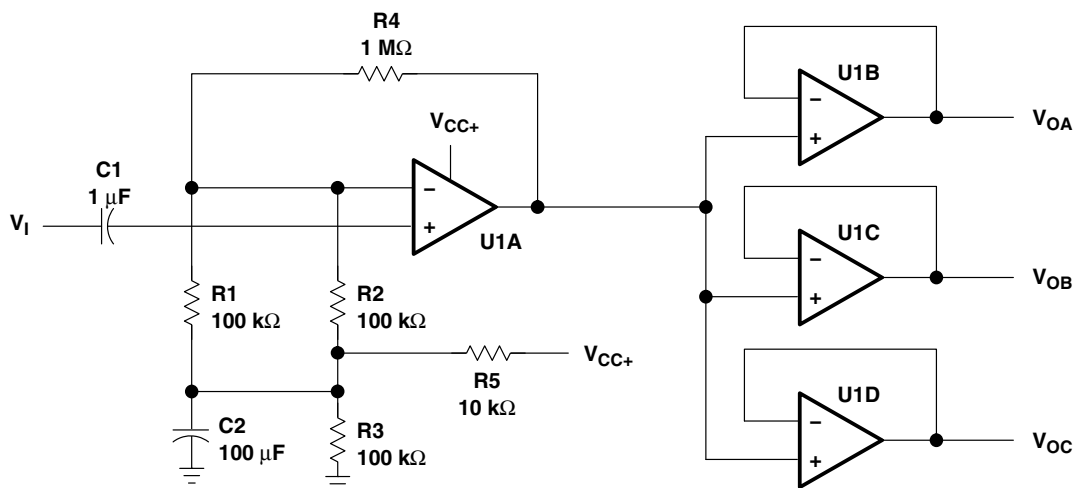
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APPLICATION INFORMATION

audio-distribution amplifier

This audio-distribution amplifier (see Figure 69) feeds the input signal to three separate output channels. U1A amplifies the input signal with a gain of 10, while U1B, U1C, and U1D serve as buffers to the output channels. The gain response of this circuit is very flat from 20 Hz to 20 kHz. The TL03x allows quick response to the input signal while maintaining low power consumption.



NOTE A: U1A through U1D = TL03x; $V_{CC+} = 5\text{ V}$

Figure 69. Audio-Distribution Amplifier Circuit

PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
5962-9086102Q2A	OBSOLETE	LCCC	FK	20		TBD	Call TI	Call TI
TL031ACD	OBSOLETE	SOIC	D	8		TBD	Call TI	Call TI
TL031ACP	OBSOLETE	PDIP	P	8		TBD	Call TI	Call TI
TL031AID	OBSOLETE	SOIC	D	8		TBD	Call TI	Call TI
TL031AIP	OBSOLETE	PDIP	P	8		TBD	Call TI	Call TI
TL031CD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL031CDE4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL031CDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL031CDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL031CDRE4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL031CDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL031CP	ACTIVE	PDIP	P	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TL031CPE4	ACTIVE	PDIP	P	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TL031CPWLE	OBSOLETE	TSSOP	PW	8		TBD	Call TI	Call TI
TL031ID	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL031IDE4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL031IDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL031IP	ACTIVE	PDIP	P	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TL031IPE4	ACTIVE	PDIP	P	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TL032ACD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL032ACDE4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL032ACDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL032ACDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL032ACDRE4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL032ACDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL032ACP	ACTIVE	PDIP	P	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TL032ACPE4	ACTIVE	PDIP	P	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
TL032AID	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL032AIDE4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL032AIDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL032AIDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL032AIDRE4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL032AIDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL032AIP	ACTIVE	PDIP	P	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TL032AIPE4	ACTIVE	PDIP	P	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TL032CD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL032CDE4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL032CDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL032CDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL032CDRE4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL032CDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL032CP	ACTIVE	PDIP	P	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TL032CPE4	ACTIVE	PDIP	P	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TL032CPSR	ACTIVE	SO	PS	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL032CPSRE4	ACTIVE	SO	PS	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL032CPSRG4	ACTIVE	SO	PS	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL032CPWLE	OBSOLETE	TSSOP	PW	8		TBD	Call TI	Call TI
TL032ID	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL032IDE4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL032IDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL032IDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL032IDRE4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL032IDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
TL032IP	ACTIVE	PDIP	P	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TL032IPE4	ACTIVE	PDIP	P	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TL032MFKB	OBSOLETE	LCCC	FK	20		TBD	Call TI	Call TI
TL032MJGB	OBSOLETE	CDIP	JG	8		TBD	Call TI	Call TI
TL034ACD	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL034ACDE4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL034ACDG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL034ACDR	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL034ACDRE4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL034ACDRG4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL034ACN	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TL034ACNE4	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TL034AID	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL034AIDE4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL034AIDG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL034AIDR	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL034AIDRE4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL034AIDRG4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL034AIN	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TL034AINE4	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TL034CD	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL034CDE4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL034CDG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL034CDR	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL034CDRE4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL034CDRG4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL034CN	ACTIVE	PDIP	N	14	25	Pb-Free	CU NIPDAU	N / A for Pkg Type

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
(RoHS)								
TL034CNE4	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TL034CNSR	ACTIVE	SO	NS	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL034CNSRE4	ACTIVE	SO	NS	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL034CNSRG4	ACTIVE	SO	NS	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL034CPW	ACTIVE	TSSOP	PW	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL034CPWE4	ACTIVE	TSSOP	PW	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL034CPWG4	ACTIVE	TSSOP	PW	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL034CPWLE	OBSOLETE	TSSOP	PW	14		TBD	Call TI	Call TI
TL034CPWR	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL034CPWRE4	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL034CPWRG4	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL034ID	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL034IDE4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL034IDG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL034IDR	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL034IDRG4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TL034IN	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TL034INE4	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TL034MD	OBSOLETE	SOIC	D	14		TBD	Call TI	Call TI
TL034MFKB	OBSOLETE	LCCC	FK	20		TBD	Call TI	Call TI
TL034MJB	OBSOLETE	CDIP	J	14		TBD	Call TI	Call TI
TL034MN	OBSOLETE	PDIP	N	14		TBD	Call TI	Call TI

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

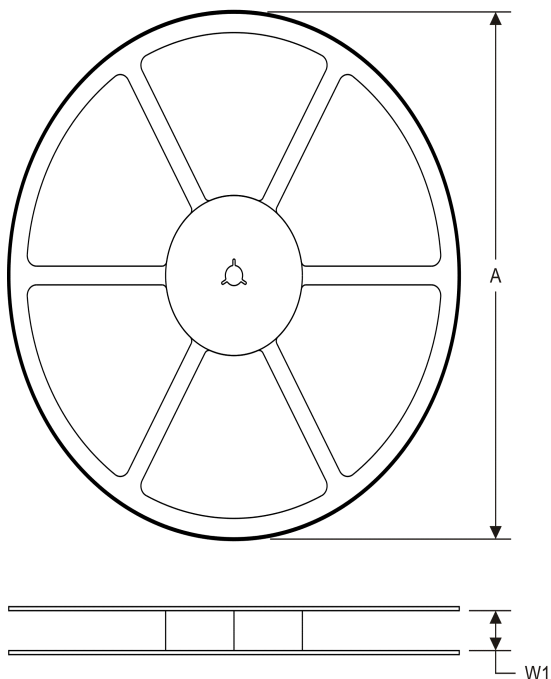
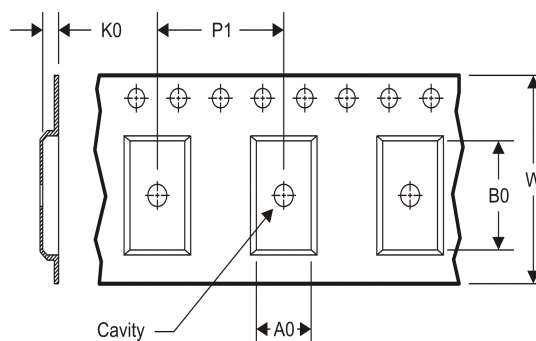
Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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TAPE AND REEL INFORMATION
REEL DIMENSIONS

TAPE DIMENSIONS


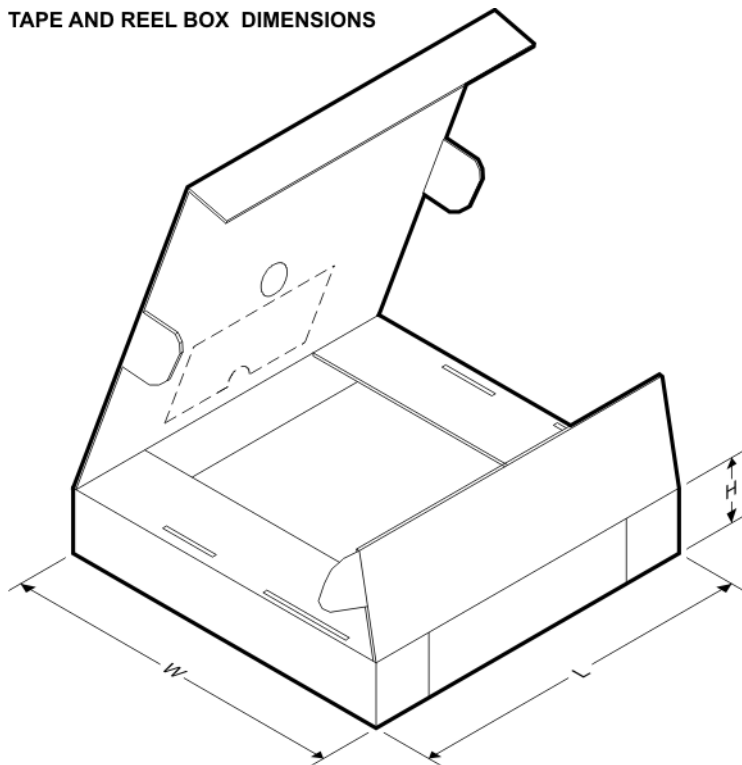
A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

TAPE AND REEL INFORMATION

*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TL031CDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TL032ACDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TL032AIDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TL032CDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TL032CPSR	SO	PS	8	2000	330.0	16.4	8.2	6.6	2.5	12.0	16.0	Q1
TL032IDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TL034ACDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TL034AIDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TL034CDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TL034CNSR	SO	NS	14	2000	330.0	16.4	8.2	10.5	2.5	12.0	16.0	Q1
TL034CPWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
TL034IDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1

TAPE AND REEL BOX DIMENSIONS

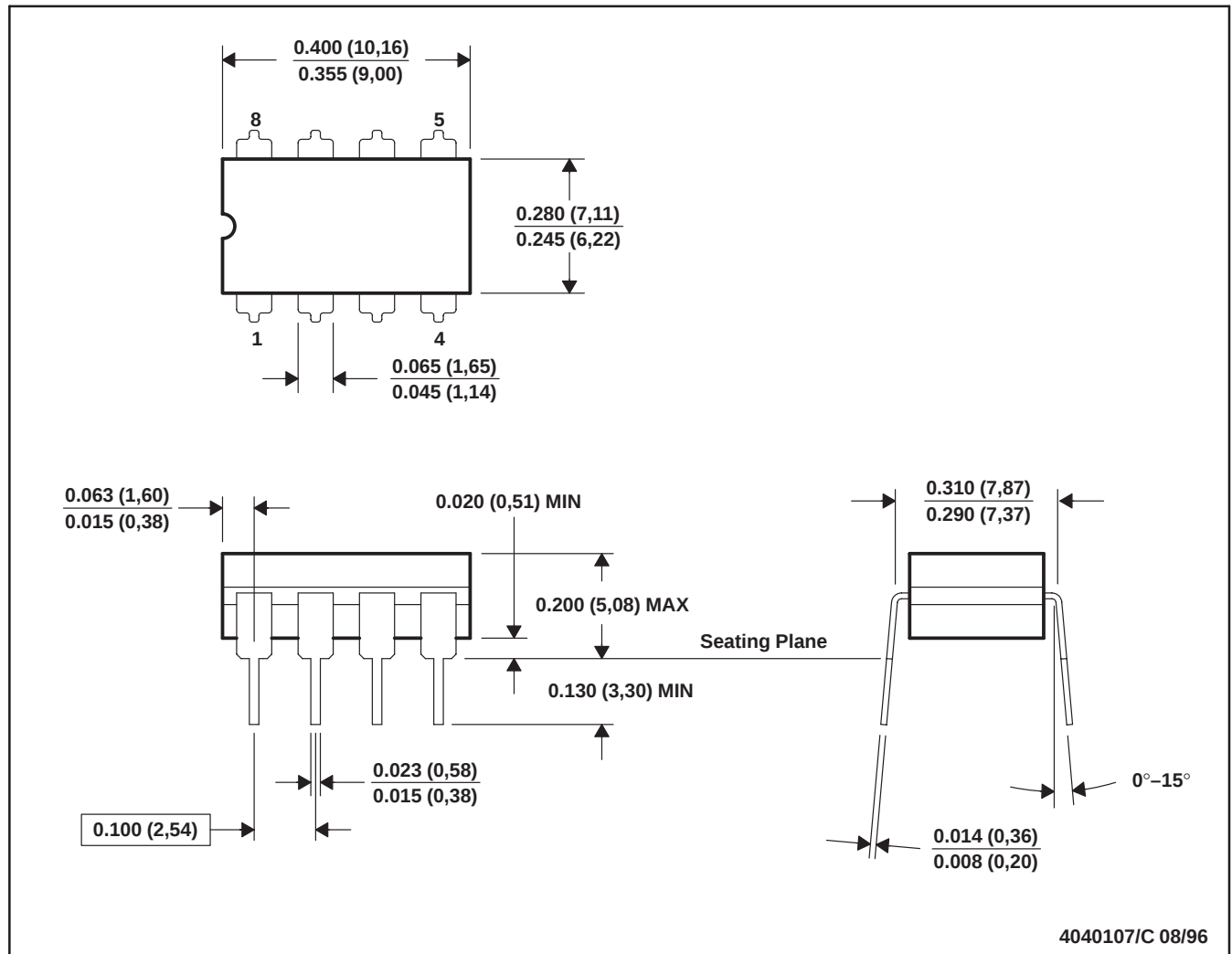


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TL031CDR	SOIC	D	8	2500	340.5	338.1	20.6
TL032ACDR	SOIC	D	8	2500	340.5	338.1	20.6
TL032AIDR	SOIC	D	8	2500	340.5	338.1	20.6
TL032CDR	SOIC	D	8	2500	340.5	338.1	20.6
TL032CPSR	SO	PS	8	2000	367.0	367.0	38.0
TL032IDR	SOIC	D	8	2500	340.5	338.1	20.6
TL034ACDR	SOIC	D	14	2500	367.0	367.0	38.0
TL034AIDR	SOIC	D	14	2500	367.0	367.0	38.0
TL034CDR	SOIC	D	14	2500	367.0	367.0	38.0
TL034CNSR	SO	NS	14	2000	367.0	367.0	38.0
TL034CPWR	TSSOP	PW	14	2000	367.0	367.0	35.0
TL034IDR	SOIC	D	14	2500	367.0	367.0	38.0

JG (R-GDIP-T8)

CERAMIC DUAL-IN-LINE

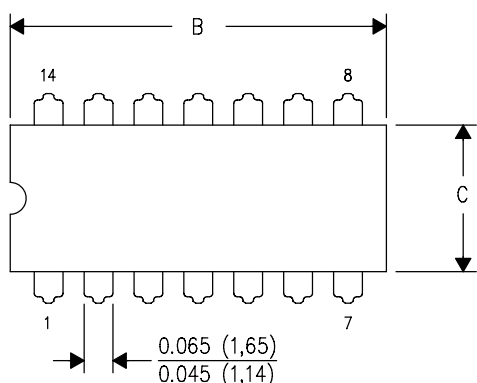


- NOTES: A. All linear dimensions are in inches (millimeters).
 B. This drawing is subject to change without notice.
 C. This package can be hermetically sealed with a ceramic lid using glass frit.
 D. Index point is provided on cap for terminal identification.
 E. Falls within MIL STD 1835 GDIP1-T8

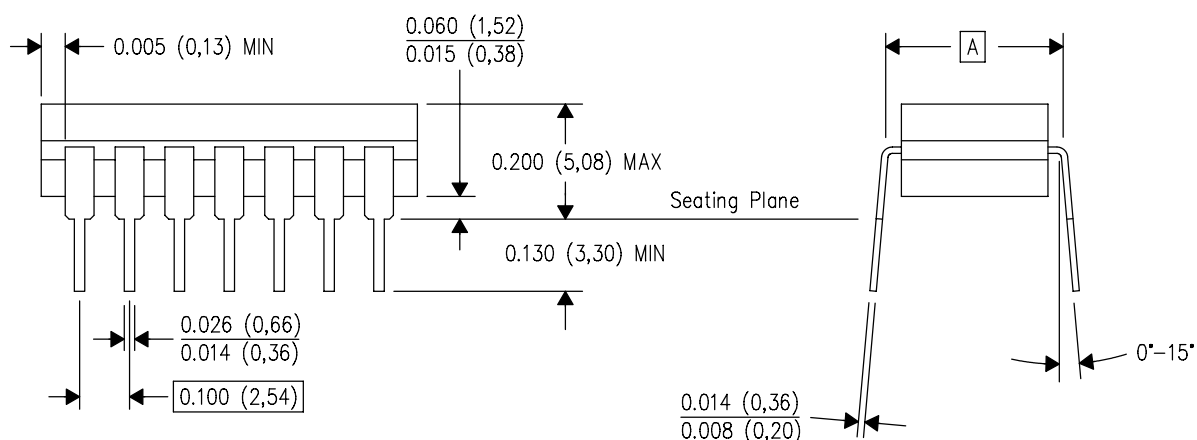
J (R-GDIP-T**)

14 LEADS SHOWN

CERAMIC DUAL IN-LINE PACKAGE



PINS ** DIM	14	16	18	20
A	0.300 (7,62) BSC	0.300 (7,62) BSC	0.300 (7,62) BSC	0.300 (7,62) BSC
B MAX	0.785 (19,94)	.840 (21,34)	0.960 (24,38)	1.060 (26,92)
B MIN	—	—	—	—
C MAX	0.300 (7,62)	0.300 (7,62)	0.310 (7,87)	0.300 (7,62)
C MIN	0.245 (6,22)	0.245 (6,22)	0.220 (5,59)	0.245 (6,22)



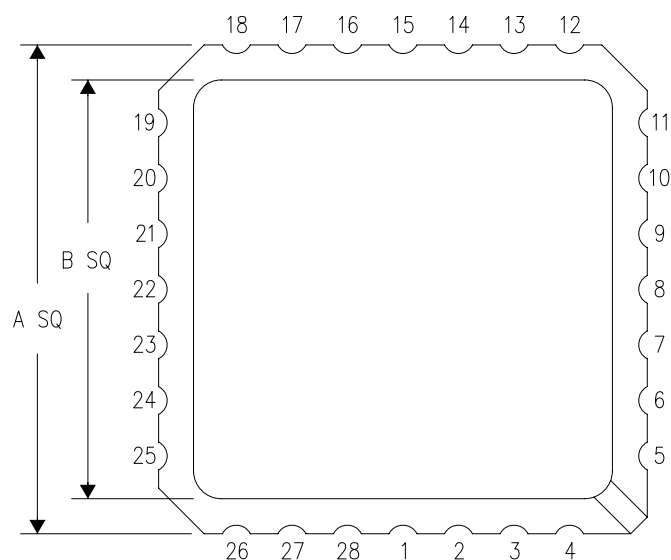
4040083/F 03/03

- NOTES:
- A. All linear dimensions are in inches (millimeters).
 - B. This drawing is subject to change without notice.
 - C. This package is hermetically sealed with a ceramic lid using glass frit.
 - D. Index point is provided on cap for terminal identification only on press ceramic glass frit seal only.
 - E. Falls within MIL STD 1835 GDIP1-T14, GDIP1-T16, GDIP1-T18 and GDIP1-T20.

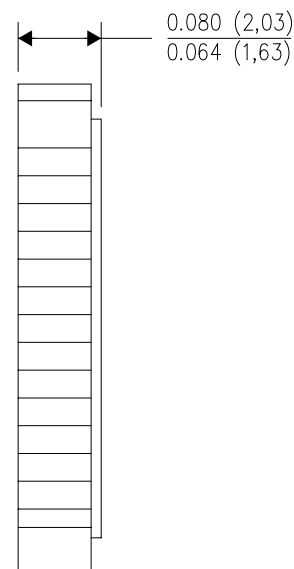
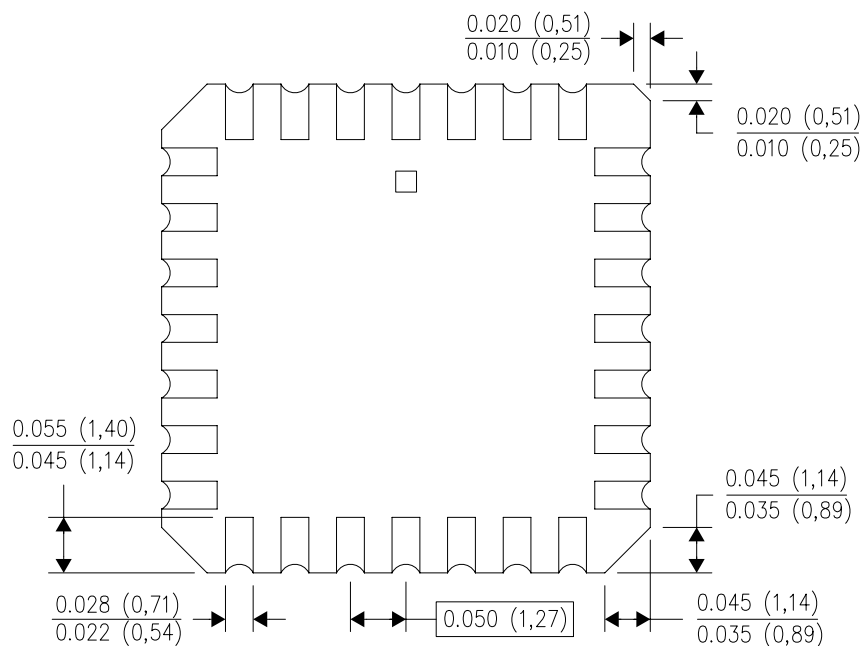
FK (S-CQCC-N**)

LEADLESS CERAMIC CHIP CARRIER

28 TERMINAL SHOWN



NO. OF TERMINALS **	A		B	
	MIN	MAX	MIN	MAX
20	0.342 (8,69)	0.358 (9,09)	0.307 (7,80)	0.358 (9,09)
28	0.442 (11,23)	0.458 (11,63)	0.406 (10,31)	0.458 (11,63)
44	0.640 (16,26)	0.660 (16,76)	0.495 (12,58)	0.560 (14,22)
52	0.740 (18,78)	0.761 (19,32)	0.495 (12,58)	0.560 (14,22)
68	0.938 (23,83)	0.962 (24,43)	0.850 (21,6)	0.858 (21,8)
84	1.141 (28,99)	1.165 (29,59)	1.047 (26,6)	1.063 (27,0)

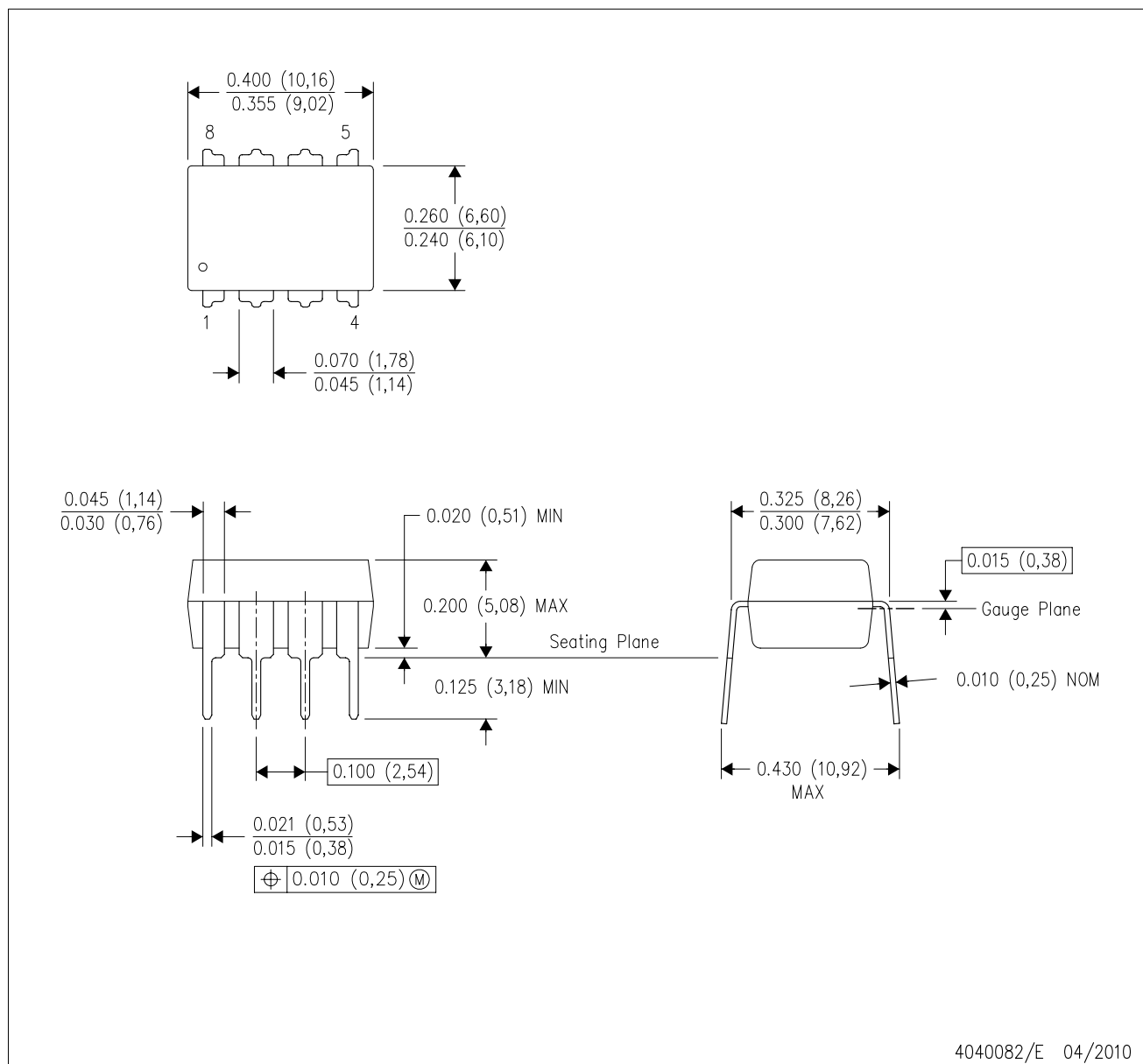


4040140/D 01/11

- NOTES:
- All linear dimensions are in inches (millimeters).
 - This drawing is subject to change without notice.
 - This package can be hermetically sealed with a metal lid.
 - Falls within JEDEC MS-004

P (R-PDIP-T8)

PLASTIC DUAL-IN-LINE PACKAGE

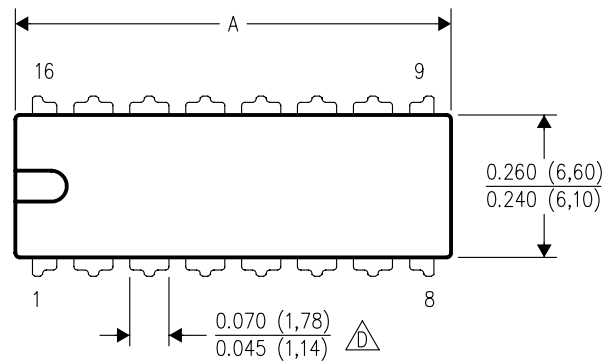


- NOTES:
- A. All linear dimensions are in inches (millimeters).
 - B. This drawing is subject to change without notice.
 - C. Falls within JEDEC MS-001 variation BA.

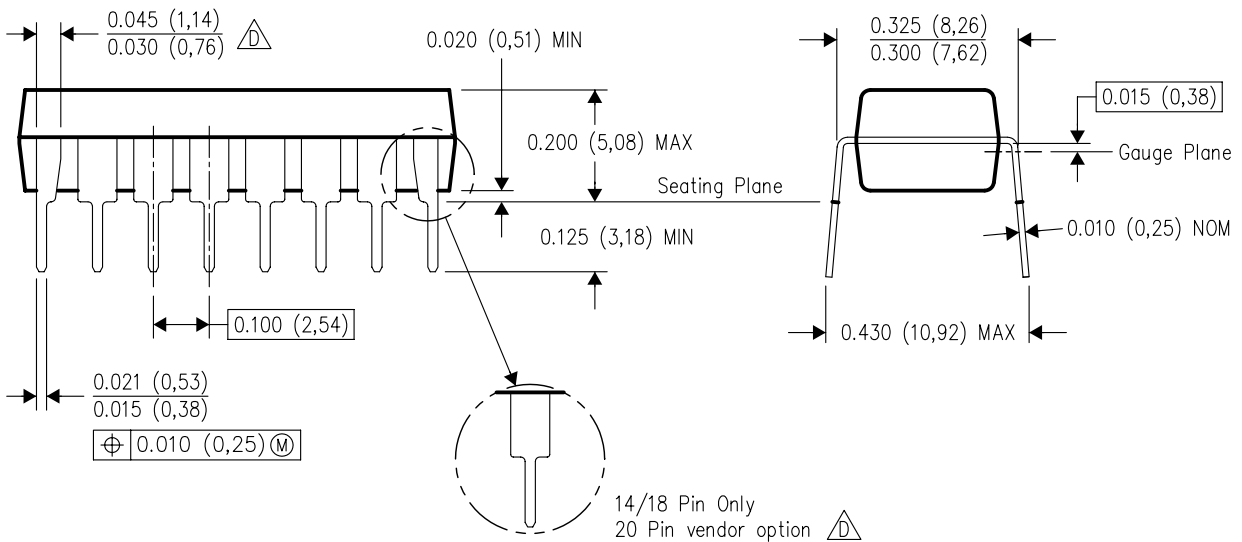
N (R-PDIP-T**)

16 PINS SHOWN

PLASTIC DUAL-IN-LINE PACKAGE



PINS **	14	16	18	20
DIM				
A MAX	0.775 (19,69)	0.775 (19,69)	0.920 (23,37)	1.060 (26,92)
A MIN	0.745 (18,92)	0.745 (18,92)	0.850 (21,59)	0.940 (23,88)
MS-001 VARIATION	AA	BB	AC	AD



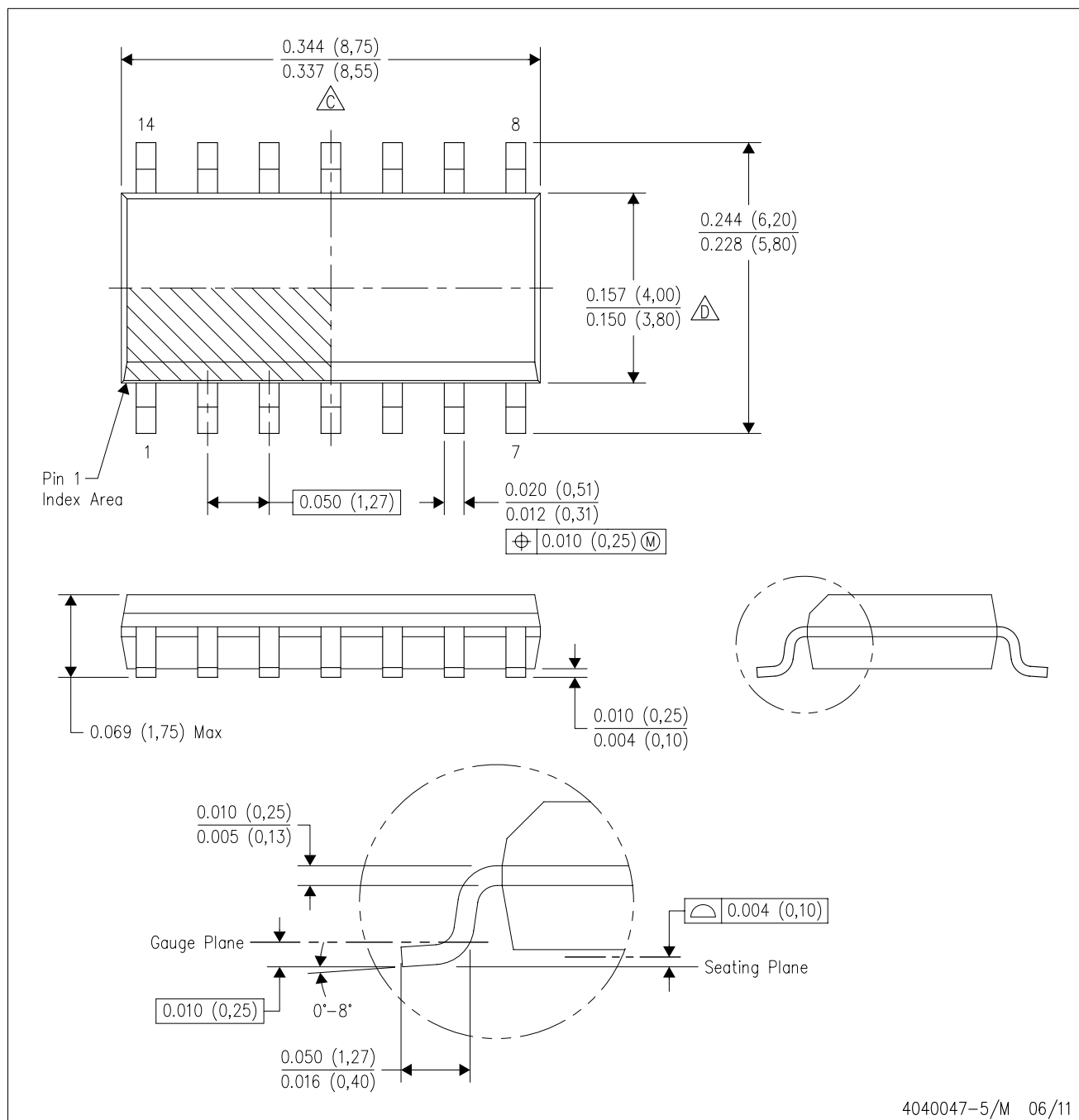
14/18 Pin Only
20 Pin vendor option

4040049/E 12/2002

- NOTES:
- A. All linear dimensions are in inches (millimeters).
 - B. This drawing is subject to change without notice.
 - Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
 - The 20 pin end lead shoulder width is a vendor option, either half or full width.

D (R-PDSO-G14)

PLASTIC SMALL OUTLINE

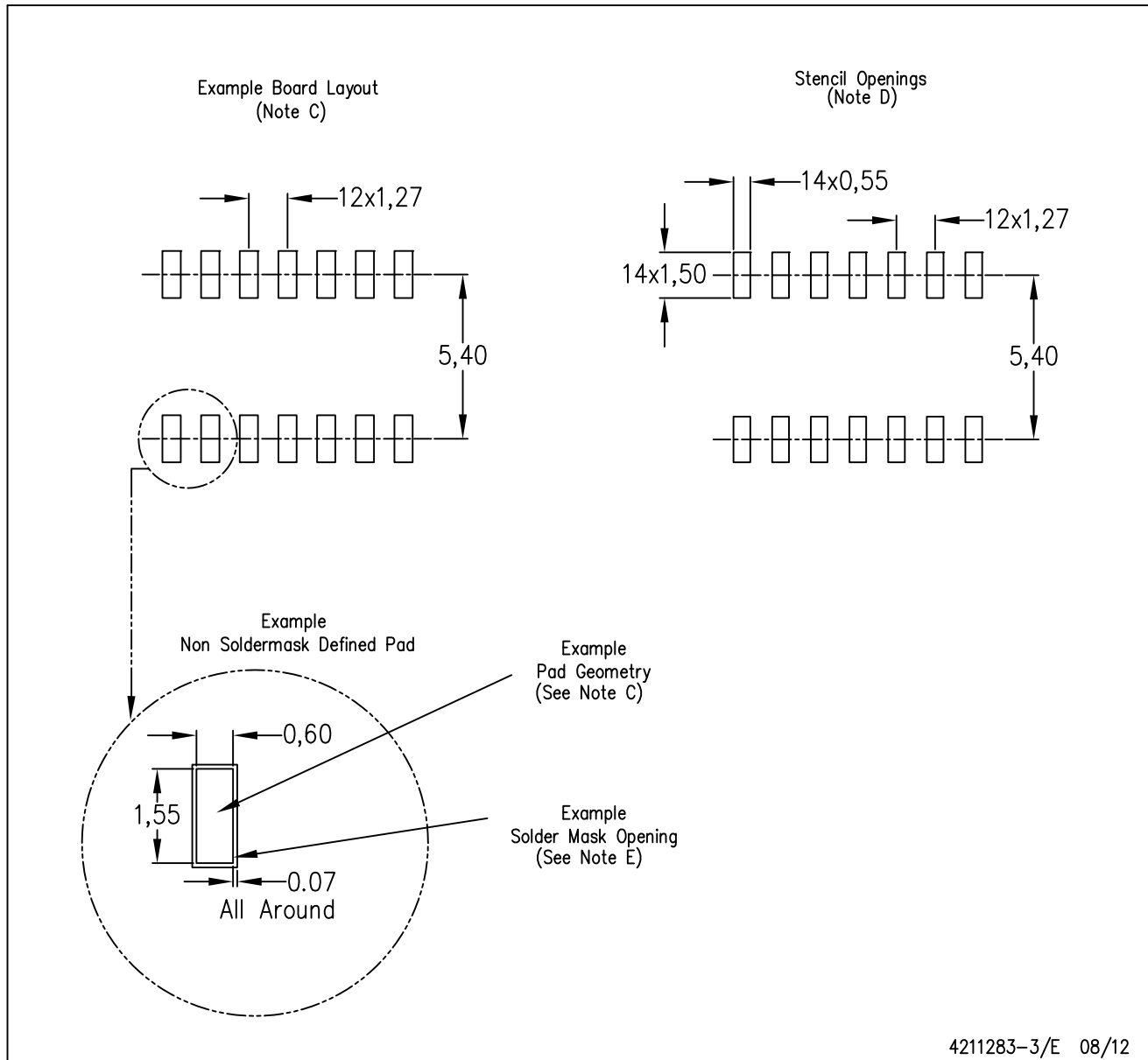


NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- D. Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AB.

D (R-PDSO-G14)

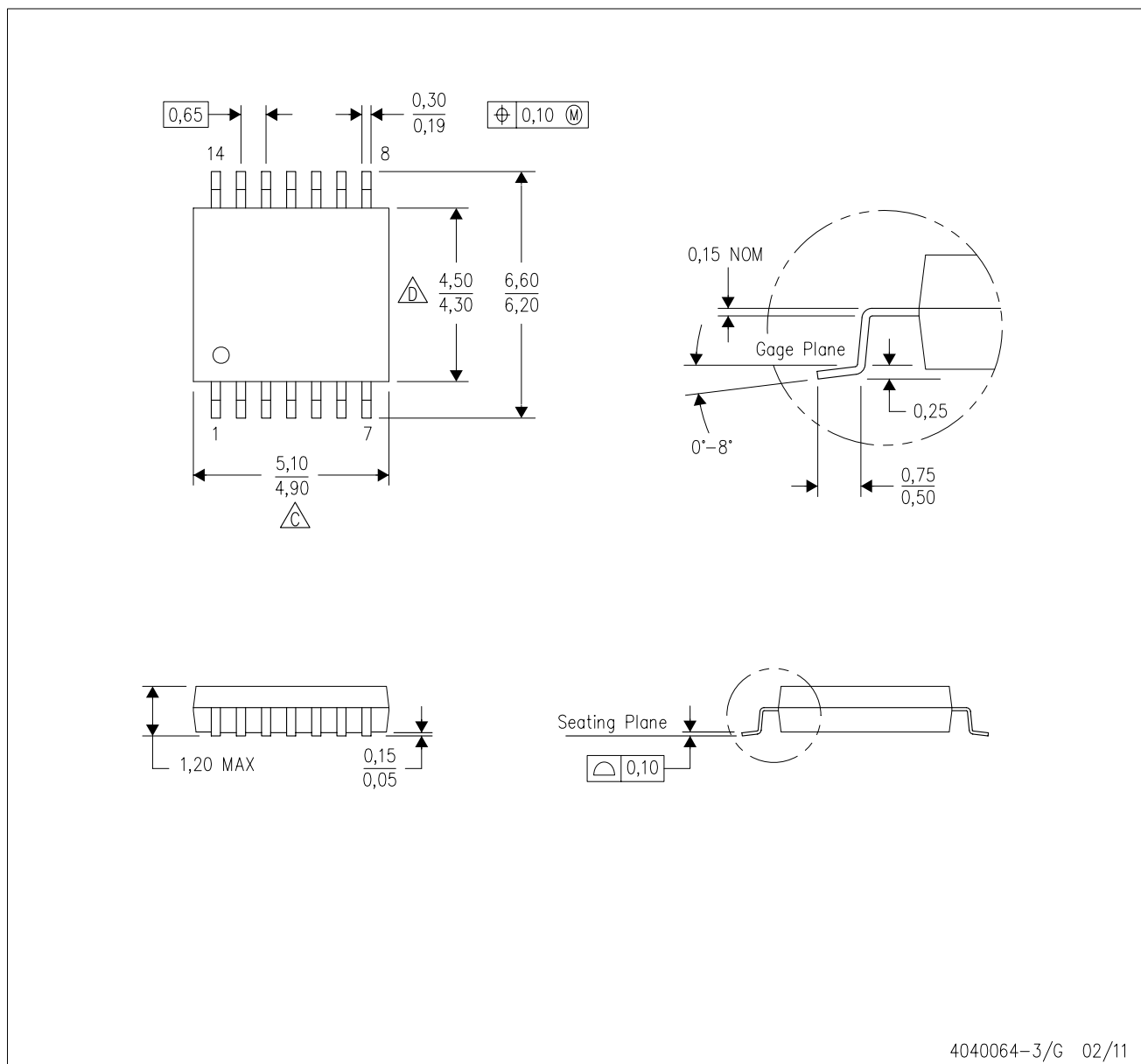
PLASTIC SMALL OUTLINE



- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Publication IPC-7351 is recommended for alternate designs.
 - D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
 - E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

PW (R-PDSO-G14)

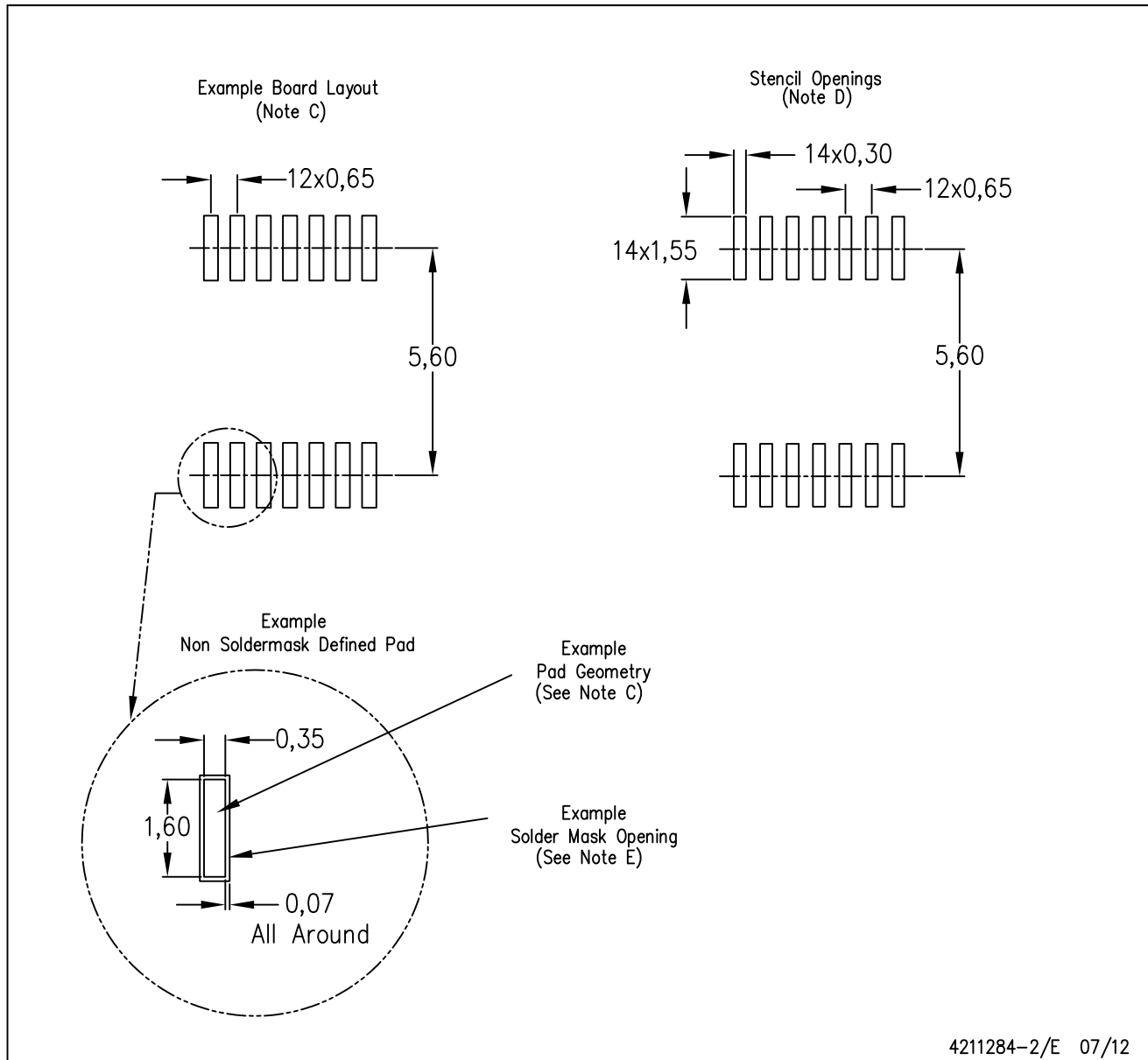
PLASTIC SMALL OUTLINE



- NOTES:
- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
 - B. This drawing is subject to change without notice.
 - C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
 - D. Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
 - E. Falls within JEDEC MO-153

PW (R-PDSO-G14)

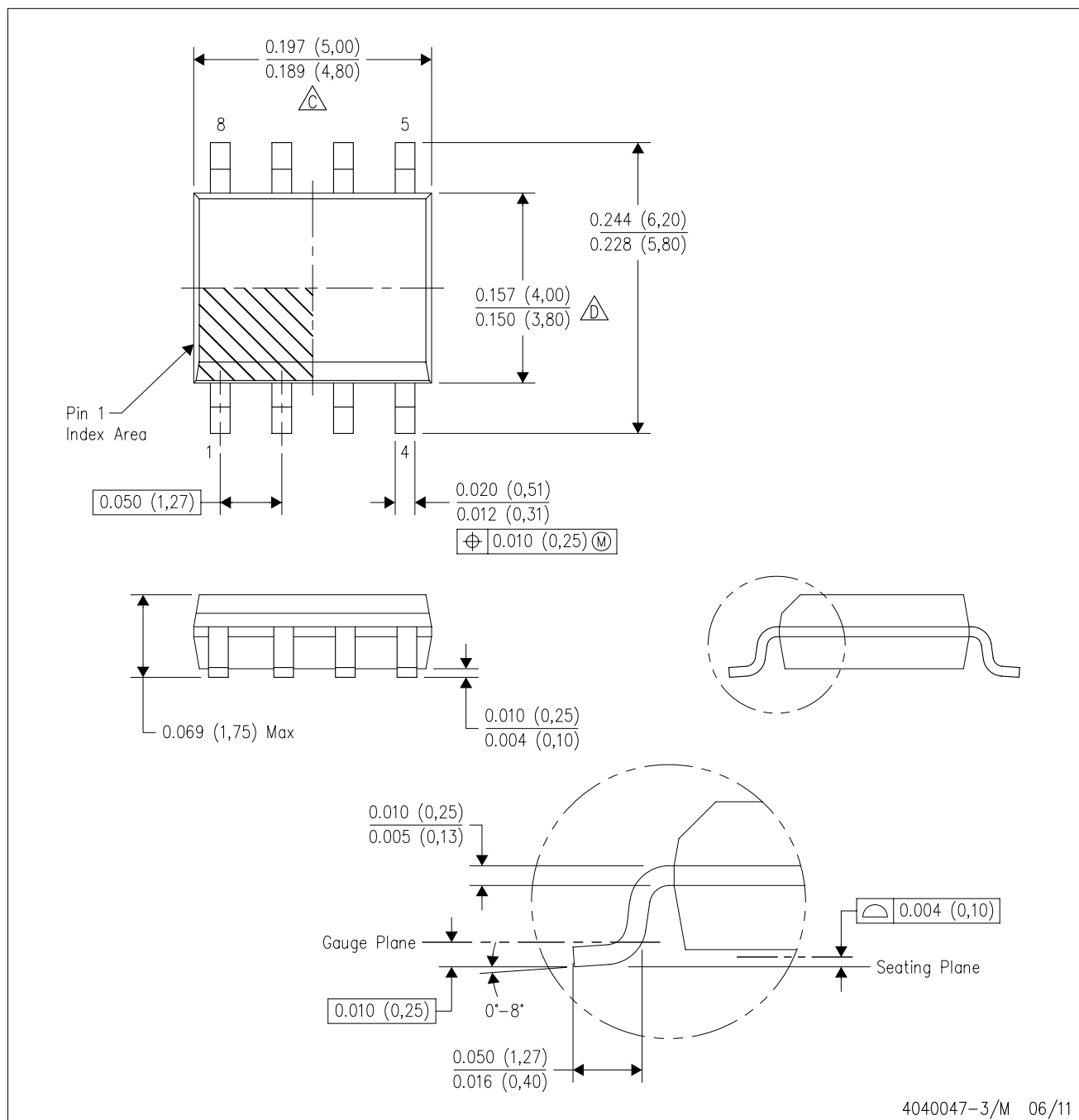
PLASTIC SMALL OUTLINE



- NOTES:
- All linear dimensions are in millimeters.
 - This drawing is subject to change without notice.
 - Publication IPC-7351 is recommended for alternate designs.
 - Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
 - Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

D (R-PDSO-G8)

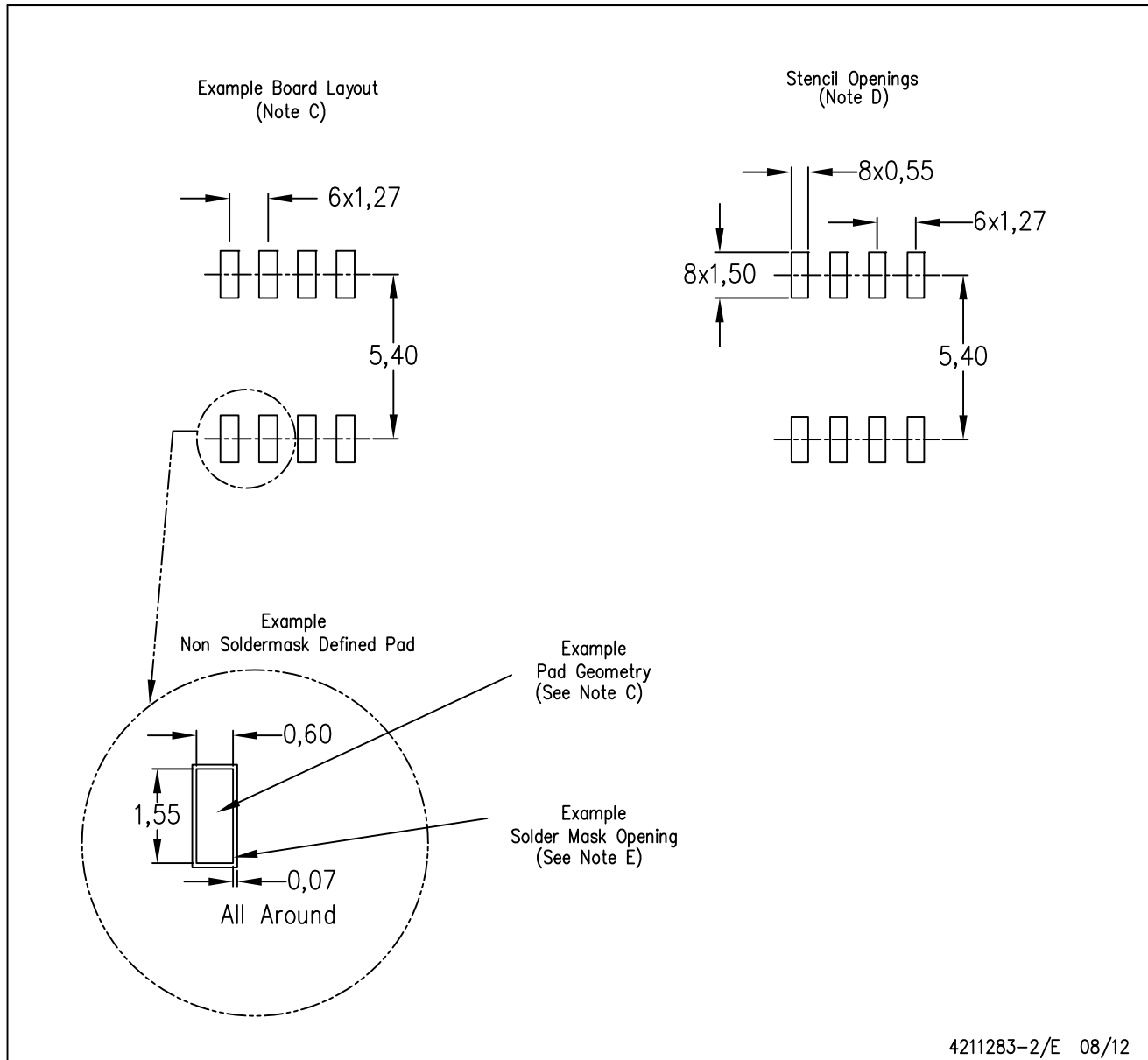
PLASTIC SMALL OUTLINE



- NOTES:
- A. All linear dimensions are in inches (millimeters).
 - B. This drawing is subject to change without notice.
 - $\triangle C$ Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
 - $\triangle D$ Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
 - E. Reference JEDEC MS-012 variation AA.

D (R-PDSO-G8)

PLASTIC SMALL OUTLINE

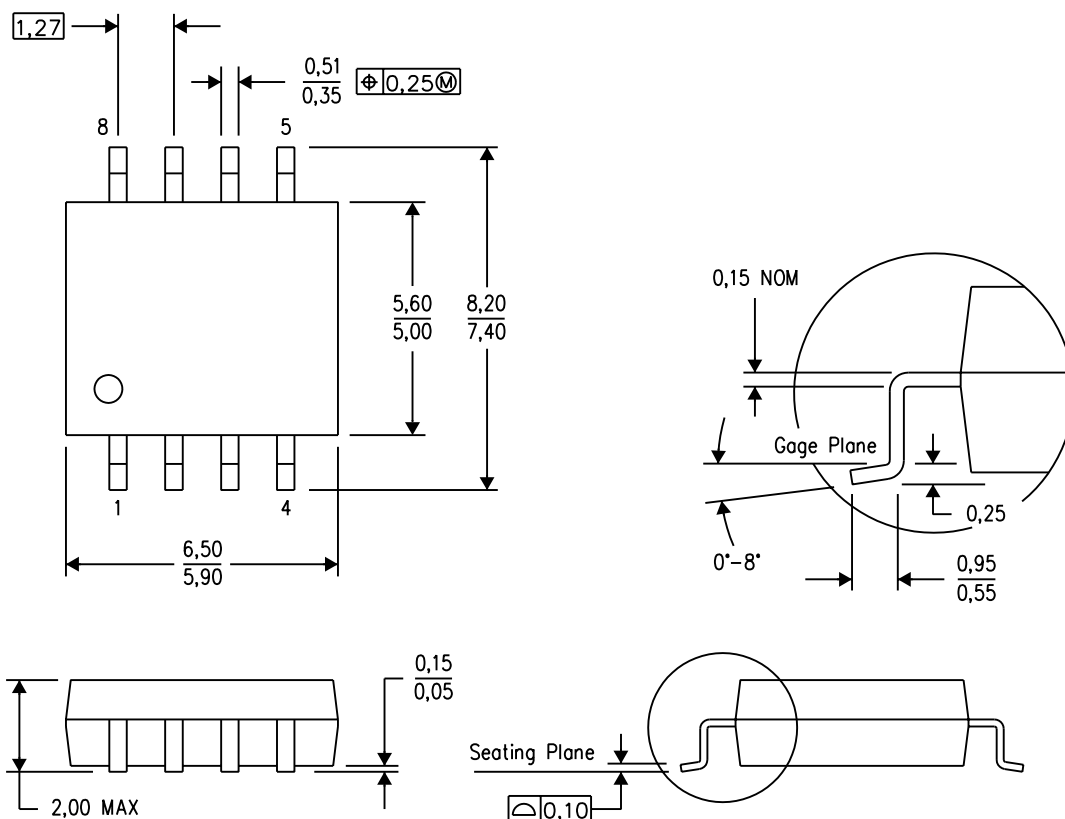


- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Publication IPC-7351 is recommended for alternate designs.
 - D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
 - E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

MECHANICAL DATA

PS (R-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE

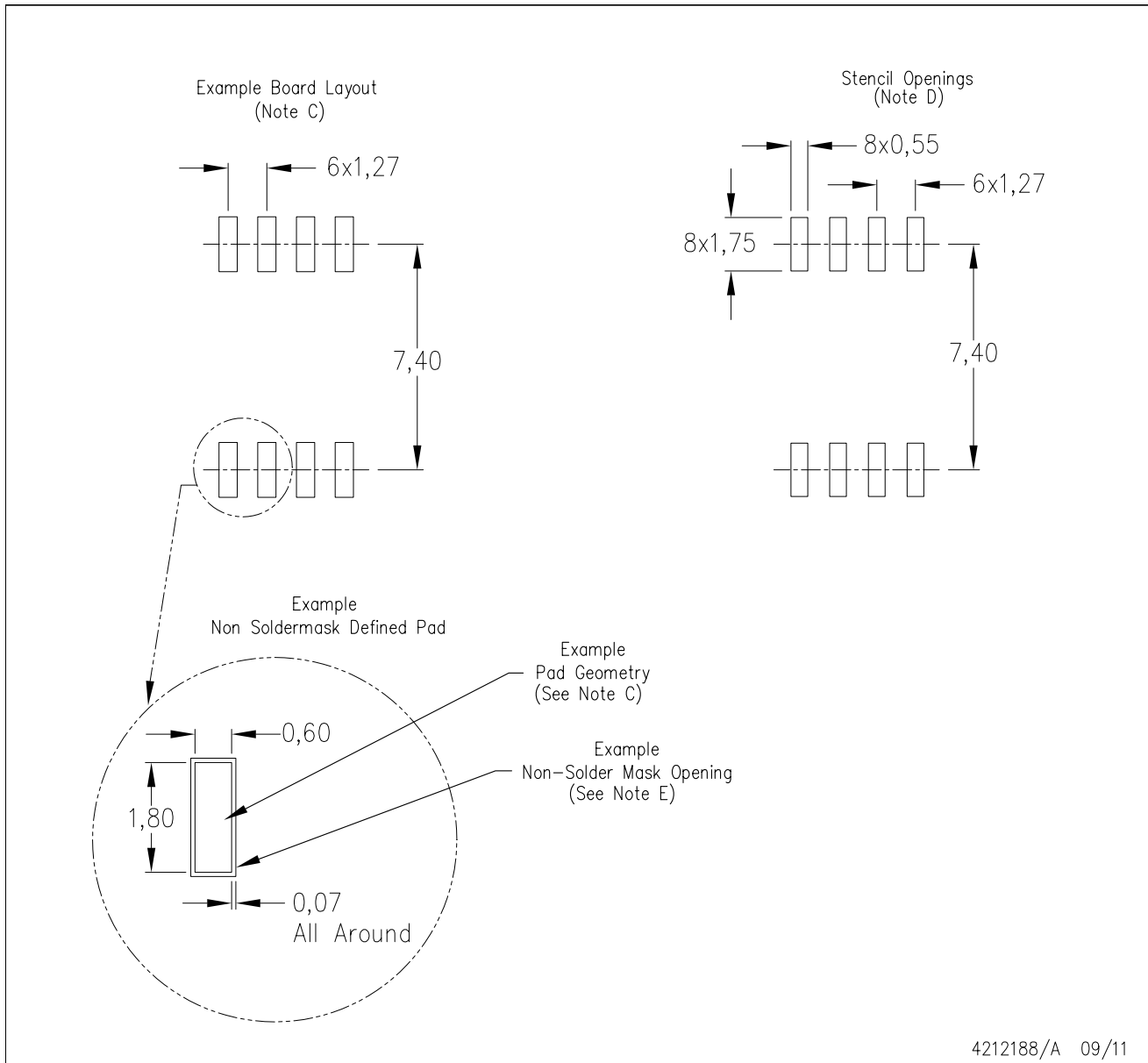


4040063/C 03/03

- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.

PS (R-PDSO-G8)

PLASTIC SMALL OUTLINE



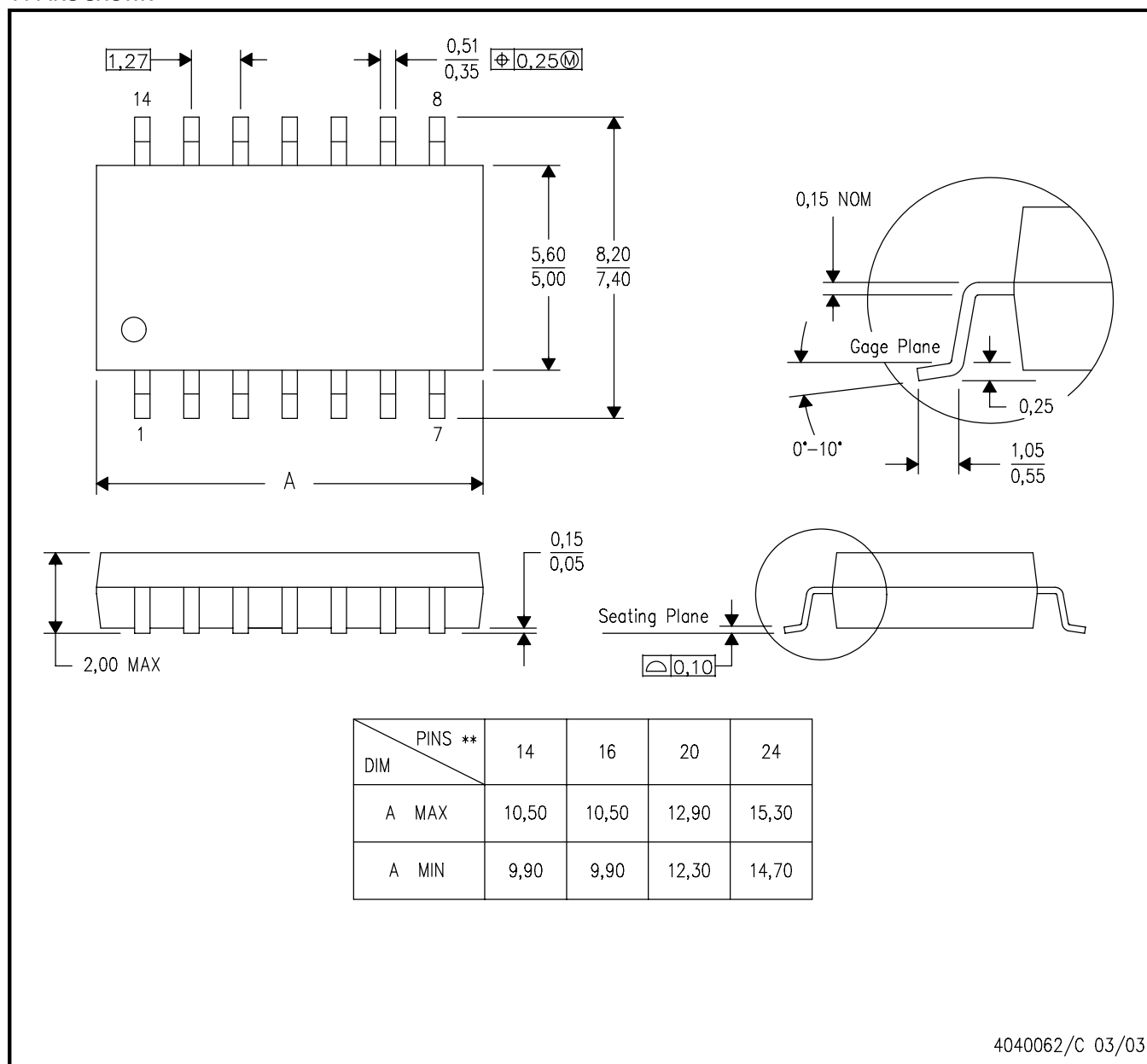
- NOTES:
- All linear dimensions are in millimeters.
 - This drawing is subject to change without notice.
 - Publication IPC-7351 is recommended for alternate designs.
 - Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
 - Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

MECHANICAL DATA

NS (R-PDSO-G**)

PLASTIC SMALL-OUTLINE PACKAGE

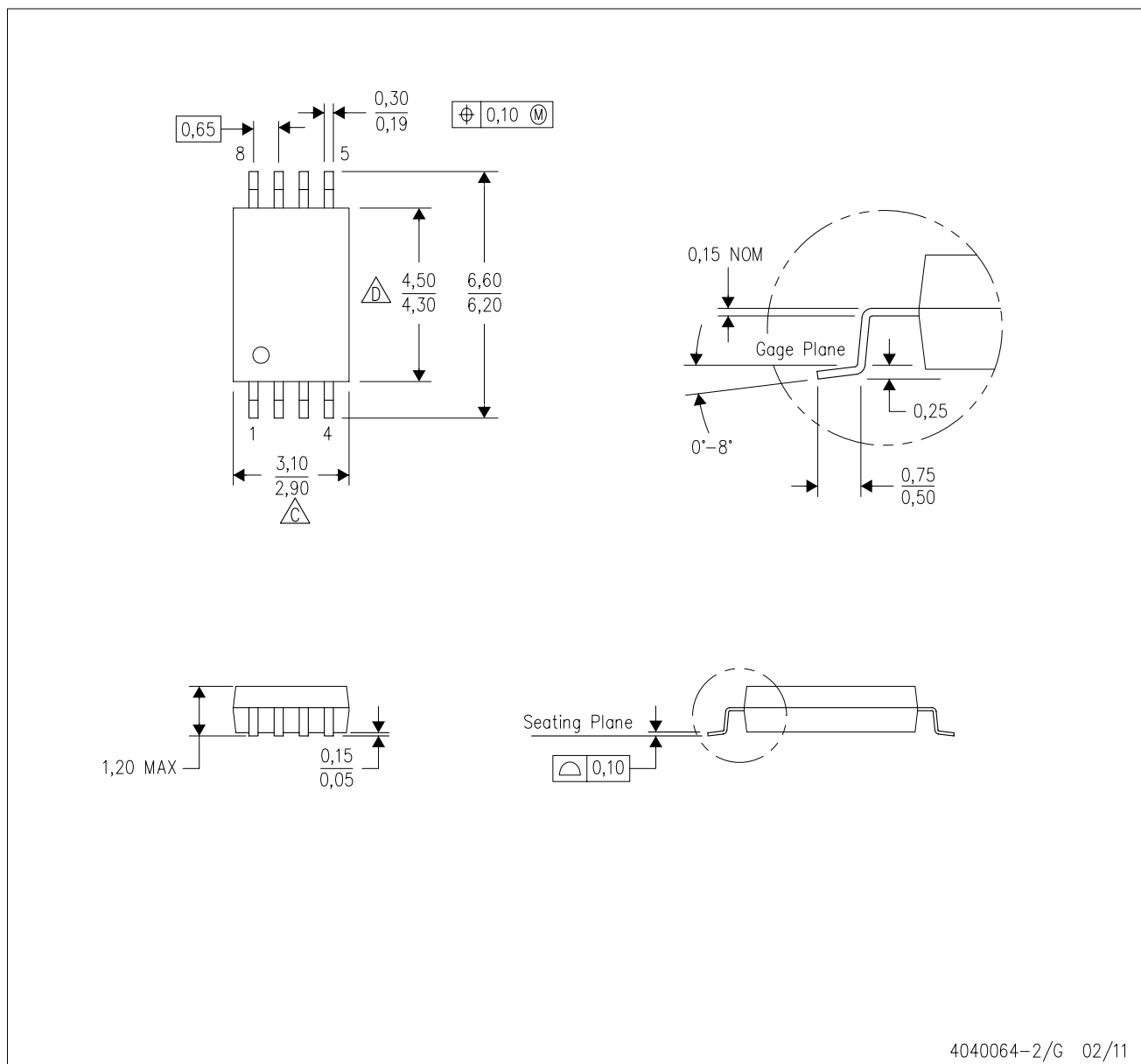
14-PINS SHOWN



- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.

PW (R-PDSO-G8)

PLASTIC SMALL OUTLINE



- NOTES:
- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
 - B. This drawing is subject to change without notice.
 - C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
 - D. Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
 - E. Falls within JEDEC MO-153

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